

RL78/G13

RENESAS MCU

R01DS0131EJ0350 Rev.3.50 Jun 30, 2020

True low-power platform (66 μ A/MHz, and 0.57 μ A for operation with only RTC and LVD) for the general-purpose applications, with 1.6-V to 5.5-V operation, 16- to 512-Kbyte code flash memory, and 41 DMIPS at 32 MHz

1. OUTLINE

1.1 Features

Ultra-low power consumption technology

- V_{DD} = single power supply voltage of 1.6 to 5.5 V
- HALT mode
- STOP mode
- SNOOZE mode

RL78 CPU core

- CISC architecture with 3-stage pipeline
- Minimum instruction execution time: Can be changed from high speed (0.03125 µs: @ 32 MHz operation with high-speed on-chip oscillator) to ultra-low speed (30.5 µs: @ 32.768 kHz operation with subsystem clock)
- Address space: 1 MB
- General-purpose registers: (8-bit register x 8) x 4 banks
- On-chip RAM: 2 to 32 KB

Code flash memory

- Code flash memory: 16 to 512 KB
- Block size: 1 KB
- Prohibition of block erase and rewriting (security function)
- On-chip debug function
- Self-programming (with boot swap function/flash shield window function)

Data Flash Memory

- Data flash memory: 4 KB to 8 KB
- Back ground operation (BGO): Instructions can be executed from the program memory while rewriting the data flash memory.
- Number of rewrites: 1,000,000 times (TYP.)
- Voltage of rewrites: VDD = 1.8 to 5.5 V

High-speed on-chip oscillator

- Select from 32 MHz, 24 MHz, 16 MHz, 12 MHz, 8 MHz, 6 MHz, 4 MHz, 3 MHz, 2 MHz, and 1 MHz
- High accuracy: +/- 1.0 % (VDD = 1.8 to 5.5 V, TA = -20 to +85°C)

Operating ambient temperature

- T_A = -40 to +85°C (A: Consumer applications, D: Industrial applications)
- TA = -40 to +105°C (G: Industrial applications)

Power management and reset function

- On-chip power-on-reset (POR) circuit
- On-chip voltage detector (LVD) (Select interrupt and reset from 14 levels)

DMA (Direct Memory Access) controller

- 2/4 channels
- Number of clocks during transfer between 8/16-bit SFR and internal RAM: 2 clocks

Multiplier and divider/multiply-accumulator

- 16 bits × 16 bits = 32 bits (Unsigned or signed)
- 32 bits ÷ 32 bits = 32 bits (Unsigned)
- 16 bits x 16 bits + 32 bits = 32 bits (Unsigned or signed)

Serial interface

- CSI: 2 to 8 channels
- UART/UART (LIN-bus supported):2 to 4 channels
- I²C/Simplified I²C communication: 3 to 10 channels

Timer

- 16-bit timer: 8 to 16 channels
- 12-bit interval timer: 1 channel
- Real-time clock: 1 channel (calendar for 99 years,

alarm function, and clock correction function)

• Watchdog timer: 1 channel (operable with the

dedicated low-speed on-chip

oscillator)

A/D converter

- 8/10-bit resolution A/D converter (VDD = 1.6 to 5.5 V)
- Analog input: 6 to 26 channels
- Internal reference voltage (1.45 V) and temperature sensor Note 1

I/O port

- I/O port: 16 to 120 (N-ch open drain I/O [withstand voltage of 6 V]: 0 to 4, N-ch open drain I/O [VDD withstand voltage Note 2/EVDD withstand voltage Note 3]: 5 to 25)
- Can be set to N-ch open drain, TTL input buffer, and on-chip pull-up resistor
- Different potential interface: Can connect to a 1.8/2.5/3
 V device
- On-chip key interrupt function
- On-chip clock output/buzzer output controller

Others

- On-chip BCD (binary-coded decimal) correction circuit
- Notes 1. Can be selected only in HS (high-speed main)
 - 2. Products with 20 to 52 pins
 - 3. Products with 64 to 128 pins

Remark The functions mounted depend on the product.

See 1.6 Outline of Functions.

O ROM, RAM capacities

Flash	Data	RAM			RL78	s/G13		
ROM	flash		20 pins	24 pins	25 pins	30 pins	32 pins	36 pins
128	8 KB	12	_	_	_	R5F100AG	R5F100BG	R5F100CG
KB	-	KB	_	_	_	R5F101AG	R5F101BG	R5F101CG
96	8 KB	8 KB	_	_	_	R5F100AF	R5F100BF	R5F100CF
KB	_		-	-	-	R5F101AF	R5F101BF	R5F101CF
64	4 KB	4 KB	R5F1006E	R5F1007E	R5F1008E	R5F100AE	R5F100BE	R5F100CE
KB	_	Note	R5F1016E	R5F1017E	R5F1018E	R5F101AE	R5F101BE	R5F101CE
48	4 KB	3 KB Note	R5F1006D	R5F1007D	R5F1008D	R5F100AD	R5F100BD	R5F100CD
KB	_	Note	R5F1016D	R5F1017D	R5F1018D	R5F101AD	R5F101BD	R5F101CD
32	4 KB	2 KB	R5F1006C	R5F1007C	R5F1008C	R5F100AC	R5F100BC	R5F100CC
KB	-		R5F1016C	R5F1017C	R5F1018C	R5F101AC	R5F101BC	R5F101CC
16	4 KB	2 KB	R5F1006A	R5F1007A	R5F1008A	R5F100AA	R5F100BA	R5F100CA
KB	_		R5F1016A	R5F1017A	R5F1018A	R5F101AA	R5F101BA	R5F101CA

Flash	Data	RAM				RL78	s/G13			
ROM	flash		40 pins	44 pins	48 pins	52 pins	64 pins	80 pins	100 pins	128 pins
512	8 KB	32 KB Note	_	R5F100FL	R5F100GL	R5F100JL	R5F100LL	R5F100ML	R5F100PL	R5F100SL
KB	-	Note	=	R5F101FL	R5F101GL	R5F101JL	R5F101LL	R5F101ML	R5F101PL	R5F101SL
384	8 KB	24 KB	-	R5F100FK	R5F100GK	R5F100JK	R5F100LK	R5F100MK	R5F100PK	R5F100SK
KB	-		_	R5F101FK	R5F101GK	R5F101JK	R5F101LK	R5F101MK	R5F101PK	R5F101SK
256	8 KB	20 KB Note	-	R5F100FJ	R5F100GJ	R5F100JJ	R5F100LJ	R5F100MJ	R5F100PJ	R5F100SJ
KB	-	Note	-	R5F101FJ	R5F101GJ	R5F101JJ	R5F101LJ	R5F101MJ	R5F101PJ	R5F101SJ
192	8 KB	16 KB	R5F100EH	R5F100FH	R5F100GH	R5F100JH	R5F100LH	R5F100MH	R5F100PH	R5F100SH
KB	_		R5F101EH	R5F101FH	R5F101GH	R5F101JH	R5F101LH	R5F101MH	R5F101PH	R5F101SH
128	8 KB	12 KB	R5F100EG	R5F100FG	R5F100GG	R5F100JG	R5F100LG	R5F100MG	R5F100PG	-
KB	-		R5F101EG	R5F101FG	R5F101GG	R5F101JG	R5F101LG	R5F101MG	R5F101PG	-
96	8 KB	8 KB	R5F100EF	R5F100FF	R5F100GF	R5F100JF	R5F100LF	R5F100MF	R5F100PF	-
KB	_		R5F101EF	R5F101FF	R5F101GF	R5F101JF	R5F101LF	R5F101MF	R5F101PF	_
64	4 KB	4 KB	R5F100EE	R5F100FE	R5F100GE	R5F100JE	R5F100LE	_	_	_
KB	-	Note	R5F101EE	R5F101FE	R5F101GE	R5F101JE	R5F101LE	_	_	_
48	4 KB	3 KB	R5F100ED	R5F100FD	R5F100GD	R5F100JD	R5F100LD	_	_	_
KB	-	Note	R5F101ED	R5F101FD	R5F101GD	R5F101JD	R5F101LD	-	-	-
32	4 KB	2 KB	R5F100EC	R5F100FC	R5F100GC	R5F100JC	R5F100LC	-	-	-
KB	_		R5F101EC	R5F101FC	R5F101GC	R5F101JC	R5F101LC	_	_	-
16	4 KB	2 KB	R5F100EA	R5F100FA	R5F100GA	-	-	-	-	-
KB	-		R5F101EA	R5F101FA	R5F101GA	ı	ı	-	-	_

Note The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C, E to G, J, L): Start address FF300H R5F100xE, R5F101xE (x = 6 to 8, A to C, E to G, J, L): Start address FEF00H R5F100xJ, R5F101xJ (x = F, G, J, L, M, P): Start address FAF00H R5F100xL, R5F101xL (x = F, G, J, L, M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

1.2 List of Part Numbers

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Figure 1-1. Part Number, Memory Size, and Package of RL78/G13



Notes 1. Products only for "A: Consumer applications (T_A = -40 to +85°C)", and "G: Industrial applications (T_A = -40 to +105°C)"

2. Products only for "A: Consumer applications ($T_A = -40$ to +85°C)", and "D: Industrial applications ($T_A = -40$ to +85°C)"

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Table 1-1. List of Ordering Part Numbers

(1/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
20 pins	20-pin plastic LSSOP	Mounted	А	R5F1006AASP, R5F1006CASP, R5F1006DASP, R5F1006EASP	#V0, #10, #30, #X0, #50	PLSP0020JC-A
	(7.62 mm (300),		D	R5F1006ADSP, R5F1006CDSP, R5F1006DDSP, R5F1006EDSP		
	0.65-mm pitch)		G	R5F1006AGSP, R5F1006CGSP, R5F1006DGSP, R5F1006EGSP		
		Not mounted	А	R5F1016AASP, R5F1016CASP, R5F1016DASP, R5F1016EASP	#V0, #10, #30, #X0, #50	PLSP0020JC-A
			D	R5F1016ADSP, R5F1016CDSP, R5F1016DDSP, R5F1016EDSP		
	20-pin plastic TSSOP	Mounted	А	R5F1006AASM, R5F1006CASM, R5F1006DASM, R5F1006EASM	#10, #30, #50	PTSP0020JI-A
	(4.4 x 6.5 mm,		G	R5F1006AGSM, R5F1006CGSM, R5F1006DGSM, R5F1006EGSM		
	0.65-mm pitch)	Not mounted	А	R5F1016AASM, R5F1016CASM, R5F1016DASM, R5F1016EASM		
24	24-pin plastic	Mounted	Α	R5F1007AANA, R5F1007CANA, R5F1007DANA,	#U0, #W0	PWQN0024KE-A
pins	HWQFN			R5F1007EANA	#00, #20, #40	PWQN0024KF-A
	(4 × 4 mm, 0.5-mm		D	R5F1007ADNA, R5F1007CDNA, R5F1007DDNA, R5F1007EDNA	#U0, #W0	PWQN0024KE-A
	pitch)		G	R5F1007AGNA, R5F1007CGNA, R5F1007DGNA, R5F1007EGNA		
				R5F1007AGNA, R5F1007CGNA, R5F1007DGNA, R5F1007EGNA	#00, #20, #40	PWQN0024KF-A
		Not	Α	R5F1017AANA, R5F1017CANA, R5F1017DANA,	#U0, #W0	PWQN0024KE-A
		mounted		R5F1017EANA	#00, #20, #40	PWQN0024KF-A
			D	R5F1017ADNA, R5F1017CDNA, R5F1017DDNA, R5F1017EDNA	#U0, #W0	PWQN0024KE-A
25 pins	25-pin plastic WFLGA	Mounted	A	R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA	#U0, #W0	PWLG0025KA-A
	(3 × 3 mm, 0.5-mm		G	R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA		
	pitch)	Not mounted	А	R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA	#U0, #W0	PWLG0025KA-A

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(2/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
30 pins	30-pin plastic	Mounted	А	R5F100AAASP, R5F100ACASP, R5F100ADASP, R5F100AEASP, R5F100AFASP, R5F100AGASP	#V0, #10, #30, #X0, #50	PLSP0030JB-B
ľ	(7.62 mm		D	R5F100AADSP, R5F100ACDSP, R5F100ADDSP, R5F100AEDSP, R5F100AFDSP, R5F100AGDSP		
	0.65-mm pitch)		G	R5F100AGSP, R5F100ACGSP, R5F100AGGSP, R5F100AGGSP, R5F100AGGSP, R5F100AGGSP		
		Not mounted	A	R5F101AAASP, R5F101ACASP, R5F101ADASP, R5F101AEASP, R5F101AFASP, R5F101AFASP, R5F101AGASP	#V0, #10, #30, #X0, #50	PLSP0030JB-B
			D	R5F101AADSP, R5F101ACDSP, R5F101ADDSP, R5F101AEDSP, R5F101AFDSP, R5F101AGDSP		
32	32-pin plastic	Mounted	Α	R5F100BAANA, R5F100BCANA, R5F100BDANA,	#U0, #W0	PWQN0032KB-A
pins	HWQFN			R5F100BEANA, R5F100BFANA, R5F100BGANA	#00, #20, #40	PWQN0032KE-A
	(5 × 5 mm, 0.5-mm		D	R5F100BADNA, R5F100BCDNA, R5F100BDDNA, R5F100BEDNA, R5F100BFDNA, R5F100BGDNA	#U0, #W0	PWQN0032KB-A
	pitch)		G	R5F100BAGNA, R5F100BCGNA, R5F100BDGNA, R5F100BEGNA, R5F100BFGNA, R5F100BGGNA		
				R5F100BAGNA, R5F100BCGNA, R5F100BDGNA, R5F100BEGNA, R5F100BFGNA, R5F100BGGNA	#00, #20, #40	PWQN0032KE-A
		Not	A	R5F101BAANA, R5F101BCANA, R5F101BDANA,	#U0, #W0	PWQN0032KB-A
		mounted		R5F101BEANA, R5F101BFANA, R5F101BGANA	#00, #20, #40	PWQN0032KE-A
			D	R5F101BADNA, R5F101BCDNA, R5F101BDDNA, R5F101BEDNA, R5F101BFDNA, R5F101BGDNA	#U0, #W0	PWQN0032KB-A
36 pins	36-pin plastic WFLGA	Mounted	А	R5F100CAALA, R5F100CCALA, R5F100CDALA, R5F100CEALA, R5F100CFALA, R5F100CGALA	#U0, #W0	PWLG0036KA-A
	(4 × 4 mm, 0.5-mm		G	R5F100CAGLA, R5F100CCGLA, R5F100CDGLA, R5F100CEGLA, R5F100CFGLA, R5F100CGGLA		
	pitch)	Not mounted	А	R5F101CAALA, R5F101CCALA, R5F101CDALA, R5F101CEALA, R5F101CFALA, R5F101CGALA	#U0, #W0	PWLG0036KA-A

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(3/8)

Pin	Package	Data flash	Fields of	Ordering Part Number		(3/8) RENESAS Code																														
count	3.		Application Note	Product Name	Packaging Specifications																															
40	40-pin	Mounted	А	R5F100EAANA, R5F100ECANA, R5F100EDANA,	#U0, #W0	PWQN0040KC-A																														
pins	plastic HWQFN			R5F100EEANA, R5F100EFANA, R5F100EGANA, R5F100EHANA	#00, #20, #40	PWQN0040KD-A																														
	(6 × 6 mm, 0.5-mm pitch)		D	R5F100EADNA, R5F100ECDNA, R5F100EDDNA, R5F100EEDNA, R5F100EFDNA, R5F100EGDNA, R5F100EHDNA	#U0, #W0	PWQN0040KC-A																														
			G	R5F100EAGNA, R5F100ECGNA, R5F100EDGNA,	#U0, #W0	PWQN0040KC-A																														
				R5F100EEGNA, R5F100EFGNA, R5F100EGGNA, R5F100EHGNA	#00, #20, #40	PWQN0040KD-A																														
		Not	А	R5F101EAANA, R5F101ECANA, R5F101EDANA,	#U0, #W0	PWQN0040KC-A																														
			R5F101EEANA, R5F101EFANA, R5F101EGANA, R5F101EHANA	#00, #20, #40	PWQN0040KD-A																															
			D	R5F101EADNA, R5F101ECDNA, R5F101EDDNA, R5F101EEDNA, R5F101EFDNA, R5F101EGDNA, R5F101EHDNA	#U0, #W0	PWQN0040KC-A																														
44	44-pin	Mounted	А	R5F100FAAFP, R5F100FCAFP, R5F100FDAFP,	#V0, #X0	PLQP0044GC-A																														
pins	plastic LQFP (10 x 10				R5F100FEAFP, R5F100FFAFP, R5F100FGAFP, R5F100FHAFP, R5F100FJAFP, R5F100FLAFP	#10, #30, #50	PLQP0044GC-A/ PLQP0044GC-D																													
	mm,			_																													D	R5F100FADFP, R5F100FCDFP, R5F100FDDFP,	#V0, #X0	PLQP0044GC-A
	0.8-mm pitch)																								R5F100FEDFP, R5F100FFDFP, R5F100FGDFP, R5F100FHDFP, R5F100FJDFP, R5F100FKDFP, R5F100FLDFP	#10, #30, #50	PLQP0044GC-A/ PLQP0044GC-D									
			G	R5F100FAGFP, R5F100FCGFP, R5F100FDGFP,	#V0, #X0	PLQP0044GC-A																														
				R5F100FEGFP, R5F100FGGFP,	#10, #30, #50	PLQP0044GC-A/																														
				R5F100FHGFP, R5F100FJGFP		PLQP0044GC-D																														
		Not	Α	R5F101FAAFP, R5F101FCAFP, R5F101FDAFP,	#V0, #X0	PLQP0044GC-A																														
		mounted		R5F101FEAFP, R5F101FFAFP, R5F101FGAFP,	#10, #30, #50	PLQP0044GC-A/																														
				R5F101FHAFP, R5F101FJAFP, R5F101FKAFP, R5F101FLAFP		PLQP0044GC-D																														
			D	R5F101FADFP, R5F101FCDFP, R5F101FDDFP,	#V0, #X0	PLQP0044GC-A																														
			R5F101FEDFP, R5F101FFDFP, R5F101FGDFP,	#10, #30, #50	PLQP0044GC-A/																															
			1	R5F101FHDFP, R5F101FJDFP, R5F101FKDFP, R5F101FLDFP		PLQP0044GC-D																														

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(4/8)

Pin	Package	Data flash	Fields of	Ordering Part Number		RENESAS Code										
count			Application Note	Product Name	Packaging Specifications											
48	48-pin	Mounted	Α	R5F100GAAFB, R5F100GCAFB, R5F100GDAFB,	#V0, #X0	PLQP0048KF-A										
pins	plastic LFQFP (7 × 7 mm,)FP		R5F100GEAFB, R5F100GFAFB, R5F100GGAFB, R5F100GHAFB, R5F100GJAFB, R5F100GLAFB	#10, #30, #50	PLQP0048KB-B										
	0.5-mm		D	R5F100GADFB, R5F100GCDFB, R5F100GDDFB,	#V0, #X0	PLQP0048KF-A										
	pitch)		G	R5F100GEDFB, R5F100GFDFB, R5F100GGDFB, R5F100GHDFB, R5F100GJDFB, R5F100GKDFB, R5F100GLDFB	#10, #30, #50	PLQP0048KB-B										
				R5F100GAGFB, R5F100GCGFB, R5F100GDGFB,	#V0, #X0	PLQP0048KF-A										
				R5F100GEGFB, R5F100GFGFB, R5F100GHGFB, R5F100GHGFB, R5F100GJGFB	#10, #30, #50	PLQP0048KB-B										
		Not	Α	R5F101GAAFB, R5F101GCAFB, R5F101GDAFB,	#V0, #X0	PLQP0048KF-A										
		mounted		R5F101GEAFB, R5F101GFAFB, R5F101GGAFB, R5F101GHAFB, R5F101GJAFB, R5F101GLAFB	#10, #30, #50	PLQP0048KB-B										
			D	R5F101GADFB, R5F101GCDFB, R5F101GDDFB,	#V0, #X0	PLQP0048KF-A										
				R5F101GEDFB, R5F101GFDFB, R5F101GGDFB, R5F101GHDFB, R5F101GJDFB, R5F101GLDFB	#10, #30, #50	PLQP0048KB-B										
	48-pin Mo	Mounted	А	R5F100GAANA, R5F100GCANA, R5F100GDANA,	#U0, #W0	PWQN0048KB-A										
	plastic HWQFN (7 × 7 mm,	D	R5F100GEANA, R5F100GFANA, R5F100GGANA, R5F100GHANA, R5F100GJANA, R5F100GKANA, R5F100GLANA	#00, #20, #40	PWQN0048KE-A											
	0.5-mm pitch)													D	R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA	#U0, #W0
				R5F100GKDNA, R5F100GLDNA	#00, #20, #40	PWQN0048KE-A										
			G	R5F100GAGNA, R5F100GCGNA, R5F100GDGNA,	#U0, #W0	PWQN0048KB-A										
				R5F100GEGNA, R5F100GFGNA, R5F100GGGNA, R5F100GHGNA, R5F100GJGNA	#00, #20, #40	PWQN0048KE-A										
		Not	Α	R5F101GAANA, R5F101GCANA, R5F101GDANA,	#U0, #W0	PWQN0048KB-A										
		mounted		R5F101GEANA, R5F101GFANA, R5F101GGANA, R5F101GHANA, R5F101GJANA, R5F101GKANA, R5F101GLANA	#00, #20, #40	PWQN0048KE-A										
			D	R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA, R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA	#U0, #W0	PWQN0048KB-A										
				R5F101GKDNA, R5F101GLDNA	#00, #20, #40	PWQN0048KE-A										

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(5/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
pins pla LC (1) m 0.	52-pin plastic LQFP (10 × 10 mm, 0.65-mm pitch)	Mounted	A D G	R5F100JCAFA, R5F100JDAFA, R5F100JEAFA, R5F100JFAFA, R5F100JFAFA, R5F100JJAFA, R5F100JJAFA, R5F100JJAFA, R5F100JCDFA, R5F100JDDFA, R5F100JEDFA, R5F100JFDFA, R5F100JJDFA, R5F100JJDFA, R5F100JJDFA, R5F100JJDFA, R5F100JCGFA, R5F100JDGFA, R5F100JGGFA, R5F100JGGFA, R5F100JJGFA, R5F100JJGFA, R5F100JJGFA	#V0, #10, #30, #X0, #50	PLQP0052JA-A
		Not mounted	A D	R5F101JCAFA, R5F101JDAFA, R5F101JEAFA, R5F101JFAFA, R5F101JGAFA, R5F101JHAFA, R5F101JJAFA, R5F101JJAFA, R5F101JCDFA, R5F101JCDFA, R5F101JCDFA, R5F101JFDFA, R5F101JDFA, R5F101JDFA, R5F101JDFA, R5F101JDFA, R5F101JDFA, R5F101JDFA	#V0, #10, #30, #X0, #50	PLQP0052JA-A

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(6/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
64 pins	64-pin plastic LQFP (12 × 12 mm, 0.65-mm pitch)	Mounted	A D	R5F100LCAFA, R5F100LDAFA, R5F100LEAFA, R5F100LFAFA, R5F100LFAFA, R5F100LJAFA, R5F100LJAFA, R5F100LDFA, R5F100LDFA, R5F100LFDFA, R5F100LFDFA, R5F100LFDFA, R5F100LJDFA, R5F100LJDFA, R5F100LJDFA, R5F100LJDFA, R5F100LJDFA	#V0, #10, #30, #X0, #50	PLQP0064JA-A
			G	R5F100LCGFA, R5F100LDGFA, R5F100LEGFA, R5F100LFGFA, R5F100LGGFA, R5F100LJGFA		
	64-pin plastic LQFP (12 × 12 mm,	Not mounted	A	R5F101LCAFA, R5F101LDAFA, R5F101LEAFA, R5F101LFAFA, R5F101LGAFA, R5F101LHAFA, R5F101LJAFA, R5F101LKAFA, R5F101LLAFA	#V0, #10, #30, #X0, #50	PLQP0064JA-A
	0.65-mm pitch)		D	R5F101LCDFA, R5F101LDDFA, R5F101LEDFA, R5F101LFDFA, R5F101LGDFA, R5F101LHDFA, R5F101LJDFA, R5F101LKDFA, R5F101LLDFA		
	64-pin plastic Mounted LFQFP (10 × 10 mm,		А	R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB, R5F100LLAFB	#V0, #X0 #10, #30, #50	PLQP0064KF-A PLQP0064KB-C
	0.5-mm pitch)		D	R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LFDFB, R5F100LGDFB, R5F100LHDFB, R5F100LJDFB, R5F100LLDFB	#V0, #X0 #10, #30, #50	PLQP0064KF-A PLQP0064KB-C
			G	R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB, R5F100LJGFB	#V0, #X0 #10, #30, #50	PLQP0064KF-A PLQP0064KB-C
		Not mounted	А	R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB, R5F101LJAFB, R5F101LKAFB, R5F101LLAFB	#V0, #X0 #10, #30, #50	PLQP0064KF-A PLQP0064KB-C
			D	R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LFDFB, R5F101LGDFB, R5F101LHDFB, R5F101LJDFB, R5F101LKDFB, R5F101LLDFB	#V0, #X0 #10, #30, #50	PLQP0064KF-A PLQP0064KB-C
	64-pin plastic VFBGA (4 × 4 mm,	Mounted	A	R5F100LCABG, R5F100LDABG, R5F100LEABG, R5F100LFABG, R5F100LGABG, R5F100LHABG, R5F100LJABG	#U0, #W0	PVBG0064LA-A
	0.4-mm pitch)		G	R5F100LCGBG, R5F100LDGBG, R5F100LEGBG, R5F100LFGBG, R5F100LGGBG, R5F100LJGBG		
		Not mounted	A	R5F101LCABG, R5F101LDABG, R5F101LEABG, R5F101LFABG, R5F101LGABG, R5F101LHABG, R5F101LJABG	#U0, #W0	PVBG0064LA-A

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(7/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
80	80-pin plastic	Mounted	Α	R5F100MFAFA, R5F100MGAFA, R5F100MHAFA,	#V0, #10, #30,	PLQP0080JB-E
pins	LQFP			R5F100MJAFA, R5F100MKAFA, R5F100MLAFA	#X0, #50	
	(14 × 14		D	R5F100MFDFA, R5F100MGDFA, R5F100MHDFA,		
	mm,			R5F100MJDFA, R5F100MKDFA, R5F100MLDFA		
	0.65-mm		G	R5F100MFGFA, R5F100MGGFA, R5F100MHGFA,		
	pitch)			R5F100MJGFA		
		Not	Α	R5F101MFAFA, R5F101MGAFA, R5F101MHAFA,	#V0, #10, #30,	PLQP0080JB-E
		mounted		R5F101MJAFA, R5F101MKAFA, R5F101MLAFA	#X0, #50	
			D	R5F101MFDFA, R5F101MGDFA, R5F101MHDFA,		
				R5F101MJDFA, R5F101MKDFA, R5F101MLDFA		
	80-pin plastic	Mounted	Α	R5F100MFAFB, R5F100MGAFB, R5F100MHAFB,	#V0, #X0	PLQP0080KE-A
	LFQFP			R5F100MJAFB, R5F100MKAFB, R5F100MLAFB	#10, #30, #50	PLQP0080KB-B
	(12 × 12		D	R5F100MFDFB, R5F100MGDFB, R5F100MHDFB,	#V0, #X0	PLQP0080KE-A
	mm,			R5F100MJDFB, R5F100MKDFB, R5F100MLDFB	#10, #30, #50	PLQP0080KB-B
	0.5-mm		G	R5F100MFGFB, R5F100MGGFB, R5F100MHGFB,	#V0, #X0	PLQP0080KE-A
	pitch)			R5F100MJGFB	#10, #30, #50	PLQP0080KB-B
		Not	Α	R5F101MFAFB, R5F101MGAFB, R5F101MHAFB,	#V0, #X0	PLQP0080KE-A
		mounted		R5F101MJAFB, R5F101MKAFB, R5F101MLAFB	#10, #30, #50	PLQP0080KB-B
			D	R5F101MFDFB, R5F101MGDFB, R5F101MHDFB,	#V0, #X0	PLQP0080KE-A
				R5F101MJDFB, R5F101MKDFB, R5F101MLDFB	#10, #30, #50	PLQP0080KB-B

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

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Table 1-1. List of Ordering Part Numbers

(8/8)

Pin	Package	Data	Fields of	Ordering Part Number		RENESAS Code
count		flash	Application Note	Product Name	Packaging Specifications	
100	100-pin	Mounted	А	R5F100PFAFB, R5F100PGAFB, R5F100PHAFB,	#V0, #X0	PLQP0100KE-A
pins	plastic			R5F100PJAFB, R5F100PKAFB, R5F100PLAFB	#10, #30, #50	PLQP0100KB-B
	LFQFP		D	R5F100PFDFB, R5F100PGDFB, R5F100PHDFB,	#V0, #X0	PLQP0100KE-A
	(14 × 14 mm,			R5F100PJDFB, R5F100PKDFB, R5F100PLDFB	#10, #30, #50	PLQP0100KB-B
	0.5-mm pitch)		G	R5F100PFGFB, R5F100PGGFB, R5F100PHGFB,	#V0, #X0	PLQP0100KE-A
	pitori)			R5F100PJGFB	#10, #30, #50	PLQP0100KB-B
		Not	Α	R5F101PFAFB, R5F101PGAFB, R5F101PHAFB,	#V0, #X0	PLQP0100KE-A
		mounted		R5F101PJAFB, R5F101PKAFB, R5F101PLAFB	#10, #30, #50	PLQP0100KB-B
			D	R5F101PFDFB, R5F101PGDFB, R5F101PHDFB,	#V0, #X0	PLQP0100KE-A
				R5F101PJDFB, R5F101PKDFB, R5F101PLDFB	#10, #30, #50	PLQP0100KB-B
	100-pin	Mounted	Α	R5F100PFAFA, R5F100PGAFA, R5F100PHAFA,	#V0, #10, #30,	PLQP0100JC-A
	plastic			R5F100PJAFA, R5F100PKAFA, R5F100PLAFA	#X0, #50	
	LQFP		D	R5F100PFDFA, R5F100PGDFA, R5F100PHDFA,		
	(14 × 20 mm,			R5F100PJDFA, R5F100PKDFA, R5F100PLDFA		
	0.65-mm		G	R5F100PFGFA, R5F100PGGFA, R5F100PHGFA,		
	pitch)			R5F100PJGFA		
		Not	Α	R5F101PFAFA, R5F101PGAFA, R5F101PHAFA,	#V0, #10, #30,	PLQP0100JC-A
		mounted		R5F101PJAFA, R5F101PKAFA, R5F101PLAFA	#X0, #50	
			D	R5F101PFDFA, R5F101PGDFA, R5F101PHDFA,		
				R5F101PJDFA, R5F101PKDFA, R5F101PLDFA		
128	128-pin	Mounted	Α	R5F100SHAFB, R5F100SJAFB, R5F100SKAFB,	#V0, #10, #30,	PLQP0128KD-A
pins	plastic			R5F100SLAFB	#X0, #50	
	LFQFP		D	R5F100SHDFB, R5F100SJDFB, R5F100SKDFB,		
	(14 × 20 mm, 0.5-mm			R5F100SLDFB		
	pitch)	Not	Α	R5F101SHAFB, R5F101SJAFB, R5F101SKAFB,	#V0, #10, #30,	PLQP0128KD-A
	piton)	mounted		R5F101SLAFB	#X0, #50	
			D	R5F101SHDFB, R5F101SJDFB, R5F101SKDFB,		
				R5F101SLDFB		

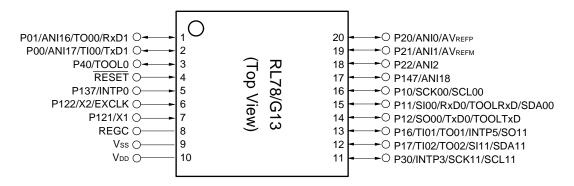
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

1.3 Pin Configuration (Top View)

1.3.1 20-pin products

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- 20-pin plastic LSSOP (7.62 mm (300), 0.65-mm pitch)
- 20-pin plastic TSSOP (4.4 × 6.5 mm, 0.65-mm pitch)

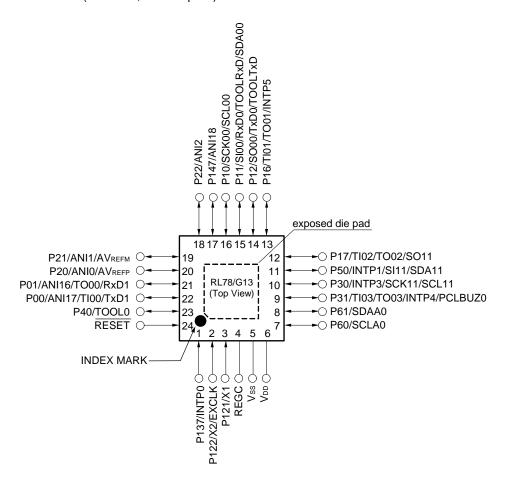


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remark For pin identification, see 1.4 Pin Identification.

1.3.2 24-pin products

• 24-pin plastic HWQFN (4 x 4 mm, 0.5-mm pitch)



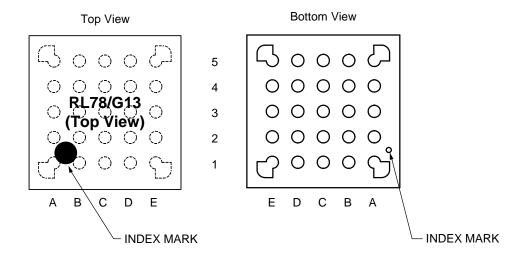
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. It is recommended to connect an exposed die pad to $V_{\mbox{\scriptsize ss}}$.

1.3.3 25-pin products

• 25-pin plastic WFLGA (3 x 3 mm, 0.50-mm pitch)



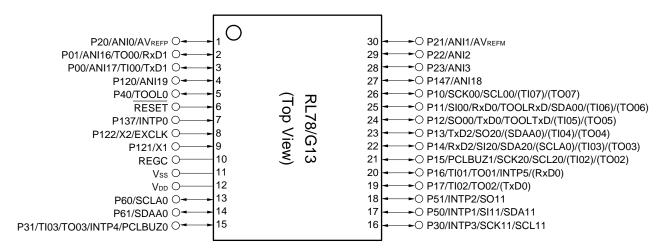
	Α	В	С	D	E	
5	P40/TOOL0	RESET	P01/ANI16/ TO00/RxD1	P22/ANI2	P147/ANI18	5
4	P122/X2/ EXCLK	P137/INTP0	P00/ANI17/ TI00/TxD1	P21/ANI1/ AV _{REFM}	P10/SCK00/ SCL00	4
3	P121/X1	V _{DD}	P20/ANI0/ AVREFP	P12/SO00/ TxD0/ TOOLTxD	P11/SI00/ RxD0/ TOOLRxD/ SDA00	3
2	REGC	Vss	P30/INTP3/ SCK11/SCL11	P17/Tl02/ TO02/SO11	P50/INTP1/ SI11/SDA11	2
1	P60/SCLA0	P61/SDAA0	P31/TI03/ TO03/INTP4/ PCLBUZ0	P16/TI01/ TO01/INTP5	P130	1
	A	В	С	D	Е	•

Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remark For pin identification, see 1.4 Pin Identification.

1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65-mm pitch)



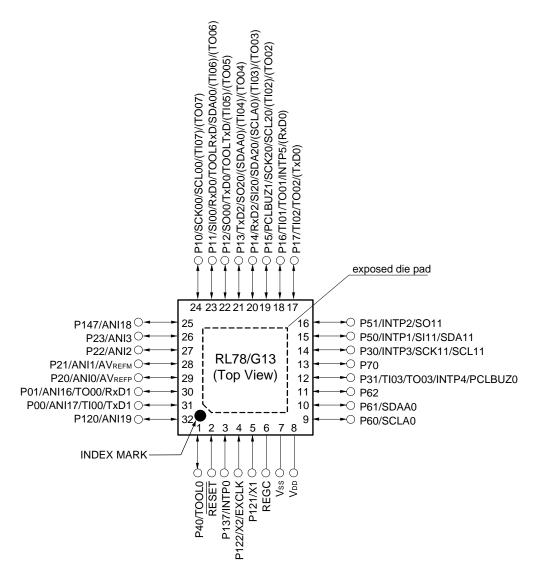
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.5 32-pin products

• 32-pin plastic HWQFN (5 x 5 mm, 0.5-mm pitch)



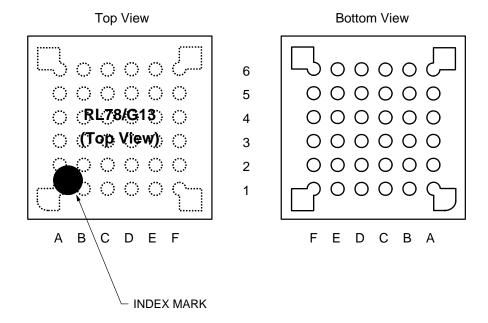
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.

1.3.6 36-pin products

• 36-pin plastic WFLGA (4 × 4 mm, 0.5-mm pitch)



	Α	В	С	D	E	F	
6	P60/SCLA0	V _{DD}	P121/X1	P122/X2/EXCLK	P137/INTP0	P40/TOOL0	6
5	P62	P61/SDAA0	Vss	REGC	RESET	P120/ANI19	5
4	P72/SO21	P71/SI21/ SDA21	P14/RxD2/SI20/ SDA20/(SCLA0) /(TI03)/(TO03)	P31/TI03/TO03/ INTP4/ PCLBUZ0	P00/Tl00/TxD1	P01/TO00/RxD1	4
3	P50/INTP1/ SI11/SDA11	P70/SCK21/ SCL21	P15/PCLBUZ1/ SCK20/SCL20/ (TI02)/(TO02)	P22/ANI2	P20/ANI0/ AV _{REFP}	P21/ANI1/ AVREFM	3
2	P30/INTP3/ SCK11/SCL11	P16/TI01/TO01/ INTP5/(RxD0)	P12/SO00/ TxD0/TOOLTxD /(TI05)/(TO05)	P11/SI00/RxD0/ TOOLRxD/ SDA00/(TI06)/ (TO06)	P24/ANI4	P23/ANI3	2
1	P51/INTP2/ SO11	P17/Tl02/TO02/ (TxD0)	P13/TxD2/ SO20/(SDAA0)/ (TI04)/(TO04)	P10/SCK00/ SCL00/(TI07)/ (TO07)	P147/ANI18	P25/ANI5	1
	Α	В	С	D	Е	F	•

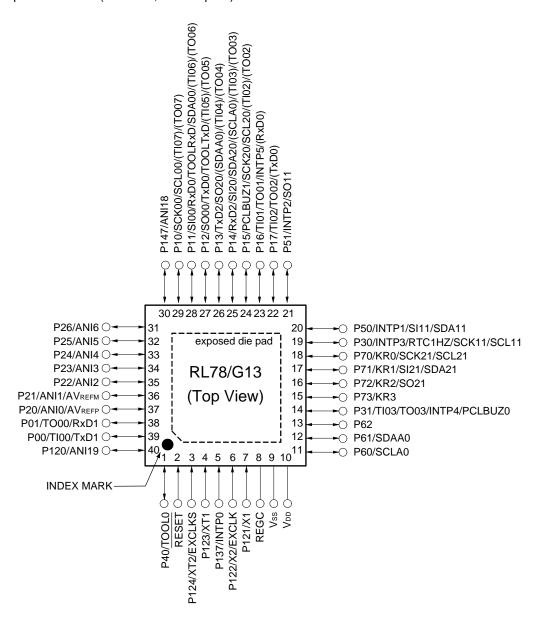
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.7 40-pin products

• 40-pin plastic HWQFN (6 x 6 mm, 0.5-mm pitch)



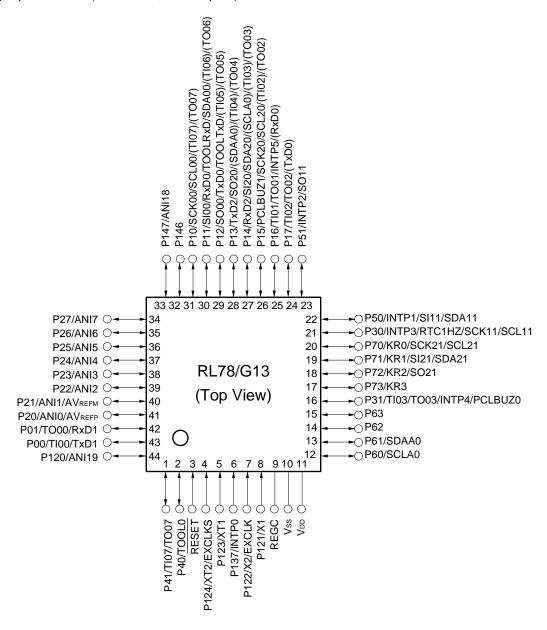
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{\mbox{\scriptsize ss}}$.

1.3.8 44-pin products

• 44-pin plastic LQFP (10 x 10 mm, 0.8-mm pitch)



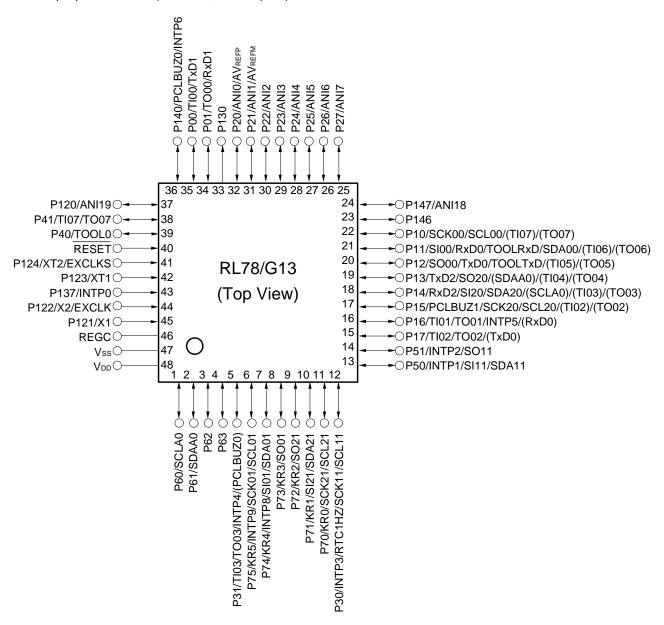
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.9 48-pin products

• 48-pin plastic LFQFP (7 x 7 mm, 0.5-mm pitch)

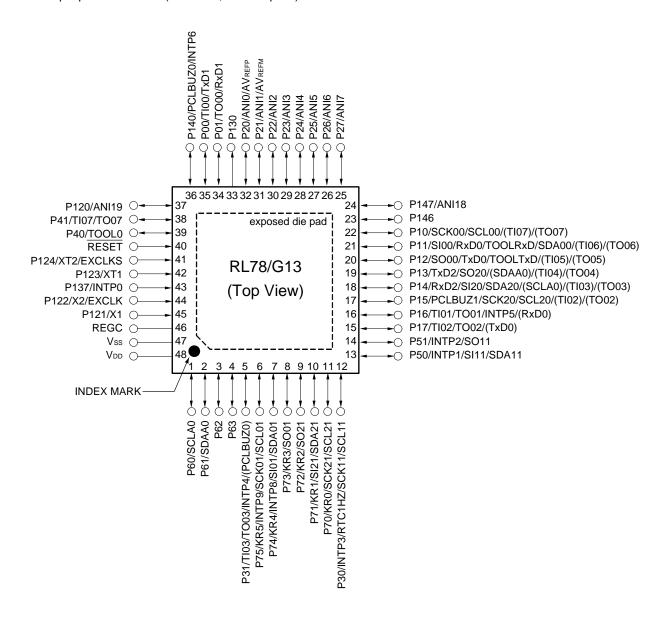


Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

 Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

• 48-pin plastic HWQFN (7 x 7 mm, 0.5-mm pitch)



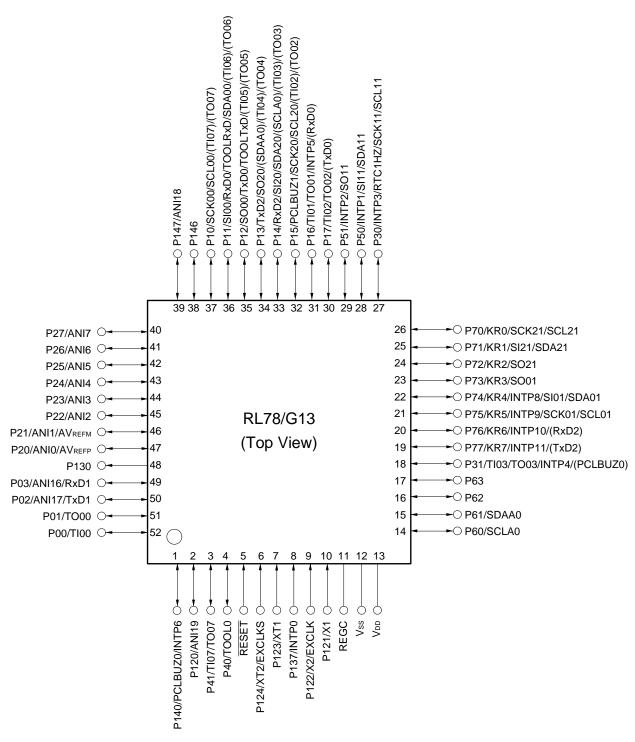
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.

1.3.10 52-pin products

• 52-pin plastic LQFP (10 x 10 mm, 0.65-mm pitch)



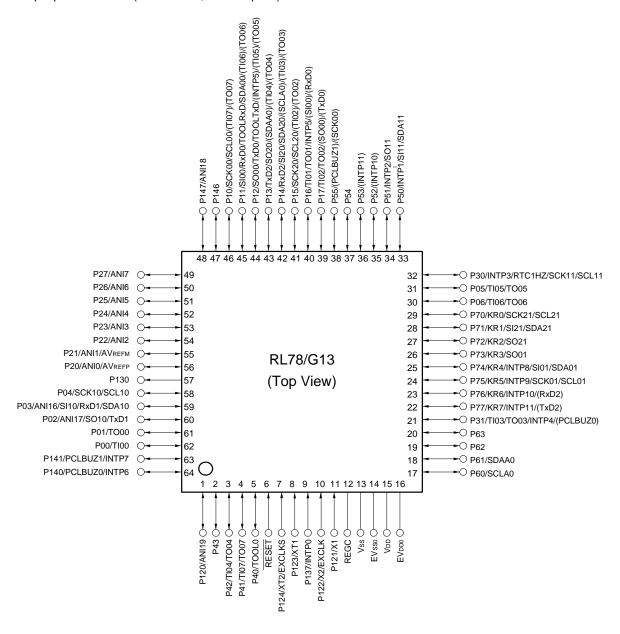
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 µF).

Remarks 1. For pin identification, see 1.4 Pin Identification.

2. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

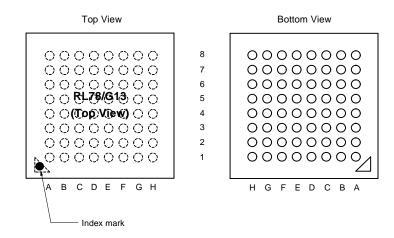
1.3.11 64-pin products

- 64-pin plastic LQFP (12 x 12 mm, 0.65-mm pitch)
- 64-pin plastic LFQFP (10 x 10 mm, 0.5-mm pitch)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is no less than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EV_{SS0} pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

• 64-pin plastic VFBGA (4 × 4 mm, 0.4-mm pitch)



Pin No.	Name	Pin No.	Name	Pin No.	Name	Pin No.	Name
A1	P05/TI05/TO05	C1	P51/INTP2/SO11	E1	P13/TxD2/SO20/ (SDAA0)/(TI04)/(TO04)	G1	P146
A2	P30/INTP3/RTC1HZ /SCK11/SCL11	C2	P71/KR1/SI21/SDA21	E2	P14/RxD2/SI20/SDA20 /(SCLA0)/(TI03)/(TO03)	_	P25/ANI5
А3	P70/KR0/SCK21 /SCL21	C3	P74/KR4/INTP8/SI01 /SDA01	E3	P15/SCK20/SCL20/ (TI02)/(TO02)	G3	P24/ANI4
A4	P75/KR5/INTP9 /SCK01/SCL01	C4	P52/(INTP10)	E4	P16/TI01/TO01/INTP5 /(SI00)/(RxD0)	G4	P22/ANI2
A5	P77/KR7/INTP11/ (TxD2)	C5	P53/(INTP11)	E5	P03/ANI16/SI10/RxD1 /SDA10	G5	P130
A6	P61/SDAA0	C6	P63	E6	P41/TI07/TO07	G6	P02/ANI17/SO10/TxD1
A7	P60/SCLA0	C7	Vss	E7	RESET	G7	P00/TI00
A8	EVDD0	C8	P121/X1	E8	P137/INTP0	G8	P124/XT2/EXCLKS
B1	P50/INTP1/SI11 /SDA11	D1	P55/(PCLBUZ1)/ (SCK00)	F1	P10/SCK00/SCL00/ (TI07)/(TO07)	H1	P147/ANI18
B2	P72/KR2/SO21	D2	P06/TI06/TO06	F2	P11/SI00/RxD0 /TOOLRxD/SDA00/ (TI06)/(TO06)	H2	P27/ANI7
В3	P73/KR3/SO01	D3	P17/TI02/TO02/ (SO00)/(TxD0)	F3	P12/SO00/TxD0 /TOOLTxD/(INTP5)/	НЗ	P26/ANI6
					(TI05)/(TO05)		
B4	P76/KR6/INTP10/ (RxD2)	D4	P54	F4	P21/ANI1/AVREFM	H4	P23/ANI3
B5	P31/TI03/TO03 /INTP4/(PCLBUZ0)	D5	P42/TI04/TO04	F5	P04/SCK10/SCL10	H5	P20/ANI0/AVREFP
B6	P62	D6	P40/TOOL0	F6	P43	H6	P141/PCLBUZ1/INTP7
B7	V _{DD}	D7	REGC	F7	P01/TO00	H7	P140/PCLBUZ0/INTP6
В8	EVsso	D8	P122/X2/EXCLK	F8	P123/XT1	H8	P120/ANI19

Cautions 1. Make EVsso pin the same potential as Vss pin.

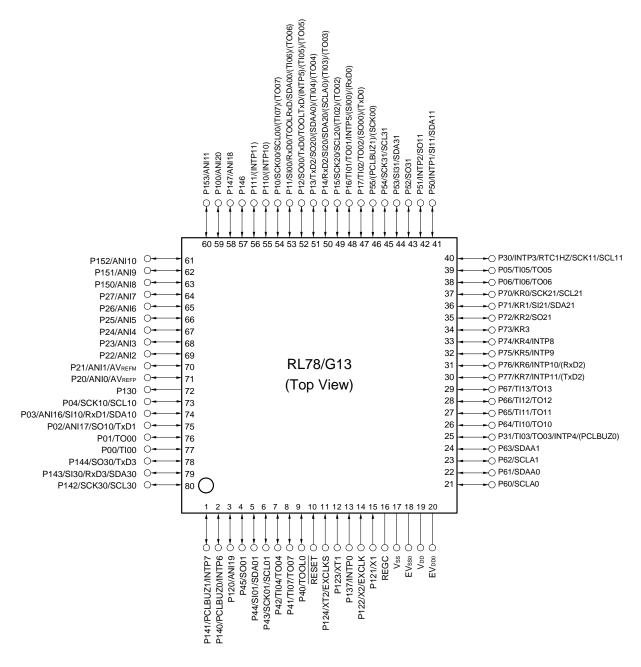
- 2. Make VDD pin the potential that is no less than EVDD0 pin.
- 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EVsso pins to separate ground lines.
- **3.** Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.3.12 80-pin products

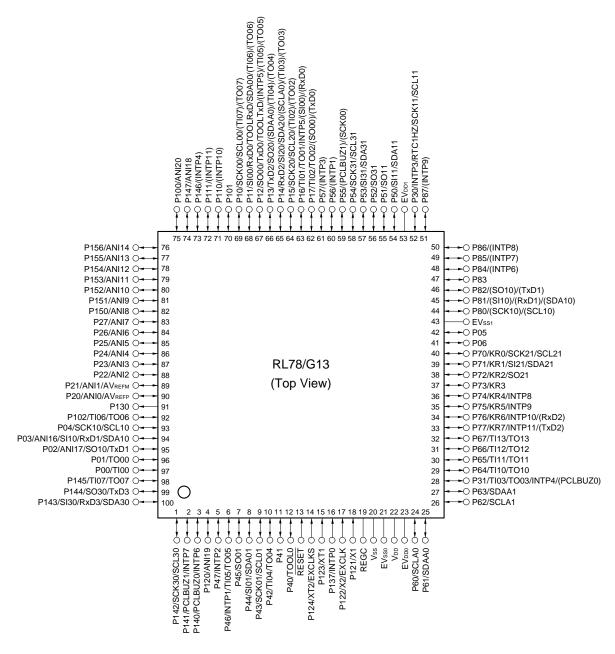
- 80-pin plastic LQFP (14 x 14 mm, 0.65-mm pitch)
- 80-pin plastic LFQFP (12 x 12 mm, 0.5-mm pitch)



- Cautions 1. Make EVsso pin the same potential as Vss pin.
 - 2. Make VDD pin the potential that is no less than EVDDO pin.
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD} and EV_{DD0} pins and connect the Vss and EVsso pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

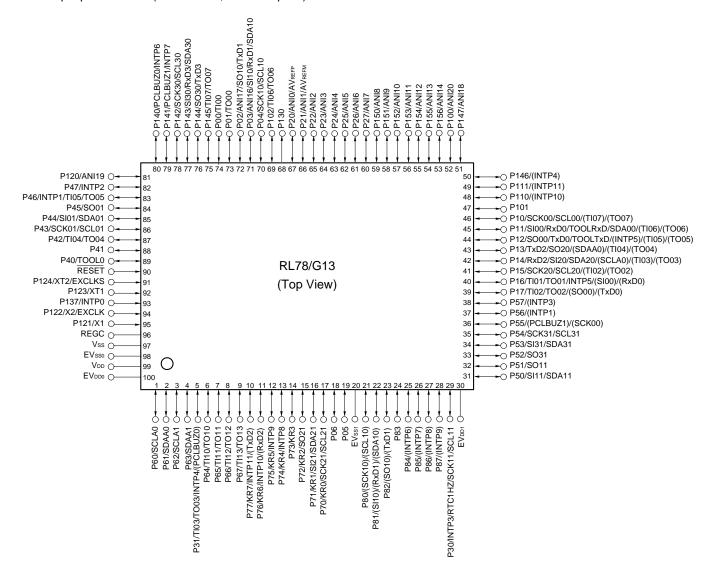
1.3.13 100-pin products

• 100-pin plastic LFQFP (14 x 14 mm, 0.5-mm pitch)



- Cautions 1. Make EVsso and EVsso pins the same potential as Vss pin.
 - 2. Make VDD pin the potential that is no less than EVDD0 and EVDD1 pins (EVDD0 = EVDD1).
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the Vss, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 - Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

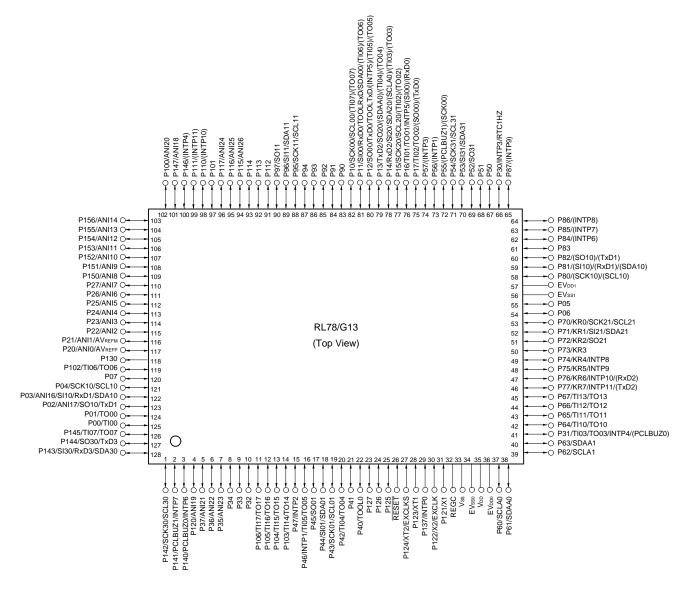
• 100-pin plastic LQFP (14 × 20 mm, 0.65-mm pitch)



- Cautions 1. Make EVsso and EVsso pins the same potential as Vss pin.
 - 2. Make VDD pin the potential that is no less than EVDD0 and EVDD1 pins (EVDD0 = EVDD1).
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the VDD, EVDD0 and EVDD1 pins and connect the Vss, EVsso and EVss1 pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.14 128-pin products

• 128-pin plastic LFQFP (14 x 20 mm, 0.5-mm pitch)



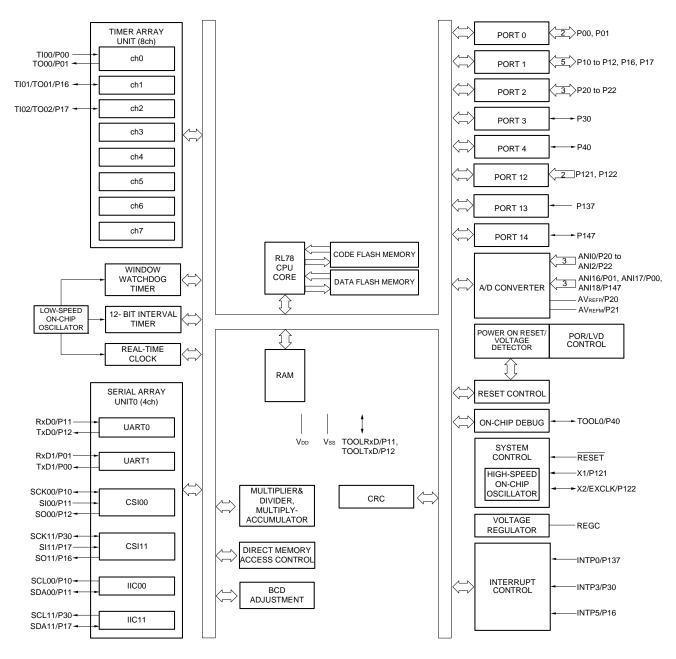
- Cautions 1. Make EVsso and EVss1 pins the same potential as Vss pin.
 - 2. Make Vod pin the potential that is no less than EVDD0 and EVDD1 pins (EVDD0 = EVDD1).
 - 3. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).
- Remarks 1. For pin identification, see 1.4 Pin Identification.
 - 2. When using the microcontroller for an application where the noise generated inside the microcontroller must be reduced, it is recommended to supply separate powers to the V_{DD}, EV_{DD0} and EV_{DD1} pins and connect the Vss, EV_{SS0} and EV_{SS1} pins to separate ground lines.
 - 3. Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.4 Pin Identification

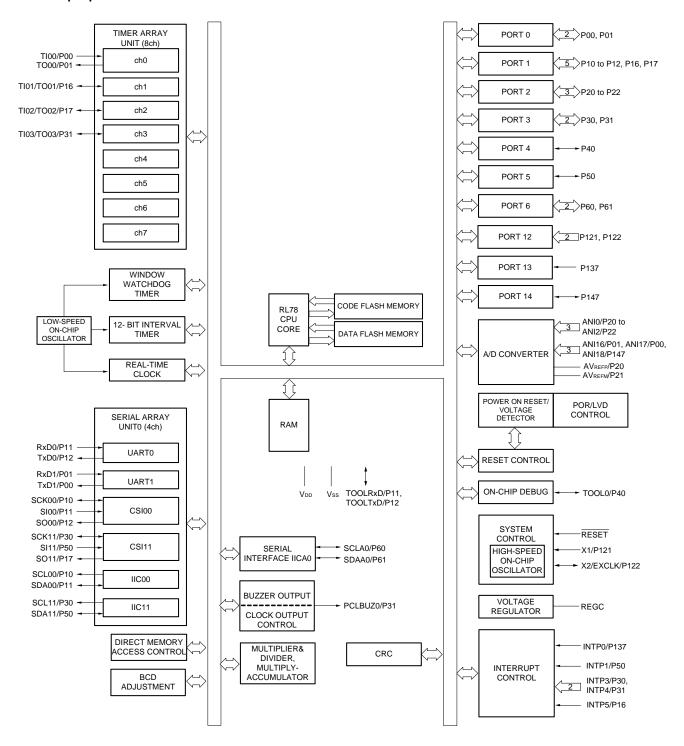
ANI0 to ANI14,		REGC:	Regulator capacitance
ANI16 to ANI26:	Analog input	RESET:	Reset
AVREFM:	A/D converter reference	RTC1HZ:	Real-time clock correction clock
	potential (- side) input		(1 Hz) output
AVREFP:	A/D converter reference	RxD0 to RxD3:	Receive data
	potential (+ side) input	SCLA0, SCLA1,	
EVDD0, EVDD1:	Power supply for port	SCK00, SCK01, SCK10,	
EVsso, EVss1:	Ground for port	SCK11, SCK20, SCK21,	
EXCLK:	External clock input (Main	SCK30, SCK31:	Serial clock input/output
	system clock)	SCL00, SCL01, SCL10,	
EXCLKS:	External clock input	SCL11, SCL20, SCL21,	
	(Subsystem clock)	SCL30, SCL31:	Serial clock output
INTP0 to INTP11:	Interrupt request from	SDAA0, SDAA1, SDA00,	
	peripheral	SDA01,SDA10, SDA11,	
KR0 to KR7:	Key return	SDA20,SDA21, SDA30,	
P00 to P07:	Port 0	SDA31:	Serial data input/output
P10 to P17:	Port 1	SI00, SI01, SI10, SI11,	
P20 to P27:	Port 2	SI20, SI21, SI30, SI31:	Serial data input
P30 to P37:	Port 3	SO00, SO01, SO10,	
P40 to P47:	Port 4	SO11, SO20, SO21,	
P50 to P57:	Port 5	SO30, SO31:	Serial data output
P60 to P67:	Port 6	TI00 to TI07,	
P70 to P77:	Port 7	TI10 to TI17:	Timer input
P80 to P87:	Port 8	TO00 to TO07,	
P90 to P97:	Port 9	TO10 to TO17:	Timer output
P100 to P106:	Port 10	TOOL0:	Data input/output for tool
P110 to P117:	Port 11	TOOLRxD, TOOLTxD:	Data input/output for external device
P120 to P127:	Port 12	TxD0 to TxD3:	Transmit data
P130, P137:	Port 13	V _{DD} :	Power supply
P140 to P147:	Port 14	Vss:	Ground
P150 to P156:	Port 15	X1, X2:	Crystal oscillator (main system clock)
PCLBUZ0, PCLBUZ1:	Programmable clock	XT1, XT2:	Crystal oscillator (subsystem clock)
	output/buzzer output		

1.5 Block Diagram

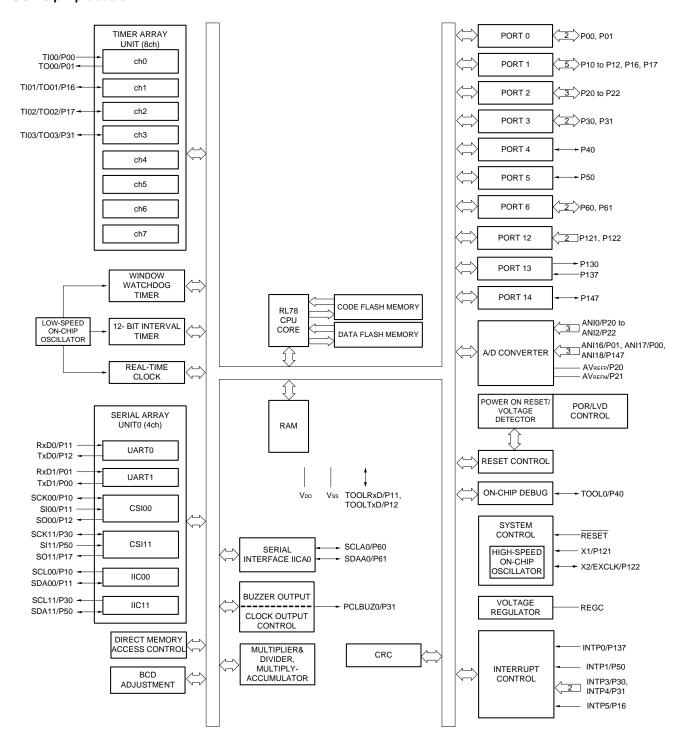
1.5.1 20-pin products



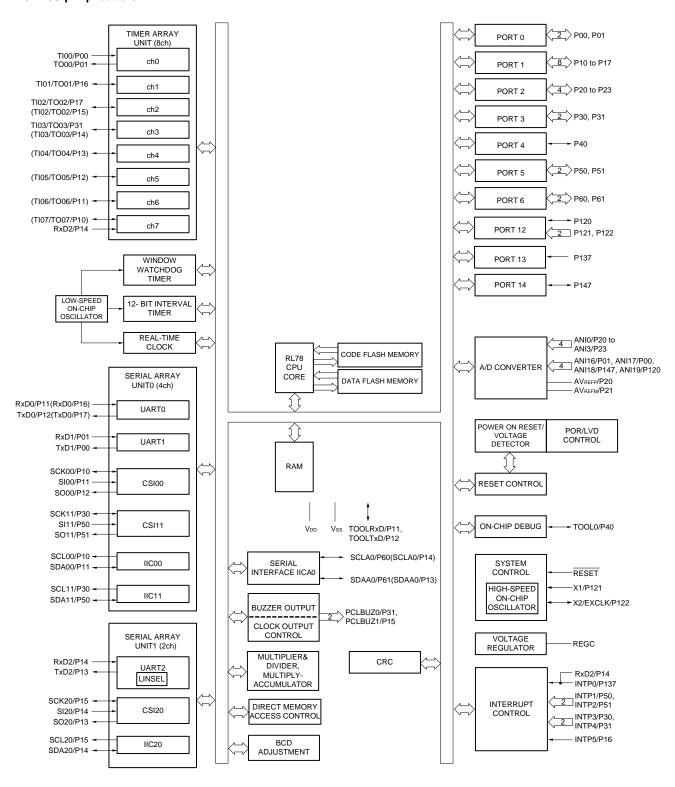
1.5.2 24-pin products



1.5.3 25-pin products

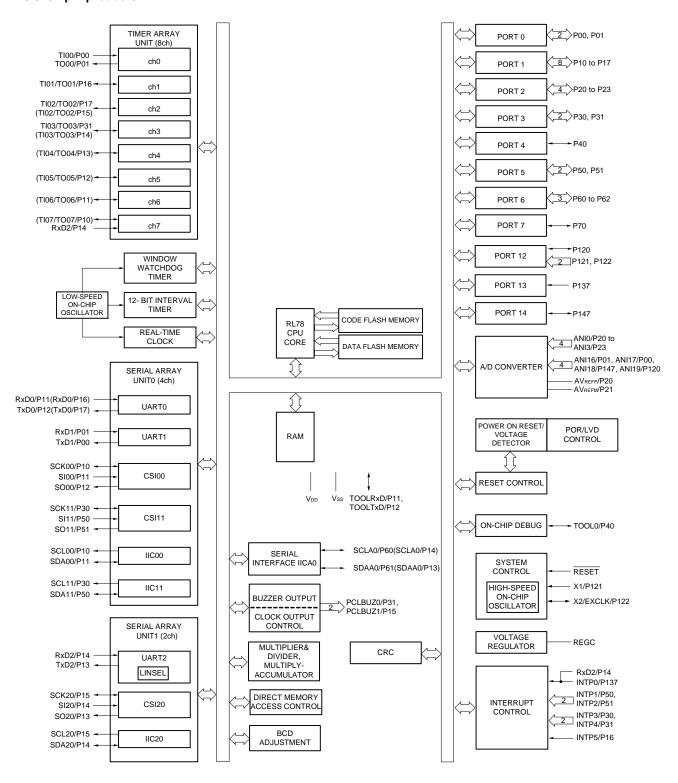


1.5.4 30-pin products



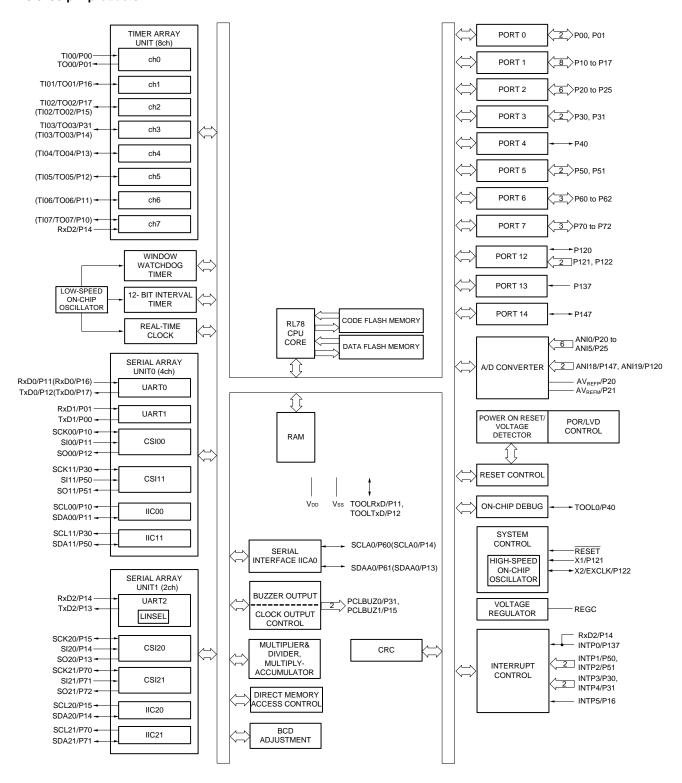
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.5 32-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

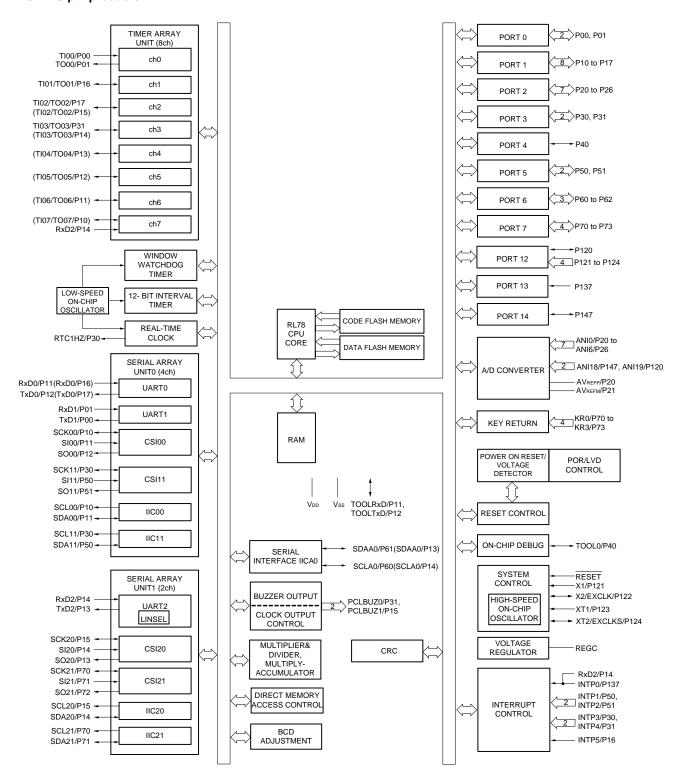
1.5.6 36-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

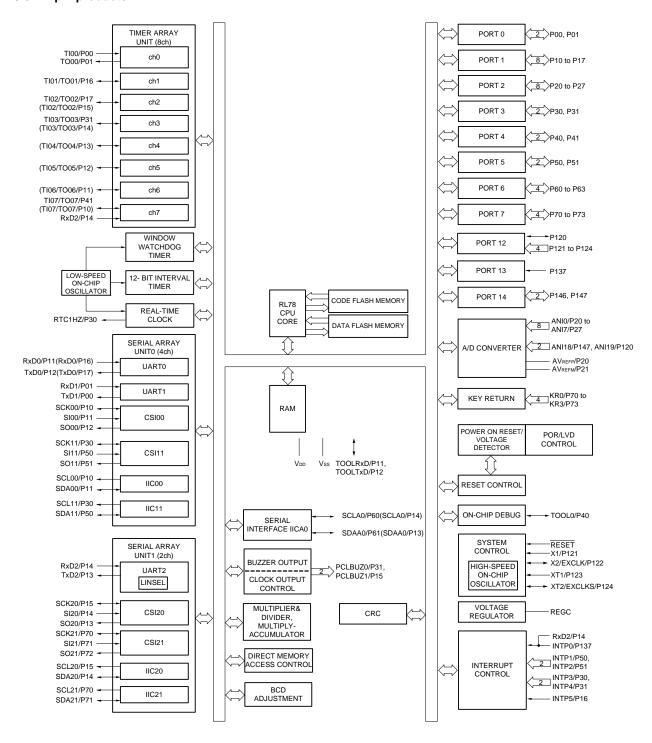
1. OUTLINE RL78/G13

1.5.7 40-pin products



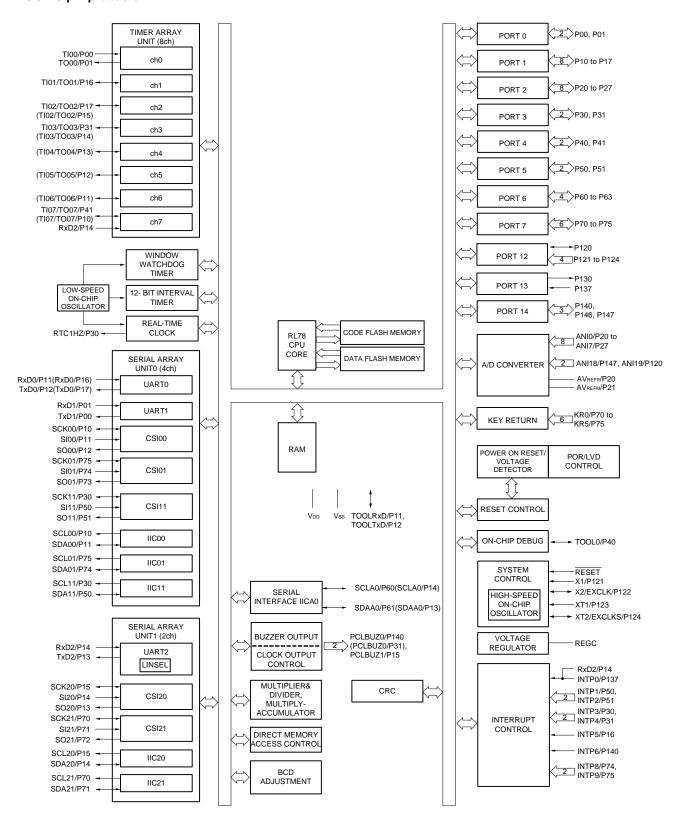
Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection Remark register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.8 44-pin products



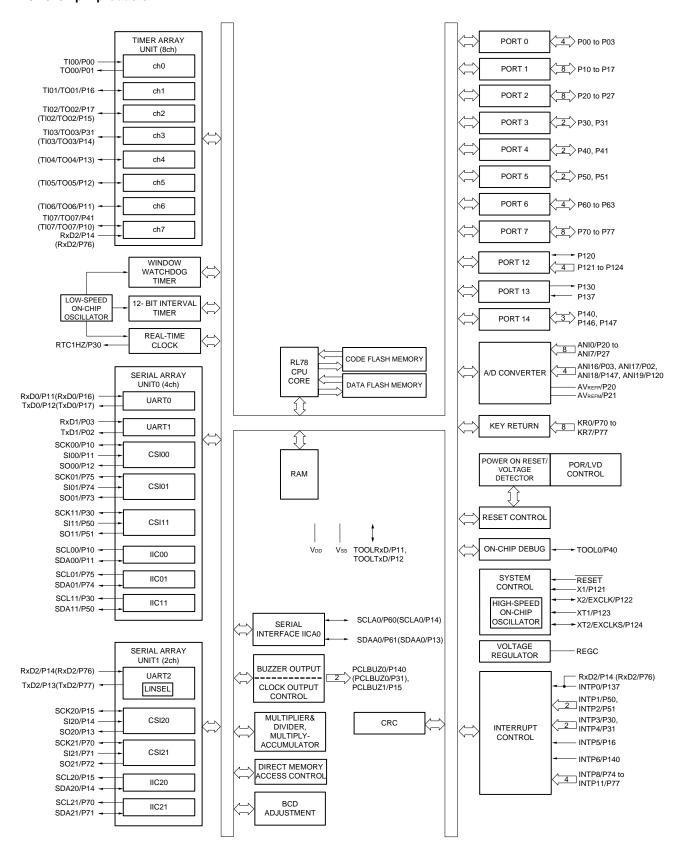
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.5.9 48-pin products



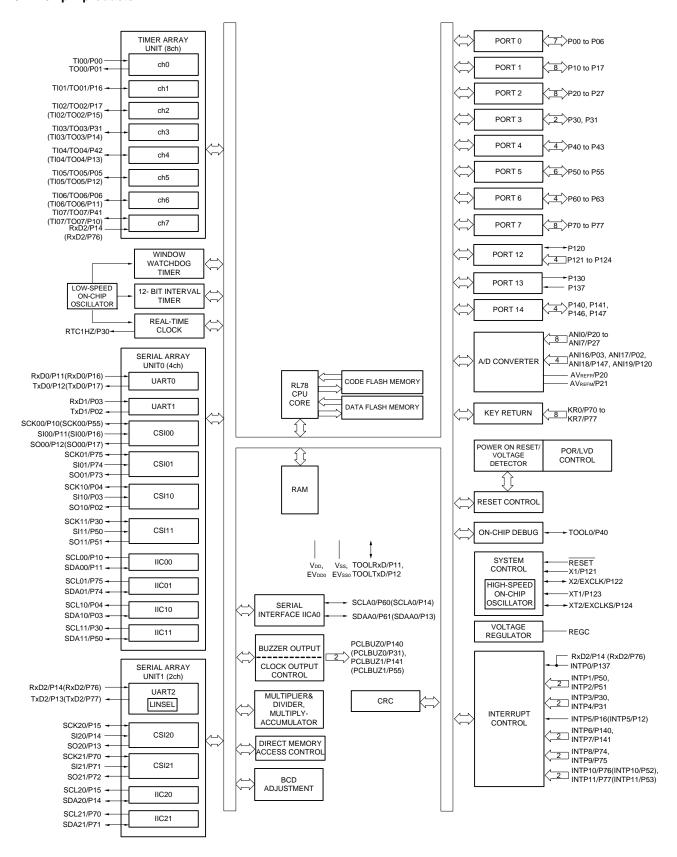
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.10 52-pin products



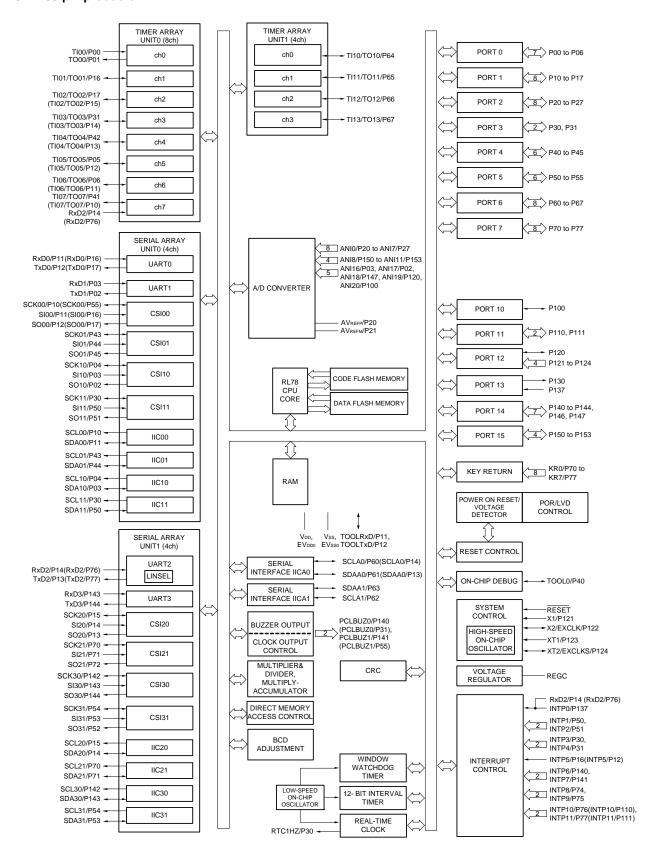
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.11 64-pin products



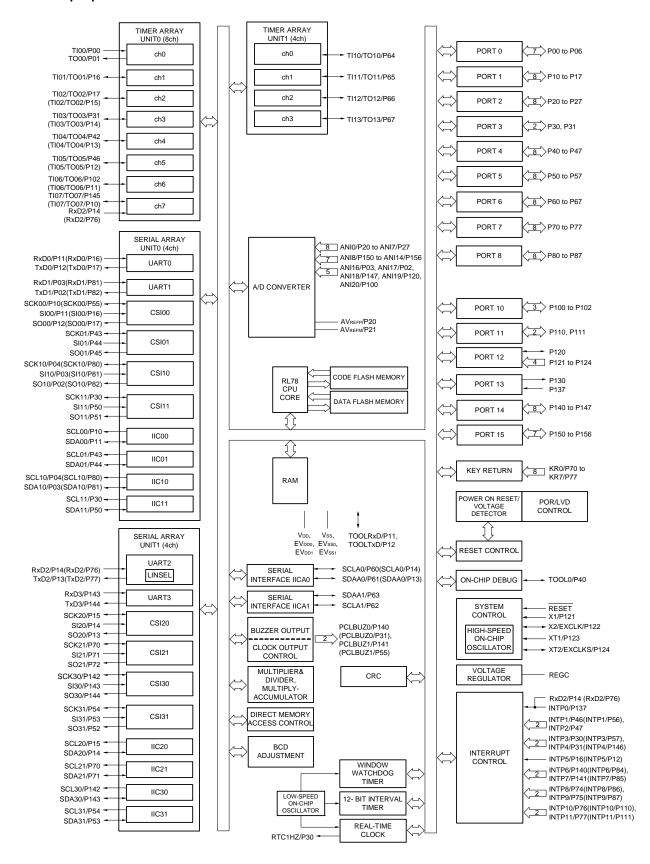
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.12 80-pin products



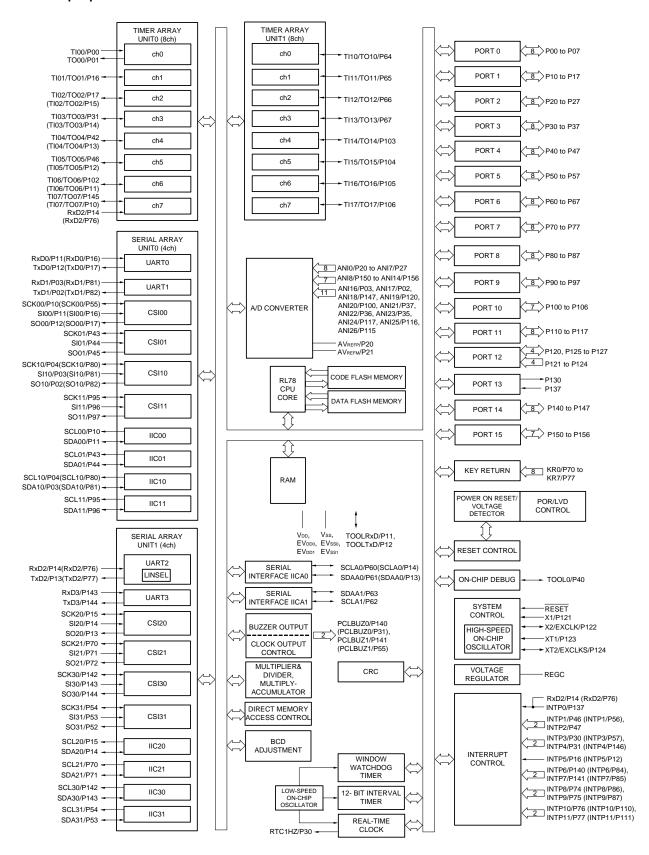
Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.13 100-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to **Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR)** in the RL78/G13 User's Manual.

1.5.14 128-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.6 Outline of Functions

[20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

		ı		ı		1							(1/2)
	Item	20-		24-ן	pin	25	-pin		pin		pin	36-	
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Code flash me	emory (KB)	16 to	64	16 to	64	16 1	o 64	16 to	128	16 to	128	16 to	128
Data flash me	emory (KB)	4	-	4	-	4	-	4 to 8	_	4 to 8	-	4 to 8	-
RAM (KB)		2 to 4	2 to 4 ^{Note1} 2 to 4 ^{Note1} 2 to 4 ^{Note1} 2 to 12 ^N								2 ^{Note1}		
Address spac	е	1 MB											
Main system clock	High-speed system clock	HS (Hig HS (Hig LS (Low	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V_{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)										
	High-speed on-chip oscillator	HS (Hig	IS (High-speed main) mode: 1 to 32 MHz (V_{DD} = 2.7 to 5.5 V), IS (High-speed main) mode: 1 to 16 MHz (V_{DD} = 2.4 to 5.5 V), IS (Low-speed main) mode: 1 to 8 MHz (V_{DD} = 1.8 to 5.5 V), IN (Low-voltage main) mode: 1 to 4 MHz (V_{DD} = 1.6 to 5.5 V)										
Subsystem cle	ock						_	-					
Low-speed or	n-chip oscillator	15 kHz	15 kHz (TYP.)										
General-purpo	ose registers	(8-bit re	gister ×	8) × 4 ba	nks								
Minimum instr	ruction execution time	0.03125	μs (Hig	h-speed	on-chip	oscillato	or: fін = 3	2 MHz o	peration)			
		0.05 µs	(High-sp	peed syst	tem cloc	:k: fмx =	20 MHz	operatio	n)				
Instruction set	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 											
I/O port	Total	10	6	20	0	2	21	2	6	2	8	3	2
	CMOS I/O	1; (N-ch C [V _{DD} wit voltag	D.D. I/O chstand	15 (N-ch O [V _{DD} wit voltag	D.D. I/O hstand	(N-ch (5 D.D. I/O thstand ge]: 6)	2 (N-ch C [V _{DD} wi voltag	D.D. I/O thstand	(N-ch C [V _{DD} wire voltage	thstand	(N-ch C [V _{DD} wi ⁻ voltag	D.D. I/O thstand
	CMOS input	3	3	3			3	3	3	3	3	3	3
	CMOS output	_	-	_	_		1	-	_	-	_	-	_
	N-ch O.D. I/O (withstand voltage: 6 V)	_	-	2	2		2	2	2	3	3	3	3
Timer	16-bit timer						8 cha	nnels					
	Watchdog timer						1 cha	nnel					
	Real-time clock (RTC)						1 chanr	nel Note 2					
	12-bit interval timer (IT)						1 cha	nnel					
	Timer output		3 channels 4 channels 4 channels (PWM outputs: 3 Note 3), (PWM outputs: 3 Note 3) 8 channels (PWM outputs: 7 Note 3) Note 3)							,			
	RTC output						-	-					

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = 6 to 8, A to C): Start address FF300H

R5F100xE, R5F101xE (x = 6 to 8, A to C): Start address FEF00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Notes 2. Only the constant-period interrupt function when the low-speed on-chip oscillator clock (fill) is selected

3. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

4. When setting to PIOR = 1

(2/2)

1.		00		0.1	-:-	0.5		000		00		00	(2/2)
lte:	m	20-	pin	24-	pin	25-	-pin	30-	-pin	32	-pin	36	-pin
		R5F1006x	R5F1016x	R5F1007x	R5F1017x	R5F1008x	R5F1018x	R5F100Ax	R5F101Ax	R5F100Bx	R5F101Bx	R5F100Cx	R5F101Cx
Clock output/buzze	er output		_		1		1		2	2 2			2
		• 2.44	kHz, 4.8	38 kHz, 9	.76 kHz	, 1.25 MI	Hz, 2.5 N	/Hz, 5 N	IHz, 10 l	ИНz			
		(Maiı	n system	n clock: f	MAIN = 20	MHz op	eration)						
8/10-bit resolution	A/D converter	6 chanr	6 channels 6 channels 6 channels 8 channels 8 channels 8 channels								nels		
Serial interface		[20-pin,	24-pin,	25-pin p	roducts]								
		• CSI:	1 chann	el/simpli	fied I ² C:	1 chann	el/UART	: 1 chan	nel				
		• CSI:	1 chann	el/simpli	fied I ² C:	1 chann	el/UART	: 1 chan	nel				
		[30-pin,	32-pin	products]								
				nel/simpli									
				nel/simpli nel/simpli						na I IN-h	nus): 1 ch	nannel	
			product			r onami	0,0,111	(0/11/1	очрроги		, ao _j . 1 oi	iai ii ioi	
		 CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel 											
		CSI: 1 channel/simplified I ² C: 1 channel/UART: 1 channel											
		• CSI:	2 chann	els/simp	lified I ² C	: 2 chan	nels/UAI	RT (UAR	T suppo	rting LIN	N-bus): 1	channel	
	I ² C bus		_	1 chanı	nel	1 chan	nel	1 chan	nel	1 chan	nel	1 channel	
Multiplier and divid	er/multiply-			its = 32		-	r signed)						
accumulator		 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 											
DMA controller		2 channels											
Vectored interrupt	Internal		23	2	24	2	24	2	 27		 27		 27
sources	External		3		- · · · · · · · · · · · · · · · · · · ·		5		6		6		6
Key interrupt								_					
Reset		• Rese	et by RF	SET pin									
			-	t by watc	hdog tin	ner							
				t by pow									
				t by volta t by illega	-		oution No	ote					
				t by lilego t by RAM			Cullon						
				t by illega			ss						
Power-on-reset cir	cuit	_	er-on-re		I.51 V (T								
		• Pow	er-down	-reset: 1	1.50 V (T	YP.)							
Voltage detector			ng edge ng edge				(14 stage (14 stage	,					
On-chip debug fun	ction	Provide	ed										
Power supply volta	ige	V _{DD} = 1	.6 to 5.5	V (T _A =	-40 to +	85°C)							
		$V_{DD} = 2$.4 to 5.5	V (T _A =	-40 to +	105°C)							
Operating ambient	T _A = 40 to +85°C (A: Consumer applications, D: Industrial applications)												
		T _A = 40 to +105°C (G: Industrial applications)											

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Item	40-	·pin	44	-pin	48-	·pin	52-	-pin	64-	(1/2) pin		
	item		<u>. </u>		i 		İ						
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx		
Code flash me	emory (KB)	16 t	o 192	16 t	o 512	16 to	o 512	32 t	o 512	32 to	32 to 512		
Data flash me	emory (KB)	4 to 8	-	4 to 8	-	4 to 8	-	4 to 8	-	4 to 8	-		
RAM (KB)		2 to 1	6 ^{Note1}	2 to 3	32 ^{Note1}	2 to 3	2 ^{Note1}	2 to 3	32 ^{Note1}	2 to 3	2 ^{Note1}		
Address space	e	1 MB											
Main system clock	High-speed system clock	HS (High HS (High LS (Low-	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (Vpp = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (Vpp = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (Vpp = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (Vpp = 1.6 to 5.5 V)										
	High-speed on-chip oscillator	HS (High LS (Low-	S (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), S (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), S (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), / (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)										
Subsystem cl	ock	XT1 (crys 32.768 k	,	ation, exte	ernal subsy	stem cloc	k input (E	XCLKS)					
Low-speed or	n-chip oscillator	15 kHz (TYP.)										
General-purp	ose registers	(8-bit reg	ister × 8)	× 4 banks									
Minimum insti	ruction execution time	0.03125	μs (High-s	speed on-	chip oscilla	ator: fih = 3	2 MHz op	eration)					
		0.05 µs (High-spee	ed system	clock: fmx	= 20 MHz	operation)					
		30.5 µs (Subsyster	n clock: fs	uв = 32.76	8 kHz ope	ration)						
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 											
I/O port	Total	3	36	4	40	4	14	4	48	Ę	58		
	CMOS I/O	(N-ch (28 O.D. I/O ithstand ge]: 10)	(N-ch [V _{DD} w	31 O.D. I/O ithstand ge]: 10)	(N-ch (34 O.D. I/O ithstand ge]: 11)	(N-ch (38 O.D. I/O ithstand ge]: 13)	(N-ch (18 O.D. I/O ithstand ge]: 15)		
	CMOS input		5		5		5		5		5		
	CMOS output		_		_		1		1		1		
	N-ch O.D. I/O (withstand voltage: 6 V)		3		4		4		4		4		
Timer	16-bit timer					8 cha	nnels						
	Watchdog timer					1 cha	annel						
	Real-time clock (RTC)					1 cha	annel						
	12-bit interval timer (IT)					1 cha	annel						
	Timer output	4 channels outputs: 3 8 channels outputs: 7	Note 2), s (PWM			utputs: 4 ^N utputs: 7 ^N				8 channel outputs:			
	RTC output	1 channe • 1 Hz (n clock: fst	лв = 32.768	8 kHz)							

Notes 1.

↑ 1 Hz (subsystem clock: 15∪B = 32.768 kHz)

The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xD, R5F101xD (x = E to G, J, L): Start address FF300H

R5F100xE, R5F101xE (x = E to G, J, L): Start address FEF00H

R5F100xJ, R5F101xJ (x = F, G, J, L): Start address FAF00H

R5F100xL, R5F101xL (x = F, G, J, L): Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see $6.9.3\,$ Operation as multiple PWM output function in the RL78/G13 User's Manual). When setting to PIOR = 1

(2/2)

Ite	m	40-	nin	11	-pin	40	-pin	E0.	-pin	64	(2/2) -pin
ite	III				i		i –				
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	:	2		2		2		2		2
		(Main s	system clo z, 512 Hz,	ock: fmain = 1.024 kHz	Hz, 1.25 N 20 MHz o z, 2.048 kH 2.768 kHz	peration) Iz, 4.096 k	кHz, 8.192			2.768 kHz	
8/10-bit resolution	A/D converter	9 channels 10 channels 12 channels 12 channels								nels	
Serial interface	20 1	 CSI: 1 CSI: 2 [48-pin, 5 CSI: 2 CSI: 2 [64-pin pi CSI: 2 CSI: 2 CSI: 2 CSI: 2 	channel/s channels, channels, 2-pin prod channels, channels, oducts] channels, channels, channels,	simplified I simplified I simplified I simplified ducts] simplified I simplified I simplified simplified simplified simplified simplified simplified simplified	² C: 1 chan ² C: 1 chan I ² C: 2 chal I ² C: 1 chan I ² C: 2 chal I ² C: 2 chal I ² C: 2 chal	nel/UART nnels/UAF nel/UART nnels/UAF nnels/UAF nnels/UAF	: 1 channe RT (UART RT: 1 chan : 1 channe RT (UART RT: 1 chan RT: 1 chan RT (UART	el supporting nel el supporting nel nel supporting	g LIN-bus) g LIN-bus)	: 1 channe	el
	I ² C bus	1 channe		1 channe	el	1 channe	el	1 channe	el	1 channe	el
Multiplier and divide accumulator DMA controller	der/multiply-	• 32 bits	÷ 32 bits : × 16 bits :	= 32 bits (l	Unsigned of Unsigned) 32 bits (U		r signed)				
Vectored	Internal	2	7	:	27	:	27	:	27	:	27
interrupt sources	External	-	7		7		10		12		13
Key interrupt			4		4		6]	8		8
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access									
Power-on-reset ci	rcuit	PowerPower		1.51 V set:1.50 V	. ,						
Voltage detector		 Rising edge: 1.67 V to 4.06 V (14 stages) Falling edge: 1.63 V to 3.98 V (14 stages) 									
On-chip debug fur	nction	Provided									
Power supply volt	age			$T_{A} = -40 \text{ to}$ $T_{A} = -40 \text{ to}$							
Operating ambien	t temperature	T _A = 40 to	+85°C (/	A: Consum	ner applica		ndustrial a	pplications	s)		

The illegal instruction is generated when instruction code FFH is executed. Note

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Item	80-	pin	100)-pin	128	(1/2) -pin				
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx				
Code flash me	emory (KB)	96 to	512	96 t	o 512	192	to 512				
Data flash me	mory (KB)	8	-	8	_	8	_				
RAM (KB)		8 to 32	Note 1	8 to 3	32 Note 1	16 to 3	32 Note 1				
Address spac	е	1 MB				•					
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	X1 (crystal/ceramic) oscillation, external main system clock input (EXCLK) HS (High-speed main) mode: 1 to 20 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)								
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	HS (High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), HS (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), LS (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), LV (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V)								
Subsystem cle	ock	XT1 (crystal) os 32.768 kHz	XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz								
Low-speed or	n-chip oscillator	15 kHz (TYP.)									
General-purpo	ose register	(8-bit register ×	8) × 4 banks								
Minimum instruction execution time 0.03125 μs (High-speed on-chip oscillator: f _{IH} = 32 MHz operation)											
		0.05 µs (High-sp	peed system clo	ck: fmx = 20 MHz	operation)						
		30.5 μs (Subsys	tem clock: fsub =	: 32.768 kHz ope	eration)						
Instruction set	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 									
I/O port	Total		'4		92		20				
	CMOS I/O	(N-ch O.D. I/O	i4 [EV _{DD} withstand e]: 21)	(N-ch O.D. I/O	82 [EV _{DD} withstand ge]: 24)	(N-ch O.D. I/O	10 [EVpp withstand ge]: 25)				
	CMOS input		5		5		5				
	CMOS output		1		1		1				
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4				
Timer	16-bit timer	12 cha	nnels	12 ch	annels	16 ch	annels				
	Watchdog timer	1 cha	innel	1 ch	annel	1 cha	annel				
	Real-time clock (RTC)	1 channel 1 channel 1 channe									
	12-bit interval timer (IT)	1 cha	innel	1 ch	annel	1 cha	annel				
	Timer output	12 channels (PWM outputs: 10 Note 2) 12 channels (PWM outputs: 10 Note 2) 16 channels (PWM outputs: 14 Note 2)									
	RTC output 1 channel 1 thannel 1 Hz (subsystem clock: fsub = 32.768 kHz)										

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see **Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944)**.

Notes 2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see **6.9.3 Operation as multiple PWM output function** in the RL78/G13 User's Manual).

(2/2)

Ite	m	80-	pin	100	-pin	128	3-pin			
		R5F100Mx	R5F101Mx	R5F100Px	R5F101Px	R5F100Sx	R5F101Sx			
Clock output/buzz	er output		2	:	2		2			
		 2.44 kHz, 4.88 kHz, 9.76 kHz, 1.25 MHz, 2.5 MHz, 5 MHz, 10 MHz (Main system clock: f_{MAIN} = 20 MHz operation) 256 Hz, 512 Hz, 1.024 kHz, 2.048 kHz, 4.096 kHz, 8.192 kHz, 16.384 kHz, 32.768 kHz (Subsystem clock: f_{SUB} = 32.768 kHz operation) 								
8/10-bit resolution	A/D converter	17 channels		20 channels		26 channels				
Serial interface		CSI: 2 channCSI: 2 channCSI: 2 chann	 [80-pin, 100-pin, 128-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel 							
	I ² C bus	2 channels		2 channels		2 channels				
Multiplier and divid accumulator	der/multiply-	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 								
DMA controller		4 channels		· · · · ·						
Vectored	Internal	3	37	3	37		41			
interrupt sources	External	1	13	1	3		13			
Key interrupt			8	;	8		8			
Reset		Internal resetInternal resetInternal resetInternal reset	by watchdog times by power-on-rest by voltage detections.	set ctor ction execution ^{Not} error	e					
Power-on-reset ci	rcuit	Power-on-reset: 1.51 V (TYP.) Power-down-reset: 1.50 V (TYP.)								
Voltage detector		 Rising edge: 1.67 V to 4.06 V (14 stages) Falling edge: 1.63 V to 3.98 V (14 stages) 								
On-chip debug fur	nction	Provided								
Power supply volta	age	$V_{DD} = 1.6 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +85^{\circ}\text{C})$ $V_{DD} = 2.4 \text{ to } 5.5 \text{ V } (T_A = -40 \text{ to } +105^{\circ}\text{C})$								
Operating ambien	t temperature	T _A = 40 to +85°C (A: Consumer applications, D: Industrial applications) T _A = 40 to +105°C (G: Industrial applications)								

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

2. ELECTRICAL SPECIFICATIONS ($T_A = -40 \text{ to } +85^{\circ}\text{C}$)

This chapter describes the following electrical specifications.

Target products A: Consumer applications T_A = −40 to +85°C R5F100xxAxx, R5F101xxAxx

- D: Industrial applications T_A = −40 to +85°C R5F100xxDxx, R5F101xxDxx
- G: Industrial applications when $T_A = -40$ to $+105^{\circ}$ C products is used in the range of $T_A = -40$ to $+85^{\circ}$ C R5F100xxGxx
- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EV_{DD0}, EV_{DD1}, EV_{SS0}, or EV_{SS1} pin, replace EV_{DD0} and EV_{DD1} with V_{DD}, or replace EV_{SS0} and EV_{SS1} with V_{SS}.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product in the RL78/G13 User's Manual.

2.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and $-0.3 \text{ to V}_{DD} +0.3^{\text{Note 1}}$	V
Input voltage	VII	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	V _{O2}	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	V _{AI2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V

- Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** AV_{REF} (+): + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	- 70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	-100	mA
	Iон ₂	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +85	°C
emperature		In flash memory p	programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}C, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	MHz
		1.8 V ≤ V _{DD} < 2.4 V	1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/G13 User's Manual.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters	Conditions			TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator		−20 to +85°C	1.8 V ≤ V _{DD} ≤ 5.5 V	-1.0		+1.0	%
clock frequency accuracy			1.6 V ≤ V _{DD} < 1.8 V	-5.0		+5.0	%
		−40 to −20°C	1.8 V ≤ V _{DD} ≤ 5.5 V	-1.5		+1.5	%
			1.6 V ≤ V _{DD} < 1.8 V	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fı∟				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

2.3 DC Characteristics

2.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	1.6 V ≤ EV _{DD0} ≤ 5.5 V			-10.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-55.0	mA
		P125 to P127, P130, P140 to P145	2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
		$(When duty \le 70\% \frac{Note 3}{})$	1.8 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
		,	1.6 V ≤ EV _{DD0} < 1.8 V			-2.5	mA
		Total of P05, P06, P10 to P17, P30, P31,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-80.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to	2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		P117, P146, P147	1.8 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
		(When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} < 1.8 V			-5.0	mA
Іон2		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} ≤ 5.5 V			-135.0 Note 4	mA
		Per pin for P20 to P27, P150 to P156	1.6 V ≤ V _{DD} ≤ 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% Note 3)	1.6 V ≤ V _{DD} ≤ 5.5 V			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(loh \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and loh = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

4. The applied current for the products for industrial application (R5F100xxDxx, R5F101xxDxx, R5F100xxGxx) is –100 mA.

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	loL1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				20.0 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			70.0	mA
		P40 to P47, P102 to P106, P120, P125	2.7 V ≤ EV _{DD0} < 4.0 V			15.0	mA
		to P127, P130, P140 to P145 (When duty ≤ 70% Note 3)	1.8 V ≤ EV _{DD0} < 2.7 V			9.0	mA
		,	1.6 V ≤ EV _{DD0} < 1.8 V			4.5	mA
		P31, P50 to P57, P60 to P67,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			80.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146,	1.8 V ≤ EV _{DD0} < 2.7 V			20.0	mA
		P147 (When duty ≤ 70% Note 3)	1.6 V ≤ EV _{DD0} < 1.8 V			10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})				150.0	mA
	lol2	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	1.6 V ≤ V _{DD} ≤ 5.5 V			5.0	mA

- **Notes 1.** Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. However, do not exceed the total current value.
 - 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$
- <Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7 \text{ mA}$

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (3/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}		EVDDO EVDDO EVDDO VDD 6.0	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	VIH3	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0.8V _{DD}		V _{DD}	V
Input voltage, low	VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		EVDDO EVDDO VDD 6.0	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 1.6 V ≤ EVDD0 < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	VIL4	P60 to P63		0		0.3EV _{DD0}	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $I_{\text{OH1}} = -10.0 \text{ mA}$	EV _{DD0} – 1.5			V
		P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} - 0.7			V
		P125 to P127, P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} - 0.6			V
			1.8 V \leq EV _{DD0} \leq 5.5 V, Іон1 = -1.5 mA	EV _{DD0} – 0.5			V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{I}_{\text{OH1}} = -1.0 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V ≤ V _{DD} ≤ 5.5 V, I _{OH2} = -100μ A	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 20 mA			1.3	V
		P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 8.5 mA		0.7	0.7	V
		P125 to P127, P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 1.5 mA			0.4	V
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 0.6 mA			0.4	V
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ IoL1 = 0.3 mA			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	$1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $1012 = 400 \mu\text{A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 15.0 mA			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 5.0 mA			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iol3 = 3.0 mA			0.4	V
			1.8 V ≤ EV _{DD0} ≤ 5.5 V, lo _{L3} = 2.0 mA			0.4	V
			1.6 V ≤ EV _{DD0} < 5.5 V, lo _{L3} = 1.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (5/5)$

Items	Symbol	Conditi	ons		MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішн1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVDDO				1	μА
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	VI = VDD				1	μA
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = V _{DD}	In input port or external clock input			1	μA
				In resonator connection			10	μA
Input leakage current, low	lui.1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso				-1	μА
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μA
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso,	In input port	10	20	100	kΩ

2.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fih = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.1		mA
current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.1		mA
			mode		Normal	V _{DD} = 5.0 V		4.6	7.0	mA
					operation	V _{DD} = 3.0 V		4.6	7.0	mA
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.7	5.5	mA
					operation	V _{DD} = 3.0 V		3.7	5.5	mA
				fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	4.0	mA
					operation	V _{DD} = 3.0 V		2.7	4.0	mA
			LS (low-	fin = 8 MHz Note 3	Nomal	V _{DD} = 3.0 V		1.2	1.8	mA
			speed main) mode ^{Note 5}		operation	V _{DD} = 2.0 V		1.2	1.8	mA
			LV (low- voltage main) mode Note 5	fiH = 4 MHz Note 3	Nomal	V _{DD} = 3.0 V		1.2	1.7	mA
					operation	V _{DD} = 2.0 V		1.2	1.7	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.0	4.6	mA
	speed	speed main) mode Note 5	$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		3.2	4.8	mA	
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.6	mA
		LS (low-	$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		3.2	4.8	mA	
			LS (low-	$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		1.9	2.7	mA
				$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		1.9	2.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		1.9	2.7	mA
				V _{DD} = 3.0 V	operation	Resonator connection		1.9	2.7	mA
				$f_{MX} = 8 MHz^{Note 2}$	Nomal	Square wave input		1.1	1.7	mA
				V _{DD} = 3.0 V	operation Normal	Resonator connection		1.1	1.7	mA
			modo	$f_{MX} = 8 MHz^{Note 2}$		Square wave input		1.1	1.7	mA
				V _{DD} = 2.0 V	operation	Resonator connection		1.1	1.7	mA
			Subsystem	fsuB = 32.768 kHz	Nomal	Square wave input		4.1	4.9	μΑ
			clock operation	Note 4 $T_A = -40^{\circ}C$	operation	Resonator connection		4.2	5.0	μA
				fsuB = 32.768 kHz	Normal	Square wave input		4.1	4.9	μΑ
				Note 4 $T_A = +25^{\circ}C$	operation	Resonator connection		4.2	5.0	μA
				fsuB = 32.768 kHz	Normal	Square wave input		4.2	5.5	μA
				Note 4	operation	Resonator connection		4.3	5.6	μA
				T _A = +50°C						
			fsuB = 32.768 kHz	Nomal	Square wave input		4.3	6.3	μA	
				Note 4 T _A = +70°C	operation	Resonator connection		4.4	6.4	μA
				fsub = 32.768 kHz	Normal	Square wave input		4.6	7.7	μA
				Note 4	operation	Resonator connection		4.7	7.8	μA
	T _A = +85°C		T _A = +85°C							

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVSSO. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V}) (2/2)$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high- speed main)	f _{IH} = 32 MHz Note 4	V _{DD} = 5.0 V		0.54	1.63	mA
current Note 1	Note 2	mode	mode Note 7		V _{DD} = 3.0 V		0.54	1.63	mA
				f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	1.28	mA
					V _{DD} = 3.0 V		0.44	1.28	mA
				fin = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.00	mA
					V _{DD} = 3.0 V		0.40	1.00	mA
			LS (low-	fih = 8 MHz Note 4	V _{DD} = 3.0 V		260	530	μA
			speed main) mode Note 7		V _{DD} = 2.0 V		260	530	μA
			LV (low- voltage main) mode Note 7	f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V		420	640	μA
					V _{DD} = 2.0 V		420	640	μA
				f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.00	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	1.17	mA
			mode	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.28	1.00	mA
				V _{DD} = 3.0 V	Resonator connection		0.45	1.17	mA
		 	f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.60	mA	
			V _{DD} = 5.0 V	Resonator connection		0.26	0.67	mA	
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.19	0.60	mA
				V _{DD} = 3.0 V	Resonator connection		0.26	0.67	mA
			LS (low-speed	$f_{MX} = 8 \text{ MHz}^{\text{Note 3}},$	Square wave input		95	330	μΑ
			main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		145	380	μΑ
				$f_{MX} = 8 MHz^{Note 3},$	Square wave input		95	330	μΑ
				V _{DD} = 2.0 V	Resonator connection		145	380	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μΑ
			clock	T _A = -40°C	Resonator connection		0.44	0.76	μΑ
			operation	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μΑ
				T _A = +25°C	Resonator connection		0.49	0.76	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μΑ
				T _A = +50°C	Resonator connection		0.56	1.36	μA
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μA
				T _A = +70°C	Resonator connection		0.72	2.16	μA
			fsub = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μA	
				T _A = +85°C	Resonator connection		1.01	3.56	μA
			T _A = -40°C				0.18	0.50	μA
		mode ^{Note 8}	T _A = +25°C				0.23	0.50	μΑ
			T _A = +50°C				0.30	1.10	μΑ
			T _A = +70°C				0.46	1.90	μΑ
			T _A = +85°C				0.75	3.30	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into V_{DD} and EV_{DDO}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DDO} or V_{SS}, EV_{SSO}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz

LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

- 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Supply current Note	Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Nome		I _{DD1}		, -	fin = 32 MHz Note 3		V _{DD} = 5.0 V		2.3		mA
Nome operation Nome op			mode	speed main)		operation	V _{DD} = 3.0 V		2.3		mA
fin = 24 MHz Note 3 Normal operation				mode			V _{DD} = 5.0 V		5.2	8.5	mA
Department Dep						operation	V _{DD} = 3.0 V		5.2	8.5	mA
fist = 16 MHz Note 3 Normal operation Nor					fih = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		4.1	6.6	mA
State Stat						operation	V _{DD} = 3.0 V		4.1	6.6	mA
LS (low-speed main) mode Notes S LV (low-voltage main) mode Notes Normal Voltage Notes Normal Nor					f _{IH} = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		3.0	4.7	mA
Speed main Mode Note S						operation	V _{DD} = 3.0 V		3.0	4.7	mA
LV (low-voltage main) mode Notes LV (low-voltage main) mode Notes				LS (low-	fIH = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.3	2.1	mA
Voltage main) mode Note 5						operation	V _{DD} = 2.0 V		1.3	2.1	mA
Main mode Mote 5 Max = 20 MHz Mete 2 Mormal Square wave input 3.4 5.5 mA Square wave input 2.1 3.2 mA Square wave input 1.2 2.0 mA Square wave input 1.2				voltage main) mode	fin = 4 MHz Note 3	Normal	V _{DD} = 3.0 V		1.3	1.8	mA
Speed main mode Note 5 Fax = 20 MHz Note 2 Vob = 5.0 V Fax = 20 MHz Note 2 Vob = 3.0 V Fax = 10 MHz Note 2 Vob = 5.0 V Vob = 5.0 V Fax = 10 MHz Note 2 Vob = 5.0 V Vob = 5.0 V Fax = 10 MHz Note 2 Vob = 3.0 V Vob = 2.0 V Vo						operation	V _{DD} = 2.0 V		1.3	1.8	mA
Mode Note 5 Mix 20 MHz Note 2 Normal Square wave input 3.4 5.5 mA				HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.4	5.5	mA
				speed main)	V _{DD} = 5.0 V	operation	Resonator connection		3.6	5.7	mA
Filipsi			mode Note 5	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.5	mA	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					V _{DD} = 3.0 V	operation	Resonator connection		3.6	5.7	mA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$					f _{MX} = 10 MHz ^{Note 2} ,		Square wave input		2.1	3.2	mA
LS (low-speed main) mode Note 5 Max = 8 MHzNote 2 Normal operation Note 4					V _{DD} = 5.0 V		Resonator connection		2.1	3.2	mA
LS (low-speed main) mode Note 5 $\frac{1}{1}$ $$				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$		Square wave input		2.1	3.2	mA	
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						operation	Resonator connection		2.1	3.2	mA
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$,	-		Square wave input		1.2	2.0	mA
					V _{DD} = 3.0 V	operation	Resonator connection		1.2	2.0	mA
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$				mode	$f_{MX} = 8 MHz^{Note 2},$		Square wave input		1.2	2.0	mA
$ \begin{array}{c} \text{clock} \\ \text{operation} \end{array} \begin{array}{c} \text{Note 4} \\ T_A = -40^{\circ}\text{C} \end{array} \begin{array}{c} \text{Normal} \\ \text{Normal} \\ \text{Note 4} \end{array} \begin{array}{c} \text{Square wave input} \\ \text{Resonator connection} \end{array} \begin{array}{c} 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 5.9 \\ 4.9 \end{array} \begin{array}{c} 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 5.9 \\ 4.9 \\ 4.9 \\ 4.9 \\ 5.0 \\ 5.0 \\ 5.0 \\ 5.0 \\ 5.0 \\ 7.6 \\ 4.9 \\ 4.9 \\ 4.9 \\ 4.9 \\ 4.9 \\ 5.0 \\ 4.9$					V _{DD} = 2.0 V	operation	Resonator connection		1.2	2.0	mA
$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$,		_	Square wave input		4.8	5.9	μΑ
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						operation	Resonator connection		4.9	6.0	μA
$T_{A} = +25^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Note 4$ $T_{A} = +50^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Note 4$ $Normal operation$ $T_{A} = +70^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Note 4$ $T_{A} = +70^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Normal operation$ $T_{A} = +70^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Normal operation$ $T_{A} = +70^{\circ}C$ $Square wave input operation operation T_{A} = +70^{\circ}C Square wave input operation opera$							Square wave input		4.9	5.9	μA
$ \begin{array}{ c c c c c c c c c } \hline Note 4 & operation \\ \hline T_A = +50 ^{\circ}C & \hline \\ f_{SUB} = 32.768 \text{ kHz} \\ Note 4 & operation \\ \hline T_A = +70 ^{\circ}C & \hline \\ f_{SUB} = 32.768 \text{ kHz} \\ Note 4 & operation \\ \hline \end{array} \begin{array}{ c c c c c c } \hline Resonator connection & 5.1 & 7.7 & μA \\ \hline \hline Square wave input & 5.2 & 9.3 & μA \\ \hline Resonator connection & 5.3 & 9.4 & μA \\ \hline \hline Resonator connection & 5.7 & 13.3 & μA \\ \hline \hline Resonator connection & 5.8 & 13.4 & μA \\ \hline \hline \end{array} $						operation	Resonator connection		5.0	6.0	μΑ
$T_{A} = +50^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Note 4$ $T_{A} = +70^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Normal operation$ $T_{A} = +70^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Normal operation$ $Normal operation$ $Operation$ $Oper$							Square wave input		5.0	7.6	μA
Note 4 operation $T_A = +70^{\circ}\text{C}$ Resonator connection $T_A = +70^{\circ}\text{C}$ Resonator connection $T_A = +70^{\circ}\text{C}$ Square wave input $T_A = +70^{\circ}\text{C}$ Square wave input $T_A = +70^{\circ}\text{C}$ Resonator connection $T_A = +70^{\circ}\text{C}$ Resonator connection $T_A = +70^{\circ}\text{C}$ $T_A = +$						operation	Resonator connection		5.1	7.7	μΑ
T _A = +70°C $ \begin{array}{c ccccccccccccccccccccccccccccccccccc$						Normal	Square wave input		5.2	9.3	μA
Note 4 operation Resonator connection 5.8 13.4 µA				No	Note 4	operation	Resonator connection		5.3	9.4	μA
						Normal	Square wave input		5.7	13.3	μA
			No	Note 4 TA = +85°C	operation	Resonator connection		5.8	13.4	μA	

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 8 MHz LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (2/2)$

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	fih = 32 MHz Note 4	V _{DD} = 5.0 V		0.62	1.86	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	1.86	mA
			mode	f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	1.45	mA
					V _{DD} = 3.0 V		0.50	1.45	mA
				f _{IH} = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.11	mA
					V _{DD} = 3.0 V		0.44	1.11	mA
			LS (low-speed main) mode	fih = 8 MHz Note 4	V _{DD} = 3.0 V		290	620	μA
					V _{DD} = 2.0 V		290	620	μΑ
			LV (low-	f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V		440	680	μΑ
			` `		V _{DD} = 2.0 V		440	680	μA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	1.08	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	1.28	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	1.08	mA
			1	V _{DD} = 3.0 V	Resonator connection		0.48	1.28	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.63	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	0.71	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.63	mA
				VDD = 3.0 V	Resonator connection		0.28	0.71	mA
			LS (low-speed	$f_{MX} = 8 MHz^{Note 3},$	Square wave input		110	360	μΑ
			main) mode Note 7	VDD = 3.0 V	Resonator connection		160	420	μΑ
				$f_{MX} = 8 MHz^{Note 3},$	Square wave input		110	360	μΑ
				V _{DD} = 2.0 V	Resonator connection		160	420	μΑ
			Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μΑ
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.47	0.80	μΑ
			орегация	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μΑ
				T _A = +25°C	Resonator connection		0.53	0.80	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μΑ
				$T_A = +50^{\circ}C$	Resonator connection		0.60	2.49	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μA
				T _A = +70°C	Resonator connection		0.83	4.22	μA
			fsub = 32.768 kHz ^{Note 5}	Square wave input		1.09	8.04	μA	
			T _A = +85°C	Resonator connection		1.28	8.23	μA	
	IDD3 ^{Note 6} STOP		T _A = -40°C				0.19	0.52	μA
		mode ^{Note 8}	T _A = +25°C				0.25	0.52	μA
			T _A = +50°C				0.32	2.21	μΑ
			T _A = +70°C				0.55	3.94	μΑ
			T _A = +85°C				1.00	7.95	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz}$ to 8 MHz

LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

- 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	fih = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.6		mA
current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.6		mA
			modo		Nomal	V _{DD} = 5.0 V		6.1	9.5	mA
					operation	V _{DD} = 3.0 V		6.1	9.5	mA
				fih = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		4.8	7.4	mA
					operation	V _{DD} = 3.0 V		4.8	7.4	mA
				fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		3.5	5.3	mA
					operation	V _{DD} = 3.0 V		3.5	5.3	mA
			LS (low-	fin = 8 MHz Note 3	Normal	V _{DD} = 3.0 V		1.5	2.3	mA
			speed main) mode Note 5		operation	V _{DD} = 2.0 V		1.5	2.3	mA
			LV (low-	$f_{IH} = 4 \text{ MHz}^{\text{Note 3}}$	Nomal	V _{DD} = 3.0 V		1.5	2.0	mA
			voltage main) mode Note 5		operation	V _{DD} = 2.0 V		1.5	2.0	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		3.9	6.1	mA
			speed main) mode Note 5	$V_{DD} = 5.0 \text{ V}$	operation	Resonator connection		4.1	6.3	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.9	6.1	mA
				$V_{DD} = 3.0 \text{ V}$	operation	Resonator connection		4.1	6.3	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		2.5	3.7	mA
				V _{DD} = 5.0 V	operation	Resonator connection		2.5	3.7	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.5	3.7	mA
				VDD = 3.0 V	operation	Resonator connection		2.5	3.7	mA
			LS (low-	•	Nomal	Square wave input		1.4	2.2	mA
			speed main) mode Note 5	V _{DD} = 3.0 V	operation	Resonator connection		1.4	2.2	mA
			modo	$f_{MX} = 8 MHz^{Note 2}$,	Nomal	Square wave input		1.4	2.2	mA
				V _{DD} = 2.0 V	operation	Resonator connection		1.4	2.2	mA
			Subsystem	fsub = 32.768 kHz Note 4	Nomal	Square wave input		5.4	6.5	μΑ
			clock operation	$T_A = -40^{\circ}C$	operation	Resonator connection		5.5	6.6	μΑ
				fsuB = 32.768 kHz	Nomal	Square wave input		5.5	6.5	μΑ
				Note 4 $T_A = +25^{\circ}C$	operation	Resonator connection		5.6	6.6	μΑ
				fsuB = 32.768 kHz	Normal	Square wave input		5.6	9.4	μA
				Note 4	operation	Resonator connection		5.7	9.5	μA
				T _A = +50°C					4.5.	
				fsub = 32.768 kHz Note 4	Normal operation	Square wave input		5.9	12.0	μA
			Note 4 TA = +70°C	Spoidion	Resonator connection		6.0	12.1	μΑ	
			fs	fsuB = 32.768 kHz Norma	Nomal	Square wave input		6.6	16.3	μΑ
			T _A = +85°C	operation	Resonator connection		6.7	16.4	μΑ	

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDO, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 8 MHz LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ @1 MHz to 4 MHz

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

(3) 128-pin products, and flash ROM: 384 to 512 KB of 44- to 100-pin products

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	f _{IH} = 32 MHz Note 4	V _{DD} = 5.0 V		0.62	1.89	mA
Current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.62	1.89	mA
			mode	fih = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	1.48	mA
					V _{DD} = 3.0 V		0.50	1.48	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.12	mA
					V _{DD} = 3.0 V		0.44	1.12	mA
			LS (low-speed	fih = 8 MHz Note 4	V _{DD} = 3.0 V		290	620	μA
			main) mode Note 7		V _{DD} = 2.0 V		290	620	μΑ
			LV (low-	f _{IH} = 4 MHz Note 4	V _{DD} = 3.0 V		460	700	μA
			voltage main) mode Note 7		V _{DD} = 2.0 V		460	700	μΑ
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	1.14	mA
			speed main) mode Note 7	$V_{DD} = 5.0 \text{ V}$	Resonator connection		0.48	1.34	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.31	1.14	mA
			$V_{DD} = 3.0 V$	Resonator connection		0.48	1.34	mA	
		fr	$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA	
				$V_{DD} = 5.0 \text{ V}$	Resonator connection		0.28	0.76	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.21	0.68	mA
				V _{DD} = 3.0 V	Resonator connection		0.28	0.76	mA
			, ,	$f_{MX} = 8 MHz^{Note 3}$	Square wave input		110	390	μΑ
			main) mode Note 7	V _{DD} = 3.0 V	Resonator connection		160	450	μΑ
				$f_{MX} = 8 MHz^{Note 3},$	Square wave input		110	390	μΑ
				$V_{DD} = 2.0 \text{ V}$	Resonator connection		160	450	μΑ
			Subsystem	$f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$	Square wave input		0.31	0.66	μΑ
			clock operation	$T_A = -40^{\circ}C$	Resonator connection		0.50	0.85	μΑ
			орогалогі	$f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$	Square wave input		0.38	0.66	μΑ
				$T_A = +25^{\circ}C$	Resonator connection		0.57	0.85	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.47	3.49	μΑ
				$T_A = +50$ °C	Resonator connection		0.66	3.68	μΑ
				$f_{SUB} = 32.768 \text{ kHz}^{\text{Note 5}}$	Square wave input		0.80	6.10	μΑ
				$T_A = +70^{\circ}C$	Resonator connection		0.99	6.29	μΑ
	I _{DD3} Note 6 STOP			fsub = 32.768 kHz ^{Note 5}	Square wave input		1.52	10.46	μΑ
				$T_A = +85^{\circ}C$	Resonator connection		1.71	10.65	μA
			T _A = -40°C				0.19	0.54	μΑ
		mode ^{Note 8}	T _A = +25°C				0.26	0.54	μΑ
			T _A = +50°C				0.35	3.37	μΑ
			T _A = +70°C				0.68	5.98	μA
			T _A = +85°C				1.40	10.34	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz}$ to 16 MHz

LS (low-speed main) mode: 1.8 V ≤ V_{DD} ≤ 5.5 V @1 MHz to 8 MHz

LV (low-voltage main) mode: 1.6 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 4 MHz

- 8. Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(4) Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1				0.20		μΑ
RTC operating current	IRTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operating current	Notes 1, 2, 4				0.02		μА
Watchdog timer operating current	Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μΑ
A/D converter	I _{ADC} Notes 1, 6	When	Normal mode, AVREFP = VDD = 5.0 V		1.3	1.7	mA
operating current		conversion at maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μΑ
Temperature sensor operating current	I _{TMPS} Note 1				75.0		μА
LVD operating current	_{LVI} Notes 1, 7				0.08		μΑ
Self- programming operating current	FSP Notes 1, 9				2.50	12.20	mA
BGO operating current	I _{BGO} Notes 1, 8				2.50	12.20	mA
SNOOZE	I _{SNOZ} Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
operating current			The A/D conversion operations are performed, Low voltage mode, AVREFP = VDD = 3.0 V		1.20	1.44	mA
		CSI/UART operati	on		0.70	0.84	mA

Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- **4.** Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- 5. Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.
- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter operates in an operation mode or the HALT mode.

- Notes 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25$ °C

2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main system	HS (high-speed	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
instruction execution time)		clock (fmain)	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		operation	LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem con operation	lock (fsub)	1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self	HS (high-speed	2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
		programming	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
External system clock frequency	fex	2.7 V ≤ V _{DD} ≤	5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} <	: 2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} <	: 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	2.7 V ≤ V _{DD} ≤	5.5 V		24			ns
level width, low-level width		2.4 V ≤ V _{DD} <	2.7 V		30			ns
		1.8 V ≤ V _{DD} <	2.4 V		60			ns
		1.6 V ≤ V _{DD} <	: 1.8 V		120			ns
	texhs, texhs				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tті∟				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	fто	HS (high-spe	ed 4.0 V ≤	EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V ≤	EV _{DD0} < 4.0 V			8	MHz
			1.8 V ≤	EV _{DD0} < 2.7 V			4	MHz
			1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
		LS (low-spee	d 1.8 V ≤	EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode	ge 1.6 V ≤	EV _{DD0} ≤ 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	ed 4.0 V ≤	≦ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V ≤	EV _{DD0} < 4.0 V			8	MHz
			1.8 V ≤	EV _{DD0} < 2.7 V			4	MHz
			1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
		LS (low-spee	d 1.8 V ≤	EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta	ge 1.8 V ≤	EV _{DD0} ≤ 5.5 V			4	MHz
		main) mode	1.6 V ≤	EV _{DD0} < 1.8 V			2	MHz
Interrupt input high-level width,	tinth,	INTP0	1.6 V ≤	V _{DD} ≤ 5.5 V	1			μs
low-level width	tintl	INTP1 to INT	P11 1.6 V ≤	EV _{DD0} ≤ 5.5 V	1			μs
Key interrupt input low-level width	tkr	KR0 to KR7	1.8 V ≤	EV _{DD0} ≤ 5.5 V	250			ns
			16V<	EV _{DD0} < 1.8 V	1			μs
			1.0 V =	_ T T D D 0				

(Note and Remark are listed on the next page.)

Note The following conditions are required for low voltage interface when EVDDO < VDD

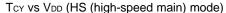
 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MIN. } 125 \text{ ns}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MIN. } 250 \text{ ns}$

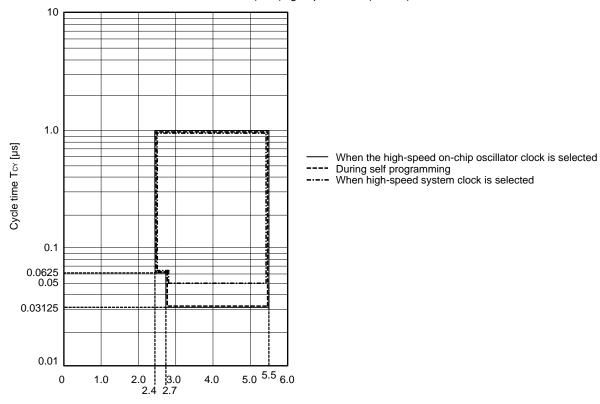
Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

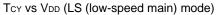
m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

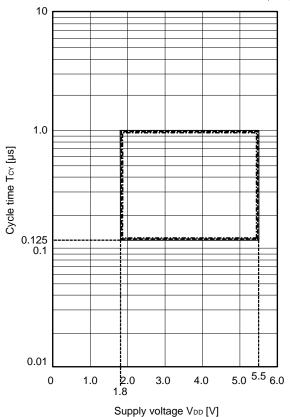
Minimum Instruction Execution Time during Main System Clock Operation





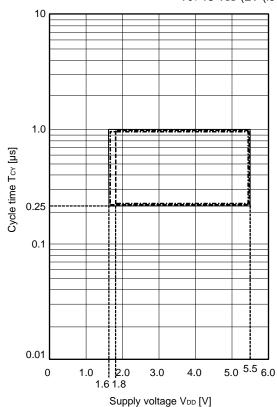
Supply voltage VDD [V]





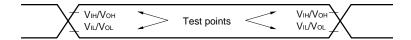
- When the high-speed on-chip oscillator clock is selected
- ---- During self programming
 ---- When high-speed system clock is selected

Tcy vs Vdd (LV (low-voltage main) mode)

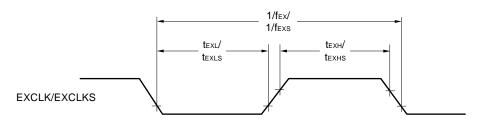


- When the high-speed on-chip oscillator clock is selected
 During self programming
- ---- When high-speed system clock is selected

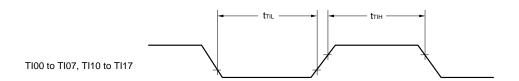
AC Timing Test Points

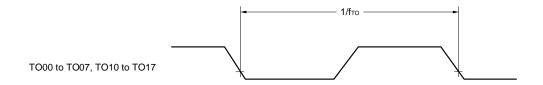


External System Clock Timing

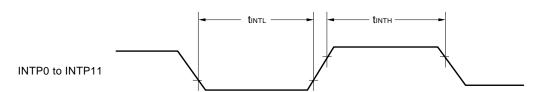


TI/TO Timing

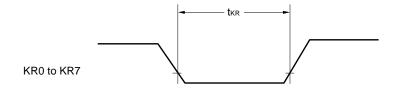




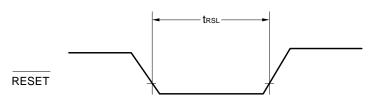
Interrupt Request Input Timing



Key Interrupt Input Timing

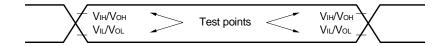


RESET Input Timing



2.5 Peripheral Functions Characteristics

AC Timing Test Points



2.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions		h-speed Mode	LS (lov	v-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate Note 1		2.4 V≤ EV	₀₀₀ ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3		5.3		1.3		0.6	Mbps
		1.8 V ≤ EV	_{DD0} ≤ 5.5 V		fMCK/6 Note 2		fмск/6		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		5.3		1.3		0.6	Mbps
		1.7 V ≤ EV	_{DD0} ≤ 5.5 V		fMCK/6 Note 2		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		5.3		1.3		0.6	Mbps
		1.6 V ≤ EV	_{DD0} ≤ 5.5 V	-	-		fMCK/6 Note 2		fмск/6	bps
			Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}$ Note 3	-	_		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

2. The following conditions are required for low voltage interface when EVDDO < VDD.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 2.6 \text{ Mbps}$ $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 2.4 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$ $1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V} : \text{MAX. } 0.6 \text{ Mbps}$

3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

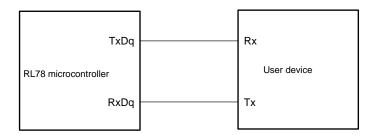
HS (high-speed main) mode: 32 MHz (2.7 V \leq VDD \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

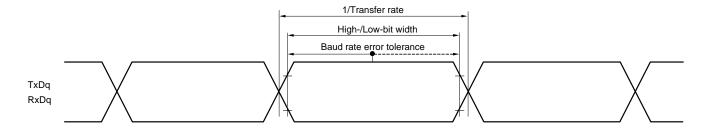
LS (low-speed main) mode: 8 MHz (1.8 V \leq V_{DD} \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq V_{DD} \leq 5.5 V)

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	` `	h-speed Mode	,	r-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 2/fcLk	4.0 V ≤ EV _{DD0} ≤ 5.5 V	62.5		250		500		ns
			2.7 V ≤ EV _{DD0} ≤ 5.5 V	83.3		250		500		ns
SCKp high-/low-level width	tkH1, tkL1	4.0 V ≤ EV _{DD}	0 ≤ 5.5 V	tксү1/2 — 7		tксү1/2 — 50		tксү1/2 — 50		ns
		2.7 V ≤ EV _{DD}	o ≤ 5.5 V	tксү1/2 — 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑)	tsik1	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	23		110		110		ns
Note 1		2.7 V ≤ EV _{DD}	o ≤ 5.5 V	33		110		110		ns
SIp hold time (from SCKp↑)	tksi1	2.7 V ≤ EV _{DD}	o ≤ 5.5 V	10		10		10		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 20 pF Not	e 4		10		10		10	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. This value is valid only when CSI00's peripheral I/O redirect function is not used.

- 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0), g: PIM and POM numbers (g = 1)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))

(3) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	C	Conditions	HS (high main)	•	,	r-speed Mode	LV (low- main)	•	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fcLk	2.7 V ≤ EV _{DD0} ≤ 5.5 V	125		500		1000		ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V	250		500		1000		ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V	500		500		1000		ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	1000		1000		1000		ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	ı		1000		1000		ns
SCKp high-/low-level width	tkH1,	4.0 V ≤ EV _{DD}	o ≤ 5.5 V	tксү1/2 –		tксү1/2 — 50		tксү1/2 — 50		ns
		2.7 V ≤ EV _{DD} (o ≤ 5.5 V	tkcy1/2 -		tксү1/2 – 50		tксү1/2 – 50		ns
		2.4 V ≤ EV _{DD} (o ≤ 5.5 V	tксу1/2 — 38		tксу1/2 — 50		tксу1/2 — 50		ns
		1.8 V ≤ EV _{DD} (o ≤ 5.5 V	tксү1/2 — 50		tксү1/2 — 50		tксу1/2 — 50		ns
		1.7 V ≤ EV _{DD} (o ≤ 5.5 V	tксу1/2 — 100		tксу1/2 — 100		tксу1/2 — 100		ns
		1.6 V ≤ EV _{DD}	o ≤ 5.5 V	-		tксу1/2 — 100		tксу1/2 — 100		ns
SIp setup time	tsik1	4.0 V ≤ EVDD	o ≤ 5.5 V	44		110		110		ns
(to SCKp↑) Note 1		2.7 V ≤ EVDD	o ≤ 5.5 V	44		110		110		ns
Note 1		2.4 V ≤ EVDD	o ≤ 5.5 V	75		110		110		ns
		1.8 V ≤ EVDD	o ≤ 5.5 V	110		110		110		ns
		1.7 V ≤ EV _{DD}	o ≤ 5.5 V	220		220		220		ns
		1.6 V ≤ EV _{DD}	o ≤ 5.5 V	ı		220		220		ns
SIp hold time	t _{KSI1}	1.7 V ≤ EV _{DD}	o ≤ 5.5 V	19		19		19		ns
(from SCKp↑) Note 2		1.6 V ≤ EV _{DD}	o ≤ 5.5 V	ı		19		19		ns
Delay time from SCKp↓ to SOp	tkso1	$1.7 \text{ V} \leq \text{EV}_{\text{DDG}}$ $C = 30 \text{ pF}^{\text{Note}}$			25		25		25	ns
output Note 3		1.6 V ≤ EV _{DD} (C = 30 pF ^{Note}			-		25		25	ns

Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

- 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Condit	ions	, ,	peed main) ode	,	r-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fмск	8/fмск		1		_		ns
Note 5			fмск ≤ 20 MHz	6/fмск		6/fмск		6/ƒмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fмск	8/fмск		1		_		ns
			fмcк ≤ 16 MHz	6/fмск		6/fмск		6/ƒмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		6/fмcк and 500		6/fмск and 500		6/fмск and 500		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 \	1	-		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 7		tксу2/2 -7		tксү2/2 -7		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy2/2 - 8		txcy2/2 -8		tксу2/2 -8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксу2/2 — 18		tксу2/2 - 18		tксү2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксу2/2 — 66		tkcy2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 \	1	-		tkcy2/2 - 66		tkcy2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

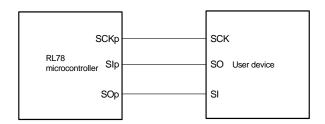
Parameter	Symbol		Conditions	HS (high-sp Mo	,	LS (low-sp Mo	,	LV (low-vol	,	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time	tsik2	2.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+20		1/fмск+30		1/fмск+30		ns
(to SCKp \uparrow) Note 1		1.8 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+30		1/fмск+30		1/fмск+30		ns
		1.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+40		1/fмск+40		1/fмск+40		ns
		1.6 V ≤ E	EV _{DD0} ≤ 5.5 V	-		1/fмск+40		1/fмск+40		ns
SIp hold time	tksi2	1.8 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+31		1/fмск+31		1/fмск+31		ns
(from SCKp↑) Note 2		1.7 V ≤ E	V _{DD0} ≤ 5.5 V	1/fмск+ 250		1/fмск+ 250		1/fмск+ 250		ns
		1.6 V ≤ E	V _{DD0} ≤ 5.5 V	_		1/fмск+ 250		1/fмск+ 250		ns
Delay time from SCKp↓ to SOp	tkso2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 44		2/fмск+ 110		2/fмск+ 110	ns
output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 75		2/fмск+ 110		2/fмск+ 110	ns
			1.8 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 110		2/fмск+ 110		2/fмск+ 110	ns
			1.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+ 220		2/fмск+ 220		2/fмск+ 220	ns
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		-		2/fмск+ 220		2/fмск+ 220	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

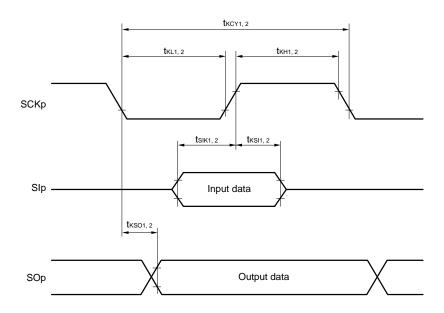
Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

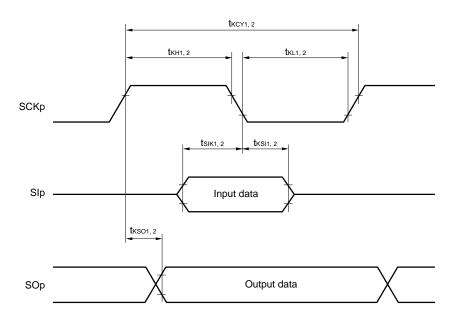
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(5) During communication at same potential (simplified I²C mode) (1/2)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions	HS (hig	h-speed Mode	LS (lov	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$		1000 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} \leq 5.5 V, C _b = 100 pF, R _b = 3 kΩ		400 Note 1		400 Note 1		400 Note 1	kHz
		1.8 V \leq EV _{DD0} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ		300 Note 1		300 Note 1		300 Note 1	kHz
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		250 Note 1		250 Note 1		250 Note 1	kHz
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ		_		250 Note 1		250 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, $C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1550		1550		1550		ns
		$1.7 \text{ V} \le \text{EV}_{\text{DD0}} < 1.8 \text{ V},$ $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-		1850		1850		ns
Hold time when SCLr = "H"	tніgн	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	475		1150		1150		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1150		1150		1150		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1550		1550		1550		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	1850		1850		1850		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, $C_b = 100 \text{ pF}, R_b = 5 \text{ k}\Omega$	-		1850		1850		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(5) During communication at same potential (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	, ,	h-speed Mode	,	v-speed Mode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	1/f _{MCK} + 85 Note2		1/fmck + 145 Note2		1/fmck + 145 Note2		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	1/fмск + 145 Note2		1/fmck + 145 Note2		1/f _{MCK} + 145 Note2		ns
		1.8 V ≤ EV _{DD0} < 2.7 V, C _b = 100 pF, R _b = 5 kΩ	1/f _{MCK} + 230 Note2		1/f _{MCK} + 230 Note2		1/fmck + 230 Note2		ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	1/fmck + 290 Note2		1/fmck + 290 Note2		1/fmck + 290 Note2		ns
		1.6 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	_		1/f _{MCK} + 290 Note2		1/fmck + 290 Note2		ns
Data hold time (transmission)	thd:dat	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V, C _b = 100 pF, R _b = 3 kΩ	0	355	0	355	0	355	ns
		1.8 V \leq EV _{DD0} $<$ 2.7 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.7 V ≤ EV _{DD0} < 1.8 V, C _b = 100 pF, R _b = 5 kΩ	0	405	0	405	0	405	ns
		1.6 V \leq EV _{DD0} $<$ 1.8 V, C _b = 100 pF, R _b = 5 kΩ	-		0	405	0	405	ns

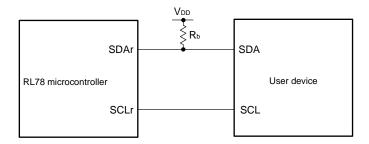
Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

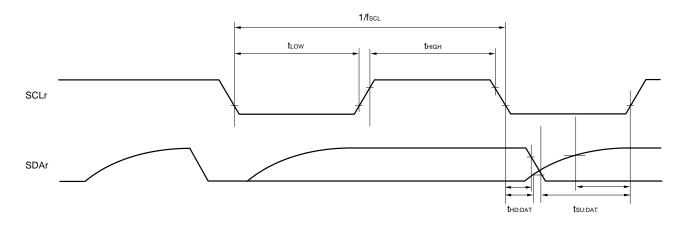
Caution Select the normal input buffer and the N-ch open drain output (V_{DD} tolerance (When 20- to 52-pin products)/EV_{DD} tolerance (When 64- to 128-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions			h-speed Mode		/-speed Mode		-voltage Mode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Recep- tion	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$			fmck/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$			fMCK/6 Note 1		fMCK/6 Note 1		fMCK/6 Note 1	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps
			1.8 V ≤ EV _{DD0} < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V			fMCK/6 Notes 1 to 3		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate fmck = fclk Note 4		5.3		1.3		0.6	Mbps

Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.

- 2. Use it with $EV_{DD0} \ge V_b$.
- 3. The following conditions are required for low voltage interface when EVDDO < VDD.

2.4 V ≤ EV_{DD0} < 2.7 V : MAX. 2.6 Mbps 1.8 V ≤ EV_{DD0} < 2.4 V : MAX. 1.3 Mbps

4. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: $32 \text{ MHz} (2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V})$

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpb tolerance (When 20- to 52-pin products)/EVpb tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For ViH and ViL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions		speed	high- I main) ode		v-speed Mode	voltage	(low- e main) ode	Unit
					MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			Note 1		Note 1		Note 1	bps
			2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate		2.8 Note 2		2.8 Note 2		2.8 Note 2	Mbps
				$C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$							
			2.7 V ≤ EV _{DD0} < 4.0 V,			Note 3		Note 3		Note 3	bps
			2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate		1.2 Note 4		1.2 Note 4		1.2 Note 4	Mbps
				$C_b = 50 \text{ pF}, R_b =$ 2.7 k Ω , $V_b = 2.3 \text{ V}$							
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			Notes 5, 6		Notes 5, 6		Notes 5, 6	bps
				Theoretical value of the maximum transfer rate		0.43 Note 7		0.43 Note 7		0.43 Note 7	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$							

Notes 1. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V ≤ EV_{DD0} ≤ 5.5 V and 2.7 V ≤ V_b ≤ 4.0 V

$$\label{eq:maximum transfer rate} \text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1-\frac{2.2}{V_b})\} \times 3} \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- 2. This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.

Notes 3. The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V \leq EV_{DDO} < 4.0 V and 2.3 V \leq V_b \leq 2.7 V

$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.
- 5. Use it with EVDD0 ≥ Vb.
- **6.** The smaller maximum transfer rate derived by using fmck/6 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 1.8 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

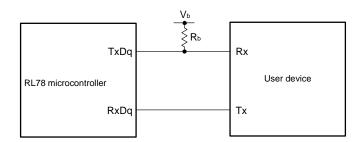
Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{1.5}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln(1 - \frac{1.5}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

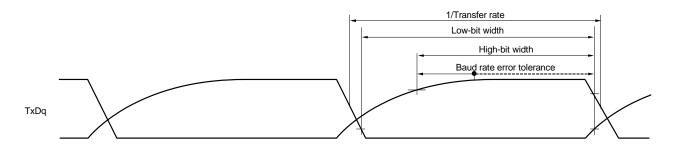
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **7.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 6 above to calculate the maximum transfer rate under conditions of the customer.

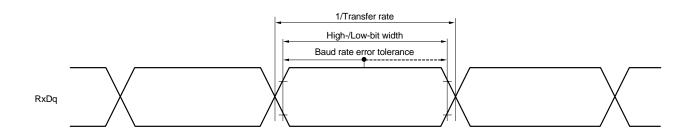
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpd tolerance (When 20- to 52-pin products)/EVpd tolerance (When 64- to 128-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For Viii and Viii, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** $R_b[\Omega]$:Communication line (TxDq) pull-up resistance,
 - $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high	h-speed Mode	LS (low main)	•	LV (low- main)		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tксү1 ≥ 2/fcLK	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	200		1150		1150		ns
			$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	300		1150		1150		ns
			$C_b=20~pF,~R_b=2.7~k\Omega$							
SCKp high-level width	t _{KH1}	4.0 V ≤ EV _{DD} 0 2.7 V ≤ V _b ≤ 4		tксү1/2 — 50		tксү1/2 — 50		tксу1/2 — 50		ns
		C _b = 20 pF, R	b = 1.4 kΩ							
		2.7 V ≤ EV _{DD} 0 2.3 V ≤ V _b ≤ 2	,	tксу1/2 — 120		tксу1/2 — 120		tксу1/2 — 120		ns
		C _b = 20 pF, R	b = 2.7 kΩ							
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD} 0 2.7 V ≤ V _b ≤ 4	,	tксу1/2 — 7		tксү1/2 — 50		tксү1/2 — 50		ns
		C _b = 20 pF, R	b = 1.4 kΩ							
		2.7 V ≤ EV _{DD} 0 2.3 V ≤ V _b ≤ 2	·	tксү1/2 — 10		tксү1/2 — 50		tксү1/2 — 50		ns
		C _b = 20 pF, R	_b = 2.7 kΩ							
SIp setup time (to SCKp↑) Note 1	tsik1	4.0 V ≤ EV _{DD0} 2.7 V ≤ V _b ≤ 4	,	58		479		479		ns
		C _b = 20 pF, R	b = 1.4 kΩ							
		2.7 V ≤ EV _{DD} 0 2.3 V ≤ V _b ≤ 2		121		479		479		ns
		C _b = 20 pF, R	b = 2.7 kΩ							
SIp hold time (from SCKp↑) Note 1	tksi1	4.0 V ≤ EV _{DD} 0 2.7 V ≤ V _b ≤ 4		10		10		10		ns
		C _b = 20 pF, R	b = 1.4 kΩ							
		2.7 V ≤ EV _{DD} 0 2.3 V ≤ V _b ≤ 2	,	10		10		10		ns
		C _b = 20 pF, R	b = 2.7 kΩ							
Delay time from SCKp↓ to SOp	tkso1	4.0 V ≤ EV _{DD0} 2.7 V ≤ V _b ≤ 4			60		60		60	ns
output Note 1		C _b = 20 pF, R	b = 1.4 kΩ							
		2.7 V ≤ EV _{DD0} 2.3 V ≤ V _b ≤ 2	·		130		130		130	ns
		C _b = 20 pF, R								

(Notes, Caution, and Remarks are listed on the next page.)

(7) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	, ,	h-speed Mode	,	v-speed Mode	,	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↓) Note 2	tsıĸ1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	23		110		110		ns
		$C_b = 20 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	33		110		110		ns
		$C_b=20~pF,~R_b=2.7~k\Omega$							
SIp hold time (from SCKp↓) Note 2	t KSI1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	10		10		10		ns
		$C_b=20~pF,~R_b=1.4~k\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	10		10		10		ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		10		10		10	ns
SOp output Note 2		$C_b=20~pF,~R_b=1.4~k\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		10		10		10	ns
		$C_b = 20 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

- Remarks 1. R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM number (g = 1)
 - 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,
 n: Channel number (mn = 00))
 - 4. This value is valid only when CSI00's peripheral I/O redirect function is not used.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3) (T_A = −40 to +85°C, 1.8 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V)

Parameter	Symbol		Conditions	, -	h-speed Mode	,	/-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	300		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	500		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
			$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note}},$	1150		1150		1150		ns
			$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SCKp high-level width	tкн1		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$			tксү1/2 — 75		tксү1/2 — 75		ns
		C _b = 30 pF, R _b	$R_b = 1.4 \text{ k}\Omega$							
		2.7 V ≤ EV _{DD} 2.3 V ≤ V _b ≤ 2		tксу1/2 — 170		tkcy1/2 – 170		tксү1/2 –		ns
		Сь = 30 pF, F	$R_b = 2.7 \text{ k}\Omega$							
		1.8 V ≤ EV _{DD} 1.6 V ≤ V _b ≤ 2		tксү1/2 — 458		tксү1/2 — 458		tксү1/2 — 458		ns
		C _b = 30 pF, F	$R_b = 5.5 \text{ k}\Omega$							
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD} 2.7 V ≤ V _b ≤ 4	•	tксу1/2 — 12		tксү1/2 – 50		tксү1/2 – 50		ns
		C _b = 30 pF, F	$R_b = 1.4 \text{ k}\Omega$							
		2.7 V ≤ EV _{DD} 2.3 V ≤ V _b ≤ 2	•	tксу1/2 — 18		tkcy1/2 - 50		tkcy1/2 - 50		ns
		C _b = 30 pF, F	$R_b = 2.7 \text{ k}\Omega$							
		1.8 V ≤ EV _{DD} 1.6 V ≤ V _b ≤ 2		tксү1/2 — 50		tксү1/2 — 50		tксү1/2 — 50		ns
		C _b = 30 pF, F	$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							

Note Use it with $EV_{DD0} \ge V_b$.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	` `	h-speed Mode	` '	peed main) ode	`	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SIp setup time (to SCKp↑) Note 1	tsıkı	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	81		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	177		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$	479		479		479		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
SIp hold time (from SCKp↑) Note 1	t _{KSI1}	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$	19		19		19		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$		100		100		100	ns
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$							
	op output	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		195		195		195	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$							
		$\begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array}$		483		483		483	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$							

Notes

- 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
- 2. Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

Parameter	Symbol	Conditions		h-speed Mode	, ,	peed main) ode	,	-voltage Mode	Unit	
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SIp setup time (to SCKp↓) Note 1	tsıĸ1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	44		110		110		ns	
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$								
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	44		110		110		ns	
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$								
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$	110		110		110		ns	
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$								
SIp hold time (from SCKp↓) Note 1	t _{KSI1}	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	19		19		19		ns	
		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$								
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	19		19		19		ns	
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$								
		$ \begin{array}{l} 1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \end{array} $	19		19		19		ns	
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$								
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$		25		25		25	ns	
SOp output Note 1		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$								
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		25		25		25	ns	
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$								

Notes

 $C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$ 1. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

 $1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}},$

2. Use it with EV_{DD0} ≥ V_b.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (When 20- to 52-pin products)/EVDD tolerance (When 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

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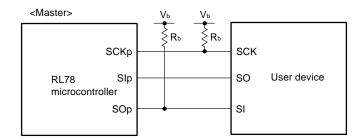
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25

ns

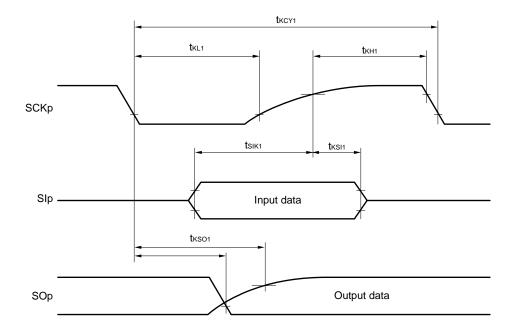
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

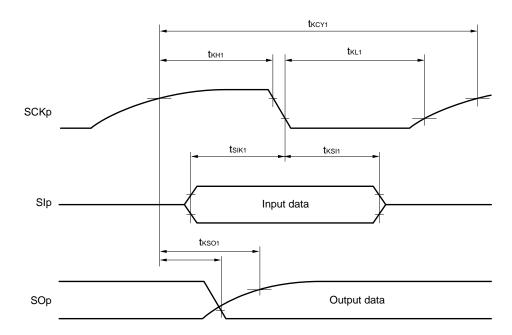


- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol	Со	nditions		h-speed Mode		v-speed Mode	-	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	24 MHz < fмск	14/ fмск		-		-		ns
			20 MHz < fмcк ≤ 24 MHz	12/ fмск		-		-		ns
			8 MHz < fмcк ≤ 20 MHz	10/ fмск		-		_		ns
			4 MHz < fMCK ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		2.3 V ≤ V _b ≤ 2.7 V	24 MHz < fмск	20/ fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/ fмск		-		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/ fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/ fмск		-		_		ns
			4 MHz < fmck ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			f _{MCK} ≤ 4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		1.8 $V \le EV_{DDO} < 3.3 V$, 1.6 $V \le V_b \le 2.0 V^{Note 2}$		48/ fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	36/ fмск		-		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/ fмск		ı		_		ns
			8 MHz < fмск ≤ 16 MHz	26/ fмск		_		_		ns
		41	4 MHz < fмск ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/2)

Parameter	Symbol	Conditions	, ,	h-speed Mode	`	v-speed Mode	LV (low-voltage main) Mode		Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp high-/low-level width	tkH2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V, 2.7 V ≤ V _b ≤ 4.0 V	tксу2/2 — 12		tkcy2/2 - 50		tксү2/2 - 50		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	tkcy2/2 —		tксү2/2 - 50		txcy2/2 - 50		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note 2}}$	tkcy2/2 -		tксү2/2 - 50		txcy2/2 - 50		ns
SIp setup time (to SCKp↑) Note 3	tsik2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	1/fмск + 20		1/fмск + 30		1/fмск + 30		ns
		1.8 V \leq EV _{DD0} $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V ^{Note 2}	1/fмск + 30		1/fмск + 30		1/fмск + 30		ns
SIp hold time (from SCKp↑) Note 4	tksi2		1/fмск + 31		1/fмск + 31		1/fмск + 31		ns
Delay time from SCKp↓ to SOp output	tkso2	$ 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, R_{\text{b}} = 1.4 \text{ k}\Omega $		2/fмск + 120		2/fмск + 573		2/fмск + 573	ns
Note 5				2/fмск + 214		2/fмск + 573		2/fмск + 573	ns
		$\begin{split} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V^{Note 2}, \\ C_{b} &= 30 \ pF, \ R_{b} = 5.5 \ k \Omega \end{split}$		2/fмск + 573		2/fмск + 573		2/fмск + 573	ns

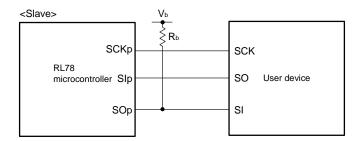
Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

- **2.** Use it with $EV_{DD0} \ge V_b$.
- 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

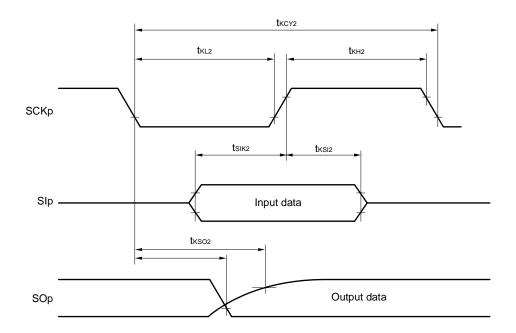
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

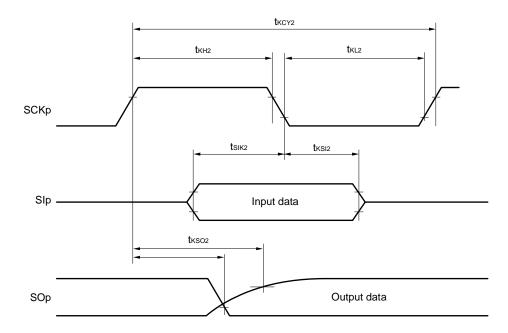


- Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - 2. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

(TA = -40 to +85°C, 1.8 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Conditions Conditions	HS (hig	h-speed Mode	LS (low		`	v-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLr clock frequency	fscL	$\begin{aligned} 4.0 \ V &\leq E V_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $		1000 Note 1		300 Note 1		300 Note 1	kHz
		$ \begin{aligned} &4.0 \; V \leq EV_{DD0} \leq 5.5 \; V, \\ &2.7 \; V \leq V_b \leq 4.0 \; V, \\ &C_b = 100 \; pF, \; R_b = 2.8 \; k\Omega \end{aligned} $		400 Note 1		300 Note 1		300 Note 1	kHz
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 100 \ pF, \ R_b = 2.7 \ k\Omega $		400 Note 1		300 Note 1		300 ote 1	kHz
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DD0}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{split}$		300 Note 1		300 Note 1		300 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	475		1550		1550		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	475		1550		1550		ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$	1150		1550		1550		ns
		2.7 V \leq EV _{DD0} $<$ 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 k Ω	1150		1550		1550		ns
		$\begin{split} 1.8 \ V &\leq EV_{DDO} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V^{Note2}, \\ C_{b} &= 100 \ pF, \ R_{b} = 5.5 \ k\Omega \end{split}$	1550		1550		1550		ns
Hold time when SCLr = "H"	tніgн	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	245		610		610		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	200		610		610		ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ kΩ}$	675		610		610		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	600		610		610		ns
		$\begin{split} &1.8 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega \end{split}$	610		610		610		ns

(10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

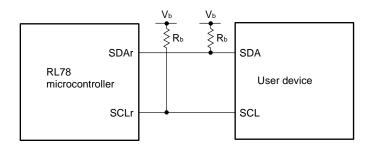
Parameter	Symbol	Conditions	HS (high	•	`	/-speed Mode	•	-voltage Mode	Unit
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu:dat	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/f _{MCK} + 135 Note 3		1/fMCK + 190 Note 3		1/fмск + 190 Note 3		kHz
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	1/fмск + 135 Note 3		1/fmck + 190 Note 3		1/fмск + 190 Note 3		kHz
			1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
			1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz
	$ \begin{aligned} &1.8 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ &1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}^{\text{Note 2}}, \\ &C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 k\Omega \end{aligned} $	1/fмск + 190 Note 3		1/fmck + 190 Note 3		1/fmck + 190 Note 3		kHz	
Data hold time (transmission)	thd:dat	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	305	0	305	0	305	ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$	0	355	0	355	0	355	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	355	0	355	0	355	ns
		$\begin{aligned} 1.8 \ V &\leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V &\leq V_{b} \leq 2.0 \ V^{ \text{Note 2}}, \\ C_{b} &= 100 \ pF, \ R_{b} = 5.5 \ k\Omega \end{aligned}$	0	405	0	405	0	405	ns

- Notes 1. The value must also be equal to or less than fmck/4.
 - 2. Use it with EV_{DD0} ≥ V_b.
 - 3. Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

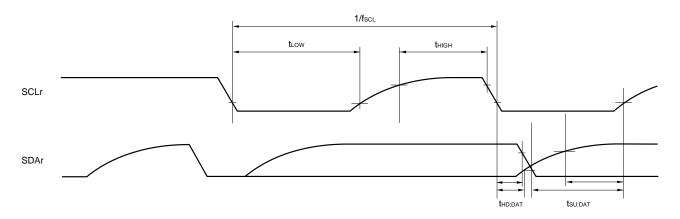
Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the next page.)

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage

- 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13)

2.5.2 Serial interface IICA

(1) I²C standard mode

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions		h-speed Mode	`	v-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard mode:	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
		fclk≥ 1 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV _{DD0} ≤ 5.5 V		_	0	100	0	100	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD0} ≤ 5.9	5 V		_	4.7		4.7		μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		.6 V ≤ EV _{DD0} ≤ 5.5 V		-	-	4.0		4.0		μs
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.	2.7 V ≤ EV _{DD0} ≤ 5.5 V			4.7		4.7		μs
" <u>L</u> "		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.6 V ≤ EV _{DD0} ≤ 5.9	5 V		_	4.7		4.7		μs
Hold time when SCLA0 =	thigh	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
"H"		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	4.0		4.0		μs
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	250		250		250		ns
		1.6 V ≤ EV _{DD0} ≤ 5.9	5 V		_	250		250		ns
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
(transmission)Note 2		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	3.45	0	3.45	0	3.45	μs
		1.6 V ≤ EV _{DD0} ≤ 5.5	5 V		_	0	3.45	0	3.45	μs
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.0		4.0		4.0		μs
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		4.0		4.0		4.0		μs
		1.6 V ≤ EV _{DD0} ≤ 5.5 V		-		4.0		4.0		μs
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
		1.7 V ≤ EV _{DD0} ≤ 5.	5 V	4.7		4.7		4.7		μs
	1.6 V ≤ EV _{DD0} ≤		5 V			4.7		4.7		μs

(Notes, Caution and Remark are listed on the next page.)



- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.
- Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.
- **Remark** The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$

(2) I2C fast mode

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Со	nditions	` `	h-speed Mode	,	v-speed Mode	`	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode:	2.7 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
		fclk≥ 3.5 MHz	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	400	0	400	0	400	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
"L"	1.8 V ≤ EV _{DD}	1.8 V ≤ EV _{DD0} ≤ 5.	5 V	1.3		1.3		1.3		μs
Hold time when SCLA0 =	tніgн	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
"H"		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	100		100		100		μs
(reception)		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	100		100		100		μs
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0	0.9	0	0.9	0	0.9	μs
(transmission)Note 2		1.8 V ≤ EV _{DD0} ≤ 5.	5 V	0	0.9	0	0.9	0	0.9	μs
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.	5 V	0.6		0.6		0.6		μs
condition		1.8 V ≤ EV _{DD0} ≤ 5.	1.8 V ≤ EV _{DD0} ≤ 5.5 V			0.6		0.6		μs
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		1.3		1.3		1.3		μs

- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

(3) I²C fast mode plus

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	, ,	h-speed Mode	,	v-speed Mode	-	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode plus: fcLk ≥ 10 MHz			1000	_		_		kHz
Setup time of restart condition	tsu:sta	2.7 V ≤ EV _{DD0} ≤ 5.5	.7 V ≤ EV _{DD0} ≤ 5.5 V			_		_	-	μs
Hold time ^{Note 1}	thd:sta	2.7 V ≤ EV _{DD0} ≤ 5.5	7 V ≤ EV _{DD0} ≤ 5.5 V			-		_		μs
Hold time when SCLA0 = "L"	tLOW	2.7 V ≤ EV _{DD0} ≤ 5.5	2.7 V ≤ EV _{DD0} ≤ 5.5 V			_		_		μs
Hold time when SCLA0 = "H"	thigh	2.7 V ≤ EV _{DD0} ≤ 5.5	5 V	0.26		-		-	-	μs
Data setup time (reception)	tsu:dat	2.7 V ≤ EV _{DD0} ≤ 5.5	5 V	50		_	-	-	-	μs
Data hold time (transmission) ^{Note 2}	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.5	5 V	0	0.45	_	-	-	-	μs
Setup time of stop condition	tsu:sto	2.7 V ≤ EV _{DD0} ≤ 5.5	.7 V ≤ EV _{DD0} ≤ 5.5 V			-	-	-	-	μs
Bus-free time	tbuf	2.7 V ≤ EV _{DD0} ≤ 5.5	5 V	0.5		_	-	-	-	μs

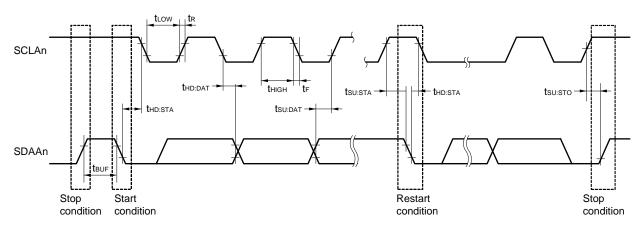
- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IoH1, IoL1, VoH1, VoL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Fast mode plus: $C_b = 120 \text{ pF}$, $R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

2.6 Analog Characteristics

2.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage	
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = VBGR
Input channel	Reference voltage (–) = AVREFM	Reference voltage (–) = Vss	Reference voltage (–) = AVREFM
ANI0 to ANI14	Refer to 2.6.1 (1) .	Refer to 2.6.1 (3).	Refer to 2.6.1 (4).
ANI16 to ANI26	Refer to 2.6.1 (2) .		
Internal reference voltage	Refer to 2.6.1 (1) .		_
Temperature sensor output			
voltage			

(1) When reference voltage (+)= AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +85°C, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin: ANI2 to ANI14	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±0.50	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR
		AVREFP = VDD Note 3	1.6 V ≤ AVREFP ≤ 5.5 V Note 4			±0.50	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±5.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±1.5	LSB
		AVREFP = VDD Note 3	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 4			±2.0	LSB
Analog input voltage	Vain	ANI2 to ANI14		0		AVREFP	V
	Internal reference voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (h		igh-speed main) mode)	V _{BGR} Note 5			V
		Temperature sensor output (2.4 V ≤ VDD ≤ 5.5 V, HS (h	V _{TMPS25} Note 5			V	

(Notes are listed on the next page.)

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.
 - Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.
 - 4. Values when the conversion time is set to 57 μs (min.) and 95 μs (max.).
 - 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditi	ons	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target ANI pin : ANI16 to	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
		ANI26	1.8 V ≤ VDD ≤ 5.5 V	17		39	μs
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs
Zero-scale errorNotes 1, 2	Ezs	F\/DD0 - Δ\/DEED - \/DD Notes 3, 4	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
			1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5			±6.0	LSB
Differential linearity	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
error Note 1		EVDD0 = AVREFP = VDD Notes 3, 4	1.6 V ≤ AV _{REFP} ≤ 5.5 V Note 5	_		±2.5	LSB
Analog input voltage	VAIN	ANI16 to ANI26		0		AV _{REFP} and EV _{DD0}	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ±1.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ±4.0 LSB to the MAX. value when AVREFP = VDD.

Zero-scale error/Full-scale error: Add ±0.20%FSR to the MAX. value when AVREFP = VDD.

Integral linearity error/ Differential linearity error: Add ± 2.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{DD}, \text{Reference voltage (-)} = \text{V}_{SS})$

Parameter	Symbol	Condition	ns	MIN.	TYP.	MAX.	Unit		
Resolution	RES			8		10	bit		
Overall errorNote 1	AINL	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB		
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3		1.2	±10.5	LSB		
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs		
		Target pin: ANI0 to ANI14,	2.7 V ≤ V _{DD} ≤ 5.5 V	3.1875		39	μs		
		ANI16 to ANI26	1.8 V ≤ VDD ≤ 5.5 V	17		39	μs		
			1.6 V ≤ VDD ≤ 5.5 V	57		95	μs		
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs		
		Target pin: Internal	2.7 V ≤ V _{DD} ≤ 5.5 V	3.5625		39	μs		
		reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs		
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	1.8 V ≤ VDD ≤ 5.5 V			±0.60	%FSR		
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±0.85	%FSR		
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR		
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±0.85	%FSR		
Integral linearity errorNote 1	ILE	10-bit resolution	1.8 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB		
			1.6 V ≤ V _{DD} ≤ 5.5 V Note 3			±6.5	LSB		
Differential linearity error Note 1	DLE	10-bit resolution	1.8 V ≤ VDD ≤ 5.5 V			±2.0	LSB		
			$1.6 \text{ V} \leq \text{VDD} \leq 5.5 \text{ V}$ Note 3			±2.5	LSB		
Analog input voltage	Vain	ANI0 to ANI14		0		V _{DD}	V		
		ANI16 to ANI26		0		EV _{DD0}	V		
		Internal reference voltage (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)		V _{BGR} Note 4			V		
			Temperature sensor output voltage (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-speed main) mode)			V _{TMPS25} Note 4			

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. When the conversion time is set to 57 μs (min.) and 95 μs (max.).
- 4. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{BGR}^{Note 3}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V}^{Note 4}, \text{HS (high-speed main) mode)}$

Parameter	Symbol	Cond	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±1.0	LSB
Analog input voltage	VAIN			0		V _{BGR} Note 3	V

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.
 - 4. When reference voltage (-) = Vss, the MAX. values are as follows.
 Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM.
 Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM.
 Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

2.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +85°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

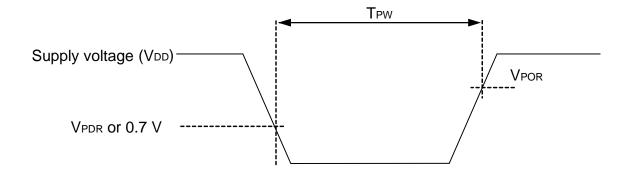
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.05		٧
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

2.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	V _{POR}	The power supply voltage is rising.		1.51	1.55	V
	V _{PDR}	The power supply voltage is falling.	1.46	1.50	1.54	V
Minimum pulse width ^{Note}	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



2.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _L VD0	The power supply voltage is rising.	3.98	4.06	4.14	V
voltage			The power supply voltage is falling.	3.90	3.98	4.06	V
		V _{LVD1}	The power supply voltage is rising.	3.68	3.75	3.82	V
			The power supply voltage is falling.	3.60	3.67	3.74	V
		V _{LVD2}	The power supply voltage is rising.	3.07	3.13	3.19	V
			The power supply voltage is falling.	3.00	3.06	3.12	V
		V _{LVD3}	The power supply voltage is rising.	2.96	3.02	3.08	V
			The power supply voltage is falling.	2.90	2.96	3.02	V
		V _{LVD4}	The power supply voltage is rising.	2.86	2.92	2.97	V
			The power supply voltage is falling.	2.80	2.86	2.91	V
		V _{LVD5}	The power supply voltage is rising.	2.76	2.81	2.87	V
			The power supply voltage is falling.	2.70	2.75	2.81	V
		V _{LVD6}	The power supply voltage is rising.	2.66	2.71	2.76	V
			The power supply voltage is falling.	2.60	2.65	2.70	V
		V _{LVD7}	The power supply voltage is rising.	2.56	2.61	2.66	V
			The power supply voltage is falling.	2.50	2.55	2.60	V
		V _{LVD8}	The power supply voltage is rising.	2.45	2.50	2.55	V
			The power supply voltage is falling.	2.40	2.45	2.50	V
		V _{LVD9}	The power supply voltage is rising.	2.05	2.09	2.13	V
			The power supply voltage is falling.	2.00	2.04	2.08	V
		V _L VD10	The power supply voltage is rising.	1.94	1.98	2.02	V
			The power supply voltage is falling.	1.90	1.94	1.98	V
		VLVD11	The power supply voltage is rising.	1.84	1.88	1.91	V
			The power supply voltage is falling.	1.80	1.84	1.87	V
		V _{LVD12}	The power supply voltage is rising.	1.74	1.77	1.81	V
			The power supply voltage is falling.	1.70	1.73	1.77	V
		V _L VD13	The power supply voltage is rising.	1.64	1.67	1.70	V
			The power supply voltage is falling.	1.60	1.63	1.66	V
Minimum pu	lse width	tuw		300			μs
Detection de	elay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

(TA = -40 to +85°C, VPDR \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	VLVDA0	VPOC2,	VPOC1, VPOC0 = 0, 0, 0,	falling reset voltage	1.60	1.63	1.66	V
mode	VLVDA1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.74	1.77	1.81	V
				Falling interrupt voltage	1.70	1.73	1.77	V
	VLVDA2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	1.84	1.88	1.91	V
				Falling interrupt voltage	1.80	1.84	1.87	V
	V _L VDA3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _L VDB0	VPOC2,	VPOC1, VPOC0 = 0, 0, 1,	falling reset voltage	1.80	1.84	1.87	V
	V _L VDB1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	1.94	1.98	2.02	V
				Falling interrupt voltage	1.90	1.94	1.98	V
	V _{LVDB2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.05	2.09	2.13	V
				Falling interrupt voltage	2.00	2.04	2.08	V
V	V _L VDB3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.07	3.13	3.19	V
				Falling interrupt voltage	3.00	3.06	3.12	V
	V _L VDC0	VPOC2,	VPOC1, VPOC0 = 0, 1, 0,	falling reset voltage	2.40	2.45	2.50	V
	V _L VDC1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.56	2.61	2.66	V
				Falling interrupt voltage	2.50	2.55	2.60	V
	V _L VDC2		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.66	2.71	2.76	V
				Falling interrupt voltage	2.60	2.65	2.70	V
	V _L VDC3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.68	3.75	3.82	V
				Falling interrupt voltage	3.60	3.67	3.74	V
	V _L VDD0	VPOC2,	VPOC1, VPOC0 = 0, 1, 1,	falling reset voltage	2.70	2.75	2.81	V
	V _L VDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.86	2.92	2.97	V
				Falling interrupt voltage	2.80	2.86	2.91	V
	V _{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.96	3.02	3.08	V
				Falling interrupt voltage	2.90	2.96	3.02	V
	V _L VDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.98	4.06	4.14	V
				Falling interrupt voltage	3.90	3.98	4.06	V

2.6.5 Power supply voltage rising slope characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

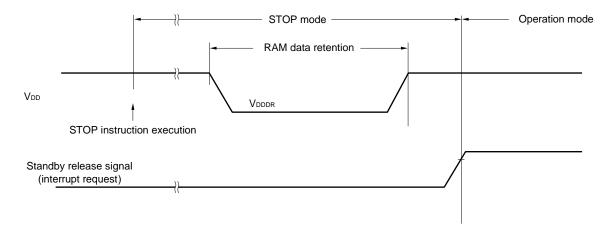
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 2.4 AC Characteristics.

2.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.46 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



2.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock frequency	fclk	1.8 V ≤ VDD ≤ 5.5 V	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Notes 1. 1 erase + 1 write after the erase is regarded as 1 rewrite.

The retaining years are until next rewrite after the rewrite.

- 2. When using flash memory programmer and Renesas Electronics self programming library
- **3.** These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

2.9 Dedicated Flash Memory Programmer Communication (UART)

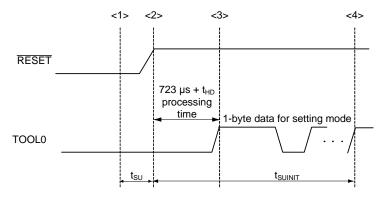
$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнo	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS T_A = -40 to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to +105°C R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product in the RL78/G13 User's Manual.
 - 4. Please contact Renesas Electronics sales office for derating of operation under T_A = +85°C to +105°C. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see 2. ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to +105°C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Арр	lication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode	HS (high-speed main) mode:	HS (high-speed main) mode only:
Operating voltage range	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 32 MHz	2.7 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 32 MHz
	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz	2.4 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 16 MHz
	LS (low-speed main) mode:	
	1.8 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 8 MHz	
	LV (low-voltage main) mode:	
	1.6 V ≤ V _{DD} ≤ 5.5 V@1 MHz to 4 MHz	
High-speed on-chip oscillator clock	1.8 V ≤ V _{DD} ≤ 5.5 V	2.4 V ≤ V _{DD} ≤ 5.5 V
accuracy	±1.0%@ T _A = -20 to +85°C	±2.0%@ T _A = +85 to +105°C
	±1.5%@ T _A = -40 to -20°C	±1.0%@ T _A = -20 to +85°C
	1.6 V ≤ V _{DD} < 1.8 V	±1.5%@ T _A = -40 to -20°C
	±5.0%@ T _A = -20 to +85°C	
	±5.5%@ T _A = -40 to -20°C	
Serial array unit	UART	UART
	CSI: fclk/2 (supporting 16 Mbps), fclk/4	CSI: fclk/4
	Simplified I ² C communication	Simplified I ² C communication
IICA	Normal mode	Normal mode
	Fast mode	Fast mode
	Fast mode plus	
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V	Rise detection voltage: 2.61 V to 4.06 V
	(14 levels)	(8 levels)
	Fall detection voltage: 1.63 V to 3.98 V	Fall detection voltage: 2.55 V to 3.98 V
	(14 levels)	(8 levels)

(Remark is listed on the next page.)



Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25^{\circ}C$) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	V
	EV _{DD0} , EV _{DD1}	EV _{DD0} = EV _{DD1}	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	VII	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 ^{Note 2}	V
	Vı2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	Vo ₁	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-0.3 to EV _{DD0} +0.3 and -0.3 to V _{DD} +0.3 Note 2	V
	Vo ₂	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	V
Analog input voltage	Val1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V
	VAI2	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 ^{Notes 2, 3}	V

- Notes 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - 2. AVREF (+): + side reference voltage of the A/D converter.
 - 3. Vss: Reference voltage

Absolute Maximum Ratings (TA = 25°C) (2/2)

Parameter	Symbols		Conditions	Ratings	Unit
Output current, high	Іон1	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	-40	mA
		Total of all pins –170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	- 70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	–100	mA
	Iон ₂	Per pin	P20 to P27, P150 to P156	-0.5	mA
		Total of all pins		-2	mA
Output current, low	lo _{L1}	Per pin	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	40	mA
		Total of all pins 170 mA	P00 to P04, P07, P32 to P37, P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	70	mA
			P05, P06, P10 to P17, P30, P31, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147	100	mA
	lo _{L2}	Per pin	P20 to P27, P150 to P156	1	mA
		Total of all pins		5	mA
Operating ambient	TA	In normal operation	on mode	-40 to +105	°C
temperature		In flash memory p	programming mode		
Storage temperature	T _{stg}			-65 to +150	°C

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

3.2 Oscillator Characteristics

3.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation	Ceramic resonator/	2.7 V ≤ V _{DD} ≤ 5.5 V	1.0		20.0	MHz
frequency (fx) ^{Note}	crystal resonator	2.4 V ≤ V _{DD} < 2.7 V	1.0		16.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to **5.4 System Clock Oscillator** in the RL78/G13 User's Manual.

3.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fıн			1		32	MHz
High-speed on-chip oscillator		−20 to +85°C	2.4 V ≤ V _{DD} ≤ 5.5 V	-1.0		+1.0	%
clock frequency accuracy		-40 to -20°C	2.4 V ≤ V _{DD} ≤ 5.5 V	-1.5		+1.5	%
		+85 to +105°C	2.4 V ≤ V _{DD} ≤ 5.5 V	-2.0		+2.0	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

3.3 DC Characteristics

3.3.1 Pin characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	Іон1	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	2.4 V ≤ EVDD0 ≤ 5.5 V			-3.0 Note 2	mA
		P40 to P47, P102 to P106, P120, P125 to P127, P130, P140 to P145	4.0 V ≤ EV _{DD0} ≤ 5.5 V			-30.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			-10.0	mA
			2.4 V ≤ EV _{DD0} < 2.7 V			-5.0	mA
			4.0 V ≤ EV _{DD0} ≤ 5.5 V			-30.0	mA
		P50 to P57, P64 to P67, P70 to P77, P80 to	2.7 V ≤ EV _{DD0} < 4.0 V			-19.0	mA
		P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% Note 3)	2.4 V ≤ EV _{DD0} < 2.7 V			-10.0	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ EV _{DD0} ≤ 5.5 V			-60.0	mA
	І он2	Per pin for P20 to P27, P150 to P156	2,4 V ≤ V _{DD} ≤ 5.5 V			-0.1 ^{Note 2}	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2.4 V ≤ V _{DD} ≤ 5.5 V			-1.5	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from the EV_{DD0}, EV_{DD1}, V_{DD} pins to an output pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor \leq 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoH = -10.0 mA

Total output current of pins = $(-10.0 \times 0.7)/(80 \times 0.01) \approx -8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

- Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.
- **Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (2/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, low ^{Note 1}	lo _{L1}	Per pin for P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147				8.5 Note 2	mA
		Per pin for P60 to P63				15.0 Note 2	mA
		Total of P00 to P04, P07, P32 to P37,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			40.0	mA
		to P127, P130, P140 to P145	2.7 V ≤ EV _{DD0} < 4.0 V			15.0	mA
			2.4 V ≤ EV _{DD0} < 2.7 V			9.0	mA
		P31, P50 to P57, P60 to P67,	4.0 V ≤ EV _{DD0} ≤ 5.5 V			40.0	mA
			2.7 V ≤ EV _{DD0} < 4.0 V			35.0	mA
		P70 to P77, P80 to P87, P90 to P97, P100, P101, P110 to P117, P146, P147 (When duty ≤ 70% Note 3)	2,4 V ≤ EV _{DD0} < 2.7 V			20.0	mA
		Total of all pins (When duty ≤ 70% Note 3)				80.0	mA
	lo _{L2}	Per pin for P20 to P27, P150 to P156				0.4 Note 2	mA
		Total of all pins (When duty ≤ 70% ^{Note 3})	2,4 V ≤ V _{DD} ≤ 5.5 V			5.0	mA

- **Notes 1**. Value of current at which the device operation is guaranteed even if the current flows from an output pin to the EVsso, EVss1 and Vss pin.
 - 2. Do not exceed the total current value.
 - 3. Specification under conditions where the duty factor ≤ 70%.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

• Total output current of pins = $(lol \times 0.7)/(n \times 0.01)$

<Example> Where n = 80% and IoL = 10.0 mA

Total output current of pins = $(10.0 \times 0.7)/(80 \times 0.01) \approx 8.7$ mA

However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (3/5)

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EVDD0		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	V
-	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCLKS	0.8V _{DD}		V _{DD}	V	
Input voltage, low	VIL1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	V
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	VIL4	P60 to P63		0		0.3EV _{DD0}	V
	VIL5	P121 to P124, P137, EXCLK, EXCLKS	, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (4/5)

Items Symbol		Conditions			TYP.	MAX.	Unit
Output voltage, high	Vон1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} - 0.7			V
		P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147 2.	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} - 0.6			V
Von			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -1.5 mA	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH2} = -100 \mu\text{A}$	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67,	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 8.5 mA			0.7	V
		P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 3.0 mA			0.6	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 1.5 mA			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL1 = 0.6 mA			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \mu\text{A}$			0.4	V
	Vol3	P60 to P63	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $\text{Io}_{\text{L3}} = 15.0 \text{ mA}$			2.0	V
			$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 5.0 mA			0.4	V
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 3.0 mA			0.4	V
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ IoL3 = 2.0 mA			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ (5/5)

Items	Symbol	Condit	ions		MIN.	TYP.	MAX.	Unit
Input leakage current, high	lun1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vi = EVDDO	Vi = EVDDO			1	μА
	ILIH2	P20 to P27, P1 <u>37,</u> P150 to P156, RESET	VI = VDD				1	μΑ
	Ішнз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	VI = VDD	In input port or external clock input			1	μА
				In resonator connection			10	μΑ
Input leakage current, low	lui.1	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Vı = EVsso				-1	μА
	ILIL2	P20 to P27, P137, P150 to P156, RESET	Vı = Vss				-1	μΑ
	Ішз	P121 to P124 (X1, X2, XT1, XT2, EXCLK, EXCLKS)	Vı = Vss	In input port or external clock input			-1	μΑ
				In resonator connection			-10	μΑ
On-chip pll-up resistance	Ru	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	VI = EVsso	, In input port	10	20	100	kΩ

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = 0 \text{ V}) (1/2)$

Parameter	Symbol			Conditions	3		MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}	Operating	HS (high-	f _{IH} = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.1		mA
Current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.1		mA
			mode		Normal	V _{DD} = 5.0 V		4.6	7.5	mA
					operation	V _{DD} = 3.0 V		4.6	7.5	mA
				fin = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		3.7	5.8	mA
					operation	V _{DD} = 3.0 V		3.7	5.8	mA
			fin = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		2.7	4.2	mA	
				operation	V _{DD} = 3.0 V		2.7	4.2	mA	
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.9	mA
	speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.2	5.0	mA		
			mode Note 3	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.9	mA
		V _{DD} = 3.0 V	operation	Resonator connection		3.2	5.0	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.9	mA
				V _{DD} = 5.0 V	operation	Resonator connection		1.9	2.9	mA
		$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.9	mA		
		V _{DD} = 3.0 V	operation	Resonator connection		1.9	2.9	mA		
			Subsystem clock operation	fsuB = 32.768 kHz	Normal	Square wave input		4.1	4.9	μΑ
					operation	Resonator connection		4.2	5.0	μΑ
				T _A = -40°C	Normal operation					
				fsuB = 32.768 kHz		Square wave input		4.1	4.9	μA
				T _A = +25°C		Resonator connection		4.2	5.0	μA
				fsuB = 32.768 kHz Normal	Square wave input		4.2	5.5	μΑ	
				Note 4	operation	Resonator connection		4.3	5.6	μΑ
				T _A = +50°C						
				fsuB = 32.768 kHz	Normal	Square wave input		4.3	6.3	μA
				Note 4	operation	Resonator connection		4.4	6.4	μA
				T _A = +70°C						
				fsuв = 32.768 kHz	Normal	Square wave input		4.6	7.7	μA
				Note 4 operation	operation	Resonator connection		4.7	7.8	μA
				T _A = +85°C						
				fsuв = 32.768 kHz	Normal	Square wave input		6.9	19.7	μΑ
				Note 4	operation	Resonator connection		7.0	19.8	μA
				T _A = +105°C						

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD and EVDDO, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDO or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz $2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V} @1 \text{ MHz to } 16 \text{ MHz}$
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (TA = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT	HS (high-	fih = 32 MHz Note 4	V _{DD} = 5.0 V		0.54	2.90	mA
current Note 1	Note 2	mode	speed main) mode Note 7		V _{DD} = 3.0 V		0.54	2.90	mA
Note 1				f _{IH} = 24 MHz Note 4	V _{DD} = 5.0 V		0.44	2.30	mA
					V _{DD} = 3.0 V		0.44	2.30	mA
				fih = 16 MHz Note 4	V _{DD} = 5.0 V		0.40	1.70	mA
					V _{DD} = 3.0 V		0.40	1.70	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.90	mA
		speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.45	2.00	mA	
			$f_{MX} = 20 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.28	1.90	mA	
			V _{DD} = 3.0 V	Resonator connection		0.45	2.00	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.02	mA
				V _{DD} = 5.0 V	Resonator connection		0.26	1.10	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 3}},$	Square wave input		0.19	1.02	mA
			VDD = 3.0 V	Resonator connection		0.26	1.10	mA	
		Subsystem	fsub = 32.768 kHz ^{Note 5}	Square wave input		0.25	0.57	μΑ	
			clock operation	T _A = -40°C	Resonator connection		0.44	0.76	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.30	0.57	μΑ
				T _A = +25°C	Resonator connection		0.49	0.76	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.37	1.17	μΑ
				T _A = +50°C	Resonator connection		0.56	1.36	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.53	1.97	μΑ
				T _A = +70°C	Resonator connection		0.72	2.16	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		0.82	3.37	μΑ
				T _A = +85°C	Resonator connection		1.01	3.56	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		3.01	15.37	μΑ
				T _A = +105°C	Resonator connection		3.20	15.56	μΑ
	I _{DD3} Note 6	STOP	T _A = -40°C				0.18	0.50	μΑ
	mode ^{Note 8}	mode ^{Note 8}	T _A = +25°C		0.23	0.50	μΑ		
			T _A = +50°C			0.30	1.10	μΑ	
		T _A = +7	T _A = +70°C	+70°C			0.46	1.90	μΑ
			T _A = +85°C		0.75	3.30	μΑ		
			T _A = +105°C				2.94	15.30	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into V_{DD} and EV_{DDO}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD}, EV_{DDO} or Vss, EVsso. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.
 HS (high-speed main) mode: 2.7 V ≤ VDD ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$

- 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1}		HS (high-	fin = 32 MHz Note 3	Basic	V _{DD} = 5.0 V		2.3		mA
Current Note 1		mode	speed main) mode Note 5		operation	V _{DD} = 3.0 V		2.3		mA
			mode		Normal	V _{DD} = 5.0 V		5.2	9.2	mA
					operation	V _{DD} = 3.0 V		5.2	9.2	mA
				f _{IH} = 24 MHz Note 3	Normal	V _{DD} = 5.0 V		4.1	7.0	mA
					operation	V _{DD} = 3.0 V		4.1	7.0	mA
				f _{IH} = 16 MHz Note 3	Normal	V _{DD} = 5.0 V		3.0	5.0	mA
					operation	V _{DD} = 3.0 V		3.0	5.0	mA
			HS (high-	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.4	5.9	mA
			speed main) mode Note 5	V _{DD} = 5.0 V	operation	Resonator connection		3.6	6.0	mA
			mode	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$ $V_{DD} = 3.0 \text{ V}$	Normal operation	Square wave input		3.4	5.9	mA
						Resonator connection		3.6	6.0	mA
			$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		2.1	3.5	mA	
			V _{DD} = 5.0 V		Resonator connection		2.1	3.5	mA	
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		2.1	3.5	mA
			V _{DD} = 3.0 V	operation	Resonator connection		2.1	3.5	mA	
			Subsystem clock operation	fsub = 32.768 kHz Note 4	Normal	Square wave input		4.8	5.9	μΑ
					operation	Resonator connection		4.9	6.0	μΑ
			operation	$T_{A} = -40^{\circ}C$ $f_{SUB} = 32.768 \text{ kHz}$ $Note 4$ $T_{A} = +25^{\circ}C$						\sqcup
					Normal operation	Square wave input		4.9	5.9	μA
						Resonator connection		5.0	6.0	μΑ
				fsub = 32.768 kHz		Square wave input		5.0	7.6	μΑ
				Note 4 TA = +50°C	operation	Resonator connection		5.1	7.7	μA
				fsub = 32.768 kHz	Normal	Square wave input		5.2	9.3	μΑ
				Note 4 TA = +70°C	operation	Resonator connection		5.3	9.4	μΑ
				fsub = 32.768 kHz	Normal	Square wave input		5.7	13.3	μΑ
				Note 4	operation	Resonator connection		5.8	13.4	μA
				T _A = +85°C						-
				fsub = 32.768 kHz Note 4	Normal	Square wave input		10.0	46.0	μΑ
				T _A = +105°C	operation	Resonator connection		10.0	46.0	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVss0, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - **5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation, temperature condition of the TYP. value is T_A = 25°C

(2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (TA = -40 to +105°C, 2.4 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V) (2/2)

Parameter	Symbol			Conditions		MIN.	TYP.	MAX.	Unit
Supply	I _{DD2}	HALT mode	HS (high-	fin = 32 MHz Note 4	V _{DD} = 5.0 V		0.62	3.40	mA
Current Note 1	Note 2		speed main) mode Note 7		V _{DD} = 3.0 V		0.62	3.40	mA
			mode	fin = 24 MHz Note 4	V _{DD} = 5.0 V		0.50	2.70	mA
					V _{DD} = 3.0 V		0.50	2.70	mA
				fin = 16 MHz Note 4	V _{DD} = 5.0 V		0.44	1.90	mA
					V _{DD} = 3.0 V		0.44	1.90	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.31	2.10	mA
			speed main) mode Note 7	V _{DD} = 5.0 V	Resonator connection		0.48	2.20	mA
			mode	f _{MX} = 20 MHz ^{Note 3} ,	Square wave input		0.31	2.10	mA
				V _{DD} = 3.0 V	Resonator connection		0.48	2.20	mA
				f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.21	1.10	mA
				V _{DD} = 5.0 V	Resonator connection		0.28	1.20	mA
			f _{MX} = 10 MHz ^{Note 3} ,	Square wave input		0.21	1.10	mA	
				V _{DD} = 3.0 V	Resonator connection		0.28	1.20	mA
		Subsystem	fsuB = 32.768 kHz ^{Note 5}	Square wave input		0.28	0.61	μA	
			clock operation	T _A = -40°C	Resonator connection		0.47	0.80	μA
			operation	fsuB = 32.768 kHz ^{Note 5}	Square wave input		0.34	0.61	μA
				T _A = +25°C	Resonator connection		0.53	0.80	μA
				fsuB = 32.768 kHz ^{Note 5}	Square wave input		0.41	2.30	μA
				T _A = +50°C	Resonator connection		0.60	2.49	μA
				fsuB = 32.768 kHz ^{Note 5}	Square wave input		0.64	4.03	μA
				T _A = +70°C	Resonator connection		0.83	4.22	μA
				fsuB = 32.768 kHz ^{Note 5}	Square wave input		1.09	8.04	μA
				T _A = +85°C	Resonator connection		1.28	8.23	μΑ
				fsub = 32.768 kHz ^{Note 5}	Square wave input		5.50	41.00	μA
				T _A = +105°C	Resonator connection		5.50	41.00	μΑ
	I _{DD3} Note 6	STOP	T _A = -40°C				0.19	0.52	μA
	mode ^{Note}	mode ^{Note 8}	T _A = +25°C				0.25	0.52	μA
			T _A = +50°C				0.32	2.21	μA
			T _A = +70°C				0.55	3.94	μA
			T _A = +85°C			1.00	7.95	μΑ	
			T _A = +105°C				5.00	40.00	μΑ

(Notes and Remarks are listed on the next page.)

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVsso, and EVss1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 4. When high-speed system clock and subsystem clock are stopped.
 - 5. When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - 7. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode: 2.7 V ≤ V_{DD} ≤ 5.5 V@1 MHz to 32 MHz $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}@1 \text{ MHz to } 16 \text{ MHz}$
 - 8. Regarding the value for current operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 4. Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is TA = 25°C

(3) Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	FIL Note 1				0.20		μА
RTC operating current	RTC Notes 1, 2, 3				0.02		μΑ
12-bit interval timer operating current	I _{IT} Notes 1, 2, 4				0.02		μΑ
Watchdog timer operating current	WDT Notes 1, 2, 5	fı∟ = 15 kHz			0.22		μΑ
A/D converter	IADC	When conversion	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
operating current	Notes 1, 6	at maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	ladref Note 1				75.0		μΑ
Temperature sensor operating current	ITMPS Note 1				75.0		μА
LVD operating current	ILVD Notes 1, 7				0.08		μΑ
Self programming operating current	IFSP Notes 1, 9				2.50	12.20	mA
BGO operating current	BGO Notes 1, 8				2.50	12.20	mA
SNOOZE	Isnoz	ADC operation	The mode is performed Note 10		0.50	1.10	mA
operating current	Note 1		The A/D conversion operations are performed, low-voltage mode, AVREFP = VDD = 3.0 V		1.20	2.04	mA
		CSI/UART operation	1		0.70	1.54	mA

Notes 1. Current flowing to the VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- **5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer operates.
- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.



- Notes 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
 - 8. Current flowing only during data flash rewrite.
 - 9. Current flowing only during self programming.
 - 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25$ °C

3.4 AC Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Items	Symbol		Conditions	1	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main		2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
instruction execution time)		system clock (fmain) operation	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		Subsystem of operation	clock (fsuв)	2.4 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μs
		In the self		2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μs
		programming mode	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
External system clock frequency	fex	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		1.0		20.0	MHz
		2.4 V ≤ V _{DD} < 2.7 V			1.0		16.0	MHz
	fexs		32		35	kHz		
External system clock input high- level width, low-level width	texh, texl	2.7 V ≤ V _{DD} ≤	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$					ns
		2.4 V ≤ V _{DD} <	< 2.7 V		30			ns
	texhs,				13.7			μs
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	f то	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	2.4 V ≤ EV _{DD0} < 2.7 V			4	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth,	INTP0	2.4 V	≤ V _{DD} ≤ 5.5 V	1			μs
low-level width	tintl	INTP1 to INT	TP11 2.4 V	2.4 V ≤ EV _{DD0} ≤ 5.5 V				μs
Key interrupt input low-level width	tkr	KR0 to KR7	2.4 V	≤ EV _{DD0} ≤ 5.5 V	250			ns
RESET low-level width	trsl				10			μs

Note The following conditions are required for low voltage interface when EVDDO < VDD

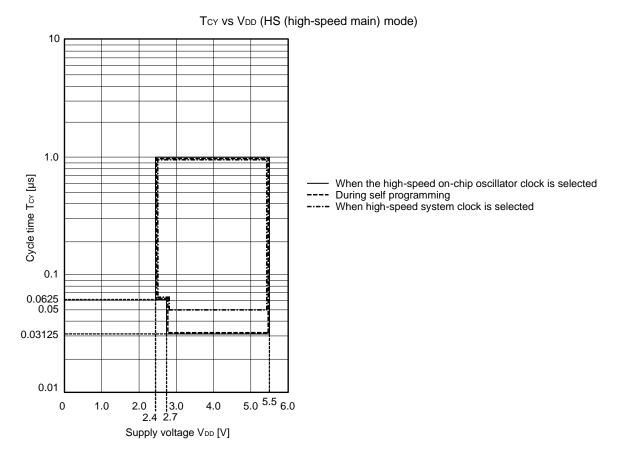
 $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

Remark fmck: Timer array unit operation clock frequency

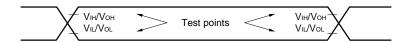
(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

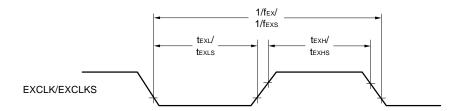
Minimum Instruction Execution Time during Main System Clock Operation



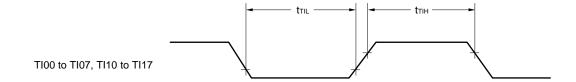
AC Timing Test Points

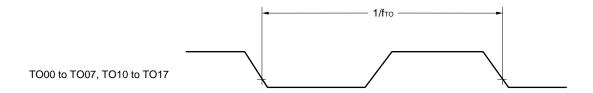


External System Clock Timing

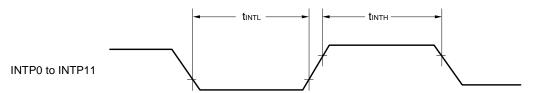


TI/TO Timing

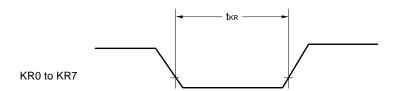




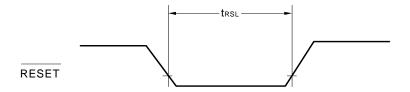
Interrupt Request Input Timing



Key Interrupt Input Timing

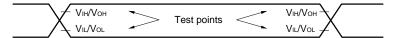


RESET Input Timing



3.5 Peripheral Functions Characteristics

AC Timing Test Points



3.5.1 Serial array unit

(1) During communication at same potential (UART mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

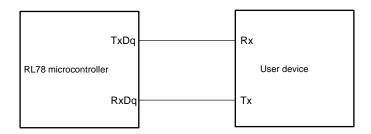
Parameter	Symbol	Conditions	HS (high-spee	Unit	
			MIN.	MAX.	
Transfer rate Note 1				fmck/12 Note 2	bps
		Theoretical value of the maximum transfer rate fclk = 32 MHz, fMCK = fclk		2.6	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The following conditions are required for low voltage interface when EVDDO < VDD.

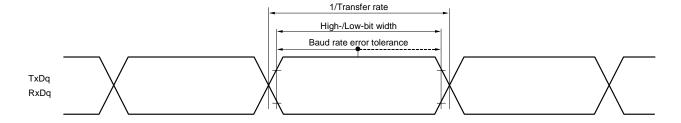
 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$

Caution Select the normal input buffer for the RxDq pin and the normal output mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg).

UART mode connection diagram (during communication at same potential)



UART mode bit width (during communication at same potential) (reference)



Remarks 1. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	2.7 V ≤ EV _{DD0} ≤ 5.5 V	250		ns
			2.4 V ≤ EV _{DD0} ≤ 5.5 V	500		ns
SCKp high-/low-level width	t кн1,	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tkcy1/2 - 24		ns
	t KL1	2.7 V ≤ EV _{DD0} ≤ 5.5 V		tkcy1/2 - 36		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) Note 1	tsık1	4.0 V ≤ EV _{DD0} ≤ 5.5 V		66		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V		66		ns
		2.4 V ≤ EV _{DD0}	2.4 V ≤ EV _{DD0} ≤ 5.5 V			ns
SIp hold time (from SCKp↑) Note 2	tksi1			38		ns
Delay time from SCKp↓ to SOp output Note 3	tkso1	C = 30 pF Note	e 4		50	ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The Slp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(3) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Cond	ditions	HS (high-speed ma	ain) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 5	tkcy2	4.0 V ≤ EV _{DD0} ≤ 5.5 V	20 MHz < fмск	16/fмск		ns
			fмcк ≤ 20 MHz	12/fмск		ns
		2.7 V ≤ EV _{DD0} ≤ 5.5 V	16 MHz < fмск	16/fмск		ns
			fmck ≤ 16 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		16/fмск		ns
				12/fмcк and 1000		ns
SCKp high-/low-level	t кн2,	4.0 V ≤ EV _{DD0} ≤ 5.5 V	,	tксу2/2 - 14		ns
width	t KL2	2.7 V ≤ EV _{DD0} ≤ 5.5 V	,	tkcy2/2 - 16		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V	,	tксү2/2 - 36		ns
SIp setup time	tsık2	2.7 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск+40		ns
(to SCKp↑) Note 1		2.4 V ≤ EV _{DD0} ≤ 5.5 V	′	1/fмск+60		ns
SIp hold time (from SCKp↑) Note 2	tksi2	2.4 V ≤ EV _{DD0} ≤ 5.5 V		1/fмск+62		ns
Delay time from SCKp↓	t KSO2	C = 30 pF Note 4	2.7 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+66	ns
to SOp output Note 3			2.4 V ≤ EV _{DD0} ≤ 5.5 V		2/fмск+113	ns

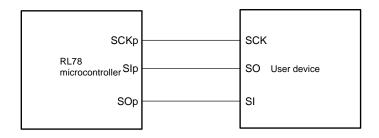
- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

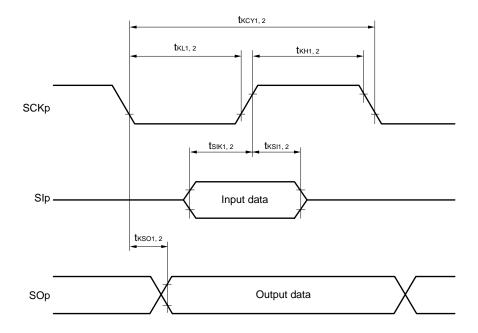
Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)

fmcκ: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,n: Channel number (mn = 00 to 03, 10 to 13))

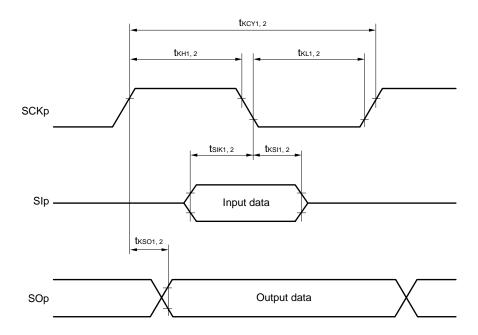
CSI mode connection diagram (during communication at same potential)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (during communication at same potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31)

2. m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

(4) During communication at same potential (simplified I²C mode)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-s _l Mo		Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	2.7 V ≤ EV _{DD0} ≤ 5.5 V,		400 Note1	kHz
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$		100 Note1	kHz
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "L"	tLOW	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	1200		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Hold time when SCLr = "H"	thigh	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$	1200		ns
		$C_b = 50$ pF, $R_b = 2.7$ k Ω			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	4600		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			
Data setup time (reception)	tsu:dat	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	1/fмск + 220		ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$	Note2		
		$2.4 \text{ V} \leq \text{EV}_{DD} \leq 5.5 \text{ V},$	1/fмск + 580		ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$	Note2		
Data hold time (transmission)	thd:dat	2.7 V ≤ EV _{DD0} ≤ 5.5 V,	0	770	ns
		$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$	0	1420	ns
		$C_b = 100 \text{ pF}, R_b = 3 \text{ k}\Omega$			

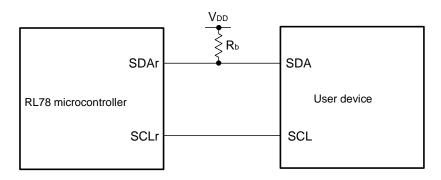
Notes 1. The value must also be equal to or less than fmck/4.

2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

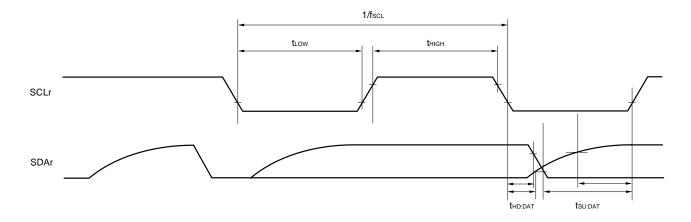
Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EV_{DD} tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(Remarks are listed on the next page.)

Simplified I²C mode mode connection diagram (during communication at same potential)



Simplified I²C mode serial transfer timing (during communication at same potential)



Remarks 1. R_b[Ω]:Communication line (SDAr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions HS (high-speed main) Mod		ed main) Mode	Unit	
					MIN.	MAX.	
Transfer rate		Reception	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			fmck/12 Note 1	bps
			2.7 V ≤ V _b ≤ 4.0 V	Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps
			2.7 V ≤ EV _{DD0} < 4.0 V,			fмск/12 Note 1	bps
			2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps
			$2.4 \text{ V} \le \text{EV}_{\text{DDO}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$			fMCK/12 Notes 1,2	bps
				Theoretical value of the maximum transfer rate fclk = 32 MHz, fMck = fclk		2.6	Mbps

- Notes 1. Transfer rate in the SNOOZE mode is 4800 bps only.
 - 2. The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$.

 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 2.7 \text{ V} : \text{MAX. } 1.3 \text{ Mbps}$

Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20-to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)
- **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol		Conditi	ions	HS (high-spe	ed main) Mode	Unit
					MIN.	MAX.	
Transfer rate		Transmission	4.0 V ≤ EV _{DD0} ≤ 5.5 V,			Note 1	bps
			$2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	Theoretical value of the maximum transfer rate		2.6 Note 2	Mbps
				$C_b = 50 \text{ pF}, R_b = 1.4 \text{ k}\Omega, V_b = 2.7 \text{ V}$			
			2.7 V ≤ EV _{DD0} < 4.0 V,			Note 3	bps
			2.3 V ≤ V _b ≤ 2.7 V	Theoretical value of the maximum transfer rate		1.2 Note 4	Mbps
				$C_b = 50 \text{ pF}, R_b = 2.7 \text{ k}\Omega, V_b = 2.3 \text{ V}$			
			2.4 V ≤ EV _{DD0} < 3.3 V,			Note 5	bps
			1.6 V ≤ V _b ≤ 2.0 V	Theoretical value of the maximum transfer rate		0.43 Note 6	Mbps
				$C_b = 50 \text{ pF}, R_b = 5.5 \text{ k}\Omega, V_b = 1.6 \text{ V}$			

Notes 1. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 4.0 V \leq EV_{DD0} \leq 5.5 V and 2.7 V \leq V_b \leq 4.0 V

$$\label{eq:maximum transfer rate} \begin{aligned} & \frac{1}{\{-C_b \times R_b \times ln\ (1\ -\frac{2.2}{V_b})\} \times 3} \ [bps] \end{aligned}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.2}{V_b})\}}{\frac{1}{(\text{Transfer rate})} \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **2.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 1 above to calculate the maximum transfer rate under conditions of the customer.
- 3. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.7 V ≤ EVDD0 < 4.0 V and 2.4 V ≤ Vb ≤ 2.7 V

Maximum transfer rate =
$$\frac{1}{\{-C_b \times R_b \times ln (1 - \frac{2.0}{V_b})\} \times 3}$$
 [bps]

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln (1 - \frac{2.0}{V_b})\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **4.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 3 above to calculate the maximum transfer rate under conditions of the customer.

Notes 5. The smaller maximum transfer rate derived by using fmck/12 or the following expression is the valid maximum transfer rate.

Expression for calculating the transfer rate when 2.4 V ≤ EV_{DD0} < 3.3 V and 1.6 V ≤ V_b ≤ 2.0 V

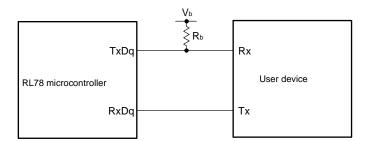
$$\text{Maximum transfer rate} = \frac{1}{\{-C_b \times R_b \times \text{ln } (1 - \frac{1.5}{V_b})\} \times 3} \text{[bps]}$$

Baud rate error (theoretical value) =
$$\frac{\frac{1}{\text{Transfer rate} \times 2} - \{-C_b \times R_b \times \ln{(1 - \frac{1.5}{V_b})}\}}{(\frac{1}{\text{Transfer rate}}) \times \text{Number of transferred bits}} \times 100 \, [\%]$$

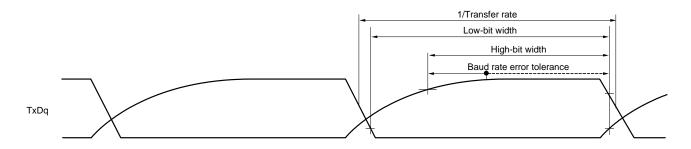
- * This value is the theoretical value of the relative difference between the transmission and reception sides.
- **6.** This value as an example is calculated when the conditions described in the "Conditions" column are met. Refer to Note 5 above to calculate the maximum transfer rate under conditions of the customer.

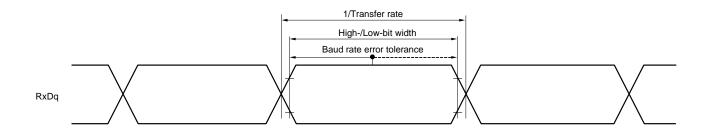
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VL, see the DC characteristics with TTL input buffer selected.

UART mode connection diagram (during communication at different potential)



UART mode bit width (during communication at different potential) (reference)





- **Remarks 1.** $R_b[\Omega]$:Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - 4. UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-speed	d main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time	tkcY1	tkcy1 ≥ 4/fclk	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	600		ns
			$C_b = 30$ pF, $R_b = 1.4$ k Ω			
			$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	1000		ns
			$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
			$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	2300		ns
			$C_b = 30$ pF, $R_b = 5.5$ k Ω			
SCKp high-level width	t кн1	4.0 V ≤ EVDD	$0 \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$	tксү1/2 - 150		ns
		C _b = 30 pF, R	$R_b = 1.4 \text{ k}\Omega$			
		2.7 V ≤ EV _{DD}	$_{0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	tксү1/2 - 340		ns
		C _b = 30 pF, R	$R_b = 2.7 \text{ k}\Omega$			
		2.4 V ≤ EVDD	$0 < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$	tkcy1/2 - 916		ns
		C _b = 30 pF, R	$R_b = 5.5 \text{ k}\Omega$			
SCKp low-level width	t _{KL1}	4.0 V ≤ EV _{DD}	$0 \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	tксү1/2 - 24		ns
		C _b = 30 pF, R	$R_b = 1.4 \text{ k}\Omega$			
		2.7 V ≤ EV _{DD0} < 4.0 V, 2.3 V ≤ V _b ≤ 2.7 V,		tксү1/2 - 36		ns
		C _b = 30 pF, R	$C_b = 30 \text{ pF}, \text{ R}_b = 2.7 \text{ k}\Omega$			
		2.4 V ≤ EV _{DD0}	o < 3.3 V, 1.6 V ≤ V _b ≤ 2.0 V,	tксү1/2 - 100		ns
		C _b = 30 pF, R	$R_b = 5.5 \text{ k}\Omega$			

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (2/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-spe	ed main) Mode	Unit
			MIN.	MAX.	
Slp setup time	tsik1	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$	162		ns
(to SCKp↑) Note		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	354		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	958		ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			
SIp hold time	tksi1	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$	38		ns
(from SCKp↑) Note		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$	38		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	38		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$		200	ns
SOp output Note		$C_b = 30 \text{ pF}, R_b = 1.4 \text{ k}\Omega$			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		390	ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$		966	ns
		$C_b = 30 \text{ pF}, R_b = 5.5 \text{ k}\Omega$			

Note When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed on the page after the next page.)

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (3/3)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

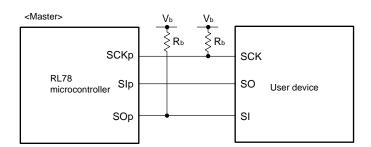
Parameter	Symbol	Conditions	HS (high-spe	ed main) Mode	Unit
			MIN.	MAX.	
SIp setup time	tsik1	$4.0 \text{ V} \le \text{EV}_{DD} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$	88		ns
(to SCKp↓) Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	88		ns
		$C_b = 30 \text{ pF}, R_b = 2.7 \text{ k}\Omega$			
		$2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$	220		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			
SIp hold time	tksi1	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$	38		ns
(from SCKp↓) Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V},$	38		ns
		$C_b = 30$ pF, $R_b = 2.7$ k Ω			
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$	38		ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_{b} \le 4.0 \text{ V},$		50	ns
SOp output Note		$C_b = 30$ pF, $R_b = 1.4$ k Ω			
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$		50	ns
		$C_b = 30$ pF, $R_b = 2.7$ k Ω			
		$2.4 \text{ V} \le \text{EV}_{DD0} < 3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_{b} \le 2.0 \text{ V},$		50	ns
		$C_b = 30$ pF, $R_b = 5.5$ k Ω			

Note When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

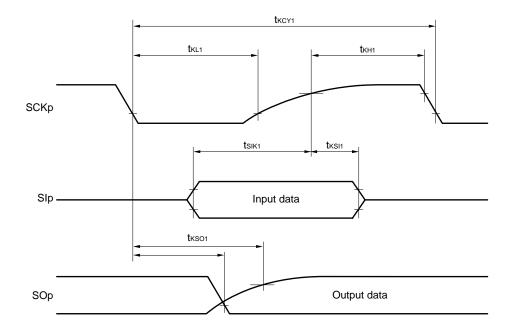
(Remarks are listed on the next page.)

CSI mode connection diagram (during communication at different potential)

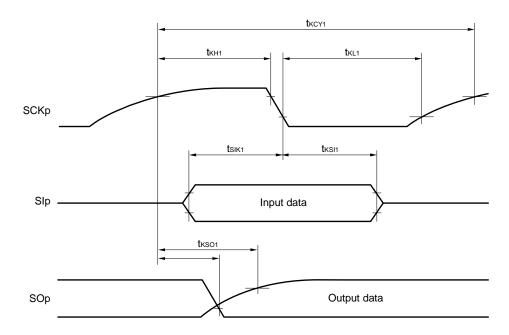


- **Remarks 1.** R_b[Ω]:Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential)
(When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input) $(T_A = -40 \text{ to } +105^{\circ}\text{C}. 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

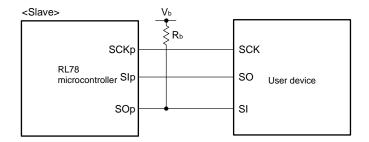
Parameter	Symbol		Conditions	HS (high-spe	ed main) Mode	Unit
				MIN.	MAX.	
SCKp cycle time Note 1	tkcy2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$	24 MHz < fmck	28/fмск		ns
		$2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	20 MHz < fмcк ≤ 24 MHz	24/fмск		ns
			8 MHz < fмск ≤ 20 MHz	20/fмск		ns
			4 MHz < fMCK ≤ 8 MHz	16/fмск		ns
			f _{MCK} ≤ 4 MHz	12/fмск		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$	24 MHz < fmck	40/fмск		ns
		$2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V}$	20 MHz < fмcк ≤ 24 MHz	32/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	28/fмск		ns
			8 MHz < fмcк ≤ 16 MHz	24/fмск		ns
			4 MHz < fMCK ≤ 8 MHz	16/ f мск		ns
			fmck ≤ 4 MHz	12/fмск		ns
		2.4 V ≤ EV _{DD0} < 3.3 V,	24 MHz < fmck	96/fмск		ns
		1.6 V ≤ V _b ≤ 2.0 V	20 MHz < fмcк ≤ 24 MHz	72/fмск		ns
			16 MHz < fмcк ≤ 20 MHz	64/f мск		ns
			8 MHz < fмcк ≤ 16 MHz	52/f мск		ns
			4 MHz < fmck ≤ 8 MHz	32/fмск		ns
			fмck ≤ 4 MHz	20/fмск		ns
SCKp high-/low-level width	tкн2, tкL2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V}$	V,	tkcy2/2 - 24		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	V,	txcy2/2 - 36		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{N}}$		tkcy2/2 - 100		ns
SIp setup time (to SCKp↑) Note2	tsıк2	4.0 V ≤ EV _{DD0} ≤ 5.5 2.7 V ≤ V _b ≤ 4.0 V	V,	1/fмск + 40		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V}$	V,	1/fмск + 40		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}$	V,	1/fмск + 60		ns
SIp hold time (from SCKp↑) Note 3	tksi2			1/fmck + 62		ns
Delay time from SCKp↓ to SOp output Note 4	tkso2	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5$ $C_b = 30 \text{ pF}, R_b = 1.4$	$V, 2.7 V \le V_b \le 4.0 V,$ 4 kΩ		2/fмск + 240	ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0$ $C_b = 30 \text{ pF}, R_b = 2.7$	V, 2.3 V ≤ V _b ≤ 2.7 V, 7 kΩ		2/fмск + 428	ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3$ $C_b = 30 \text{ pF}, R_b = 5.9$	V, 1.6 V ≤ V _b ≤ 2.0 V 5 kΩ		2/fмск + 1146	ns

(Notes, Caution and Remarks are listed on the next page.)

- Notes 1. Transfer rate in the SNOOZE mode: MAX. 1 Mbps
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **3.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

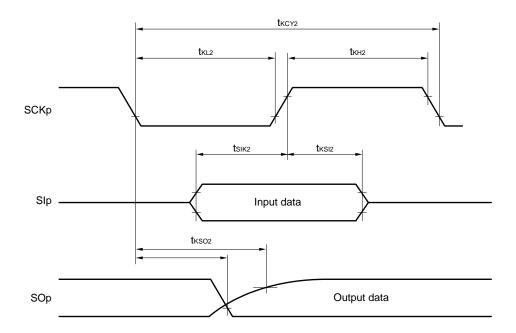
Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 128-pin products)) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

CSI mode connection diagram (during communication at different potential)

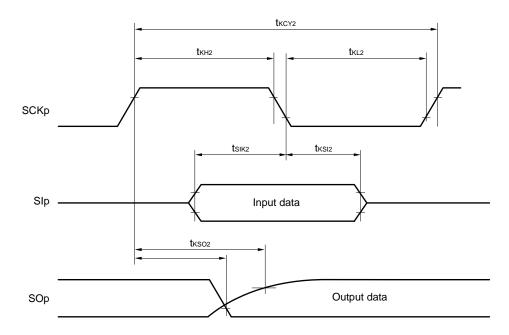


- Remarks 1. $R_b[\Omega]$:Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage
 - **2.** p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 00, 01, 02, 10, 12, 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13))
 - **4.** CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12. 13), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (1/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		speed main) ode	Unit
			MIN.	MAX.	
SCLr clock frequency	fscL	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $		400 Note 1	kHz
		$ 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega $		400 Note 1	kHz
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$		100 Note 1	kHz
		$2.7 \text{ V} \le \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$		100 Note 1	kHz
		$2.4 \text{ V} \leq \text{EV}_{\text{DDO}} < 3.3 \text{ V}, \\ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 5.5 \text{ k}\Omega$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$ \begin{aligned} 4.0 \ V &\leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V &\leq V_b \leq 4.0 \ V, \\ C_b &= 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1200		ns
		$ \begin{aligned} 2.7 & \ V \le EV_{DD0} < 4.0 \ V, \\ 2.3 & \ V \le V_b \le 2.7 \ V, \\ C_b = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned} $	1200		ns
		$ \begin{aligned} &4.0 \; \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \; \text{V}, \\ &2.7 \; \text{V} \leq \text{V}_{\text{b}} \leq 4.0 \; \text{V}, \\ &C_{\text{b}} = 100 \; \text{pF}, \; R_{\text{b}} = 2.8 \; \text{k}\Omega \end{aligned} $	4600		ns
		$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V},$ $2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega$	4600		ns
		$2.4 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 5.5 \text{ k}\Omega$	4650		ns
Hold time when SCLr = "H"	tнісн	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	620		ns
		$2.7 \text{ V} \le \text{EV}_{\text{DDO}} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{\text{b}} \le 2.7 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	500		ns
		$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_{\text{b}} \le 4.0 \text{ V},$ $C_{\text{b}} = 100 \text{ pF}, R_{\text{b}} = 2.8 \text{ k}\Omega$	2700		ns
		2.7 V \leq EV _{DD0} $<$ 4.0 V, 2.3 V \leq V _b \leq 2.7 V, C _b = 100 pF, R _b = 2.7 k Ω	2400		ns
		2.4 V \leq EV _{DDO} $<$ 3.3 V, 1.6 V \leq V _b \leq 2.0 V, C _b = 100 pF, R _b = 5.5 k Ω	1830		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

(8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I²C mode) (2/2)

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-sp Mo		Unit
			MIN.	MAX.	
Data setup time (reception)	tsu:dat	$\begin{aligned} 4.0 & \ V \le EV_{DD0} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 50 \ pF, \ R_b = 2.7 \ k\Omega \end{aligned}$	1/fmck + 340 Note 2		ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	1/fмск + 340 Note 2		ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	1/f _{MCK} + 760 Note 2		ns
			1/fmck + 760 Note 2		ns
			1/fмск + 570 Note 2		ns
Data hold time (transmission)	thd:dat	$4.0 \text{ V} \leq \text{EV}_{\text{DDO}} \leq 5.5 \text{ V},$ $2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V},$ $C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega$	0	770	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ C_{\text{b}} = 50 \text{ pF}, R_{\text{b}} = 2.7 \text{ k}\Omega $	0	770	ns
		$ \begin{aligned} &4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ &2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, \\ &C_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.8 \text{ k}\Omega \end{aligned} $	0	1420	ns
		$ 2.7 \text{ V} \leq \text{EV}_{\text{DD0}} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{\text{b}} \leq 2.7 \text{ V}, \\ \text{C}_{\text{b}} = 100 \text{ pF}, \text{ R}_{\text{b}} = 2.7 \text{ k}\Omega $	0	1420	ns
			0	1215	ns

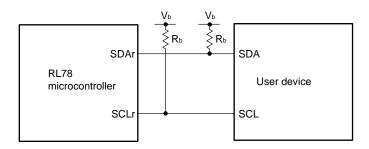
Notes 1. The value must also be equal to or less than fmck/4.

Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

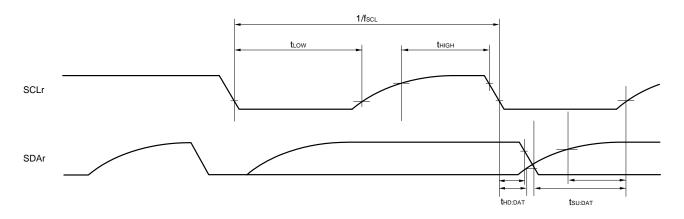
(Remarks are listed on the next page.)

^{2.} Set the fmck value to keep the hold time of SCLr = "L" and SCLr = "H".

Simplified I²C mode connection diagram (during communication at different potential)



Simplified I²C mode serial transfer timing (during communication at different potential)



Caution Select the TTL input buffer and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the N-ch open drain output (VDD tolerance (for the 20- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VH and VIL, see the DC characteristics with TTL input buffer selected.

- Remarks 1. R_b[Ω]:Communication line (SDAr, SCLr) pull-up resistance, C_b[F]: Communication line (SDAr, SCLr) load capacitance, V_b[V]: Communication line voltage
 - 2. r: IIC number (r = 00, 01, 10, 20, 30, 31), g: PIM, POM number (g = 0, 1, 4, 5, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 01, 02, 10, 12, 13)

3.5.2 Serial interface IICA

$(T_A = -40 \text{ to } +105^{\circ})$	$C, 2.4 V \leq EV_{DD0} = EV_{DD1}$	≤ V _{DD} ≤ 5.5 V. Vss	$= EVss_0 = EVss_1 = 0 V)$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Mode	Unit	
			Standa	rd Mode	Fast	Mode	
			MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Fast mode: fclk ≥ 3.5 MHz	_	_	0	400	kHz
		Standard mode: fclk ≥ 1 MHz	0	100	ı	_	kHz
Setup time of restart condition	tsu:sta		4.7		0.6		μs
Hold time ^{Note 1}	thd:STA		4.0		0.6		μs
Hold time when SCLA0 = "L"	tLOW		4.7		1.3		μs
Hold time when SCLA0 = "H"	tніgн		4.0		0.6		μs
Data setup time (reception)	tsu:dat		250		100		ns
Data hold time (transmission)Note 2	thd:dat		0	3.45	0	0.9	μs
Setup time of stop condition	tsu:sto		4.0		0.6		μs
Bus-free time	t BUF		4.7		1.3		μs

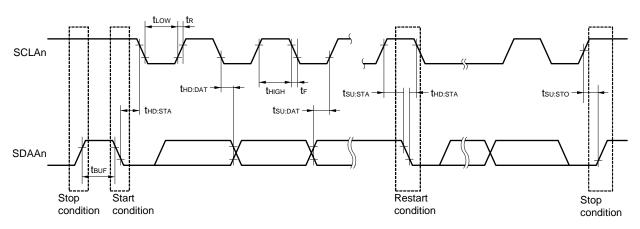
- Notes 1. The first clock pulse is generated after this period when the start/restart condition is detected.
 - 2. The maximum value (MAX.) of thd:DAT is during normal transfer and a wait state is inserted in the ACK (acknowledge) timing.

Caution The values in the above table are applied even when bit 2 (PIOR2) in the peripheral I/O redirection register (PIOR) is 1. At this time, the pin characteristics (IOH1, IOL1, VOH1, VOL1) must satisfy the values in the redirect destination.

Remark The maximum value of Cb (communication line capacitance) and the value of Rb (communication line pull-up resistor) at that time in each mode are as follows.

Standard mode: $C_b = 400 \text{ pF}, R_b = 2.7 \text{ k}\Omega$ Fast mode: $C_b = 320 \text{ pF}, R_b = 1.1 \text{ k}\Omega$

IICA serial transfer timing



Remark n = 0, 1

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage							
Input channel	Reference voltage (+) = AVREFP Reference voltage (-) = AVREFM	Reference voltage (+) = VDD Reference voltage (-) = Vss	Reference voltage (+) = VBGR Reference voltage (-) = AVREFM						
input channel	Reference voltage (-) = AVREEM	Reference voltage (-) = vss	Reference voltage (-) = AVREFM						
ANI0 to ANI14	Refer to 3.6.1 (1) .	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .						
ANI16 to ANI26	Refer to 3.6.1 (2) .								
Internal reference voltage	Refer to 3.6.1 (1) .		_						
Temperature sensor output									
voltage									

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{AV}_{REFP} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{V}_{SS} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Conditio	ns	MIN.	TYP.	MAX.	Unit	
Resolution	RES			8		10	bit	
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±3.5	LSB	
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs	
		Target pin: ANI2 to ANI14	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs	
			2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs	
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs	
		Target pin: Internal reference	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs	
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs	
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR	
Full-scale error ^{Notes 1, 2}	EFS	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.25	%FSR	
Integral linearity error	ILE	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.5	LSB	
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±1.5	LSB	
Analog input voltage	Vain	ANI2 to ANI14		0		AVREFP	V	
		Internal reference voltage output (2.4 V ≤ VDD ≤ 5.5 V, HS (high-speed main) mode)			V _{BGR} Note 4			
		Temperature sensor output vol· (2.4 V ≤ VDD ≤ 5.5 V, HS (high-	· ·		V			

(Notes are listed on the next page.)

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When AV_{REFP} < V_{DD}, the MAX. values are as follows.

 Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

 Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.
 - Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.
 - 4. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, 2.4 \text{ V} \leq \text{AV}_{REFP} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{REFP}, \text{Reference voltage (-)} = \text{AV}_{REFM} = 0 \text{ V})$

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution EV _{DD0} ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.125		39	μs
		Target pin : ANI16 to ANI26	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
			2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±3.5	LSB
Differential linearity error	DLE	10-bit resolution EVDD0 ≤ AV _{REFP} = V _{DD} Notes 3, 4	2.4 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI26		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD} .

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

(3) When reference voltage (+) = V_{DD} (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = V_{SS} (ADREFM = 0), target pin : ANI0 to ANI14, ANI16 to ANI26, internal reference voltage, and temperature sensor output voltage

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{EV}_{DD0} = \text{EV}_{DD1} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{V}_{SS} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}, \text{Reference voltage (+)} = \text{V}_{DD}, \text{Reference voltage (-)} = \text{V}_{SS})$

Parameter	Symbol	Condition	s	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	3.6 V ≤ V _{DD} ≤ 5.5 V	2.125		39	μs
		Target pin: ANIO to ANI14,	2.7 V ≤ VDD ≤ 5.5 V	3.1875		39	μs
		ANI16 to ANI26	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
		10-bit resolution	3.6 V ≤ VDD ≤ 5.5 V	2.375		39	μs
		Target pin: Internal reference	2.7 V ≤ VDD ≤ 5.5 V	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	2.4 V ≤ VDD ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Full-scale errorNotes 1, 2	Ers	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	10-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±4.0	LSB
Differential linearity error	DLE	10-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Analog input voltage	Vain	ANI0 to ANI14	•	0		V _{DD}	V
		ANI16 to ANI26		0		EV _{DD0}	V
		Internal reference voltage outpu (2.4 V ≤ V _{DD} ≤ 5.5 V, HS (high-s		V			
		Temperature sensor output volt (2.4 V ≤ VDD ≤ 5.5 V, HS (high-s	,	V _{TMPS25} Note	3	V	

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.

(4) When reference voltage (+) = Internal reference voltage (ADREFP1 = 1, ADREFP0 = 0), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI0, ANI2 to ANI14, ANI16 to ANI26

(T_A = -40 to +105°C, 2.4 V ≤ EV_{DD0} = EV_{DD1} ≤ V_{DD} ≤ 5.5 V, V_{SS} = EV_{SS0} = EV_{SS1} = 0 V, Reference voltage (+) = V_{BGR} Note 3, Reference voltage (-) = AVREFM Note 4 = 0 V, HS (high-speed main) mode)

Parameter	Symbol	Cond	MIN.	TYP.	MAX.	Unit	
Resolution	RES				8		bit
Conversion time	tconv	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	8-bit resolution	2.4 V ≤ V _{DD} ≤ 5.5 V			±0.60	%FSR
Integral linearity errorNote 1	ILE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±2.0	LSB
Differential linearity error Note 1	DLE	8-bit resolution	2.4 V ≤ VDD ≤ 5.5 V			±1.0	LSB
Analog input voltage	Vain			0		V _{BGR} Note 3	V

- Notes 1. Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. Refer to 3.6.2 Temperature sensor/internal reference voltage characteristics.
 - **4.** When reference voltage (-) = Vss, the MAX. values are as follows. Zero-scale error: Add ±0.35%FSR to the MAX. value when reference voltage (-) = AVREFM. Integral linearity error: Add ±0.5 LSB to the MAX. value when reference voltage (-) = AVREFM. Differential linearity error: Add ±0.2 LSB to the MAX. value when reference voltage (-) = AVREFM.

3.6.2 Temperature sensor/internal reference voltage characteristics

(TA = -40 to +105°C, 2.4 V \leq VDD \leq 5.5 V, Vss = 0 V, HS (high-speed main) mode)

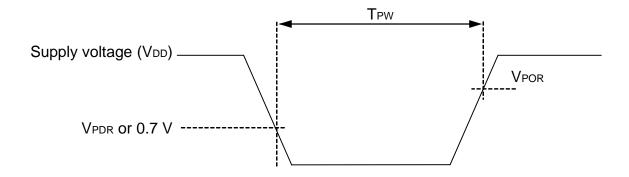
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Temperature sensor output voltage	V _{TMPS25}	Setting ADS register = 80H, TA = +25°C		1.05		V
Internal reference voltage	V _{BGR}	Setting ADS register = 81H	1.38	1.45	1.5	V
Temperature coefficient	FVTMPS	Temperature sensor that depends on the temperature		-3.6		mV/°C
Operation stabilization wait time	tamp		5			μs

3.6.3 POR circuit characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection voltage	Vpor	The power supply voltage is rising.	1.45	1.51	1.57	V
	V _{PDR}	The power supply voltage is falling.	1.44	1.50	1.56	V
Minimum pulse width Note	T _{PW}		300			μs

Note Minimum time required for a POR reset when V_{DD} exceeds below V_{PDR}. This is also the minimum time required for a POR reset from when V_{DD} exceeds below 0.7 V to when V_{DD} exceeds V_{POR} while STOP mode is entered or the main system clock is stopped through setting bit 0 (HIOSTOP) and bit 7 (MSTOP) in the clock operation status control register (CSC).



3.6.4 LVD circuit characteristics

LVD Detection Voltage of Reset Mode and Interrupt Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

	Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Detection	Supply voltage level	V _L VD0	The power supply voltage is rising.	3.90	4.06	4.22	V
voltage			The power supply voltage is falling.	3.83	3.98	4.13	V
		V _{LVD1}	The power supply voltage is rising.	3.60	3.75	3.90	V
			The power supply voltage is falling.	3.53	3.67	3.81	V
		V _{LVD2}	The power supply voltage is rising.	3.01	3.13	3.25	V
			The power supply voltage is falling.	2.94	3.06	3.18	V
		V _L VD3	The power supply voltage is rising.	2.90	3.02	3.14	V
			The power supply voltage is falling.	2.85	2.96	3.07	V
		V _{LVD4}	The power supply voltage is rising.	2.81	2.92	3.03	V
			The power supply voltage is falling.	2.75	2.86	2.97	V
		V _{LVD5}	The power supply voltage is rising.	2.70	2.81	2.92	V
			The power supply voltage is falling.	2.64	2.75	2.86	V
		V _L VD6	The power supply voltage is rising.	2.61	2.71	2.81	V
			The power supply voltage is falling.	2.55	2.65	2.75	V
		V _{LVD7}	The power supply voltage is rising.	2.51	2.61	2.71	V
			The power supply voltage is falling.	2.45	2.55	2.65	V
Minimum pu	lse width	tLW		300			μs
Detection de	elay time					300	μs

LVD Detection Voltage of Interrupt & Reset Mode

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, V_{PDR} \le V_{DD} \le 5.5 \text{ V}, V_{SS} = 0 \text{ V})$

Parameter	Symbol		Cond	ditions	MIN.	TYP.	MAX.	Unit
Interrupt and reset	V _{LVDD0}	V _{POC2} ,	VPOC1, VPOC0 = 0, 1, 1,	2.64	2.75	2.86	V	
mode	V _L VDD1		LVIS1, LVIS0 = 1, 0	Rising release reset voltage	2.81	2.92	3.03	٧
				Falling interrupt voltage	2.75	2.86	2.97	V
	V _{LVDD2}		LVIS1, LVIS0 = 0, 1	Rising release reset voltage	2.90	3.02	3.14	V
				Falling interrupt voltage	2.85	2.96	3.07	V
	VLVDD3		LVIS1, LVIS0 = 0, 0	Rising release reset voltage	3.90	4.06	4.22	V
				Falling interrupt voltage	3.83	3.98	4.13	V

3.6.5 Power supply voltage rising slope characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Power supply voltage rising slope	SVDD				54	V/ms

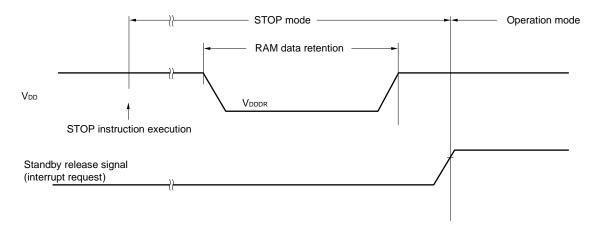
Caution Make sure to keep the internal reset state by the LVD circuit or an external reset until V_{DD} reaches the operating voltage range shown in 3.4 AC Characteristics.

3.7 RAM Data Retention Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention supply voltage	VDDDR		1.44 ^{Note}		5.5	V

Note This depends on the POR detection voltage. For a falling voltage, data in RAM are retained until the voltage reaches the level that triggers a POR reset but not once it reaches the level at which a POR reset is generated.



3.8 Flash Memory Programming Characteristics

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
CPU/peripheral hardware clock	fclk	2.4 V ≤ VDD ≤ 5.5 V	1		32	MHz
frequency						
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C Note 4	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 years TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C Note 4	100,000			
		Retained for 20 years TA = 85°C Note 4	10,000			

- **Notes 1.** 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.
 - 2. When using flash memory programmer and Renesas Electronics self programming library.
 - 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.
 - **4.** This temperature is the average value at which data are retained.

3.9 Dedicated Flash Memory Programmer Communication (UART)

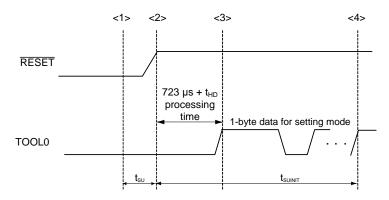
$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps

3.10 Timing of Entry to Flash Memory Programming Modes

$(T_A = -40 \text{ to } +105^{\circ}\text{C}. 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}. \text{ Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuinit	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μs
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tнo	POR and LVD reset must be released before the external reset is released.	1			ms



- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

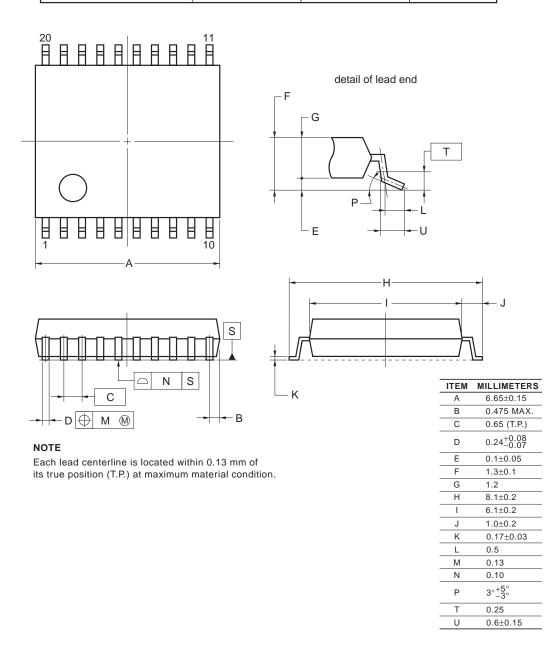
tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

4. PACKAGE DRAWINGS

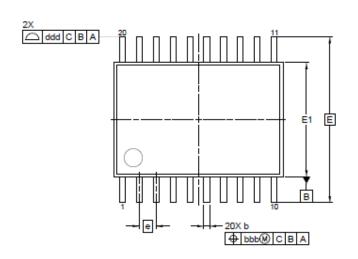
4.1 20-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP20-0300-0.65	PLSP0020JC-A	S20MC-65-5A4-3	0.12

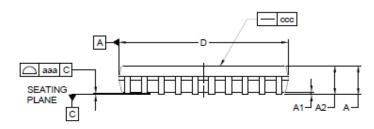


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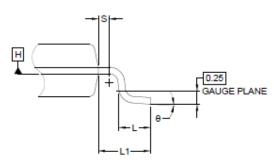
JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-TSSOP20-4.40x6.50-0.65	PTSP0020JI-A	0.08







Detail of Lead End



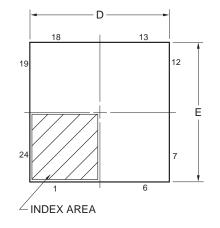
8.14	-	_	•	
NIC		-	-	т

- 1.DIMENSION 'D' AND 'E1' DOES NOT INCLUDE MOLD FLASH.
- 2.DIMENSION 'b' DOES NOT INCLUDE TRIM OFFSET.
- 3.DIMENSION 'D' AND 'E1' TO BE DETERMINED AT DATUM PLANE H.

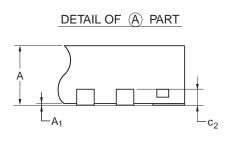
Reference Symbol	Dimension in Millimeters			
	Min.	Nom.	Max.	
Α	-	-	1.20	
A1	0.05	-	0.15	
A2	0.80	1.00	1.05	
b	0.19	-	0.30	
С	0.09	0.127	0.20	
D	6.40	6.50	6.60	
E1	4.30	4.40	4.50	
E	6.40 BSC			
e	0.65 BSC			
L1		1.00 REF		
L	0.50	0.60	0.75	
S	0.20	-	-	
θ	0°	ı	8°	
aaa	0.10			
bbb	0.10			
ccc	0.05			
ddd	0.20			

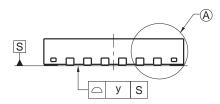
4.2 24-pin Package

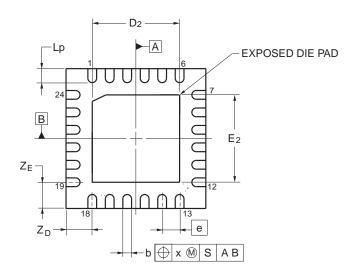
JEITA Pad	ckage code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFI	N24-4x4-0.50	PWQN0024KE-A	P24K8-50-CAB-3	0.04





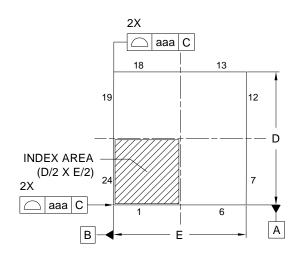


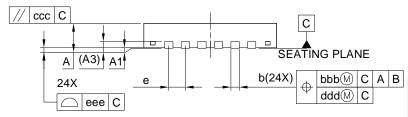


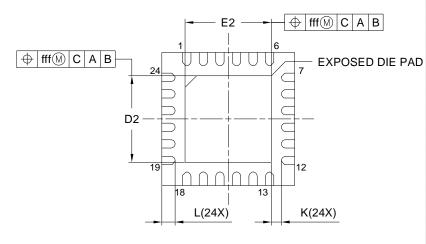


Referance	Dimension in Millimeters			
Symbol	Min	Nom	Max	
D	3.95	4.00	4.05	
E	3.95	4.00	4.05	
А			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у			0.05	
Z _D		0.75		
Z _E		0.75		
C ₂	0.15	0.20	0.25	
D ₂		2.50		
E ₂		2.50		

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN024-4x4-0.50	PWQN0024KF-A	0.04







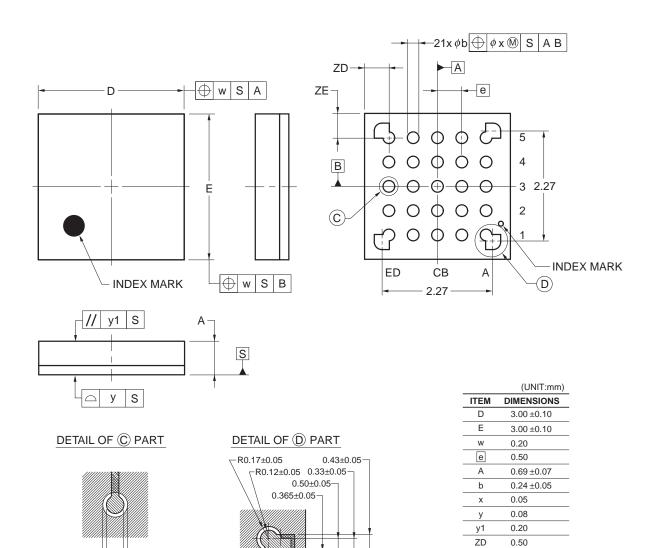
Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А	_	_	0.80
A1	0.00	0.02	0.05
А3		0.203 REF	
b	0.18	0.25	0.30
D		4.00 BSC	
E	4.00 BSC		
е	0.50 BSC		
L	0.35	0.40	0.45
К	0.20	_	_
D2	2.55	2.60	2.65
E2	2.55	2.60	2.65
aaa		0.15	
bbb	0.10		
ccc	0.10		
ddd		0.05	
eee	0.08		
fff	0.10		

4.3 25-pin Package

 ϕ b - (LAND PAD)

φ0.34±0.05 (APERTURE OF SOLDER RESIST)

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01





ZE

0.50

0.365±0.05

0.50±0.05 0.33±0.05

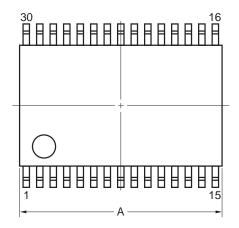
0.43±0.05

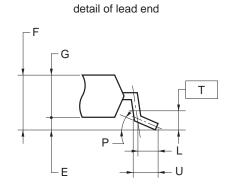
R0.165±0.05

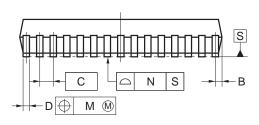
R0.215±0.05

4.4 30-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LSSOP30-0300-0.65	PLSP0030JB-B	S30MC-65-5A4-3	0.18

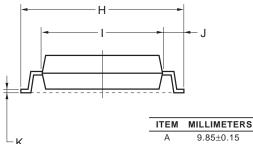






NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

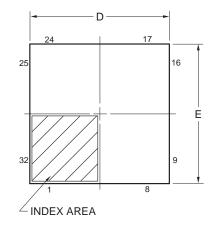


ITEM	MILLIMETERS
Α	9.85±0.15
В	0.45 MAX.
С	0.65 (T.P.)
D	$0.24_{-0.07}^{+0.08}$
Е	0.1±0.05
F	1.3±0.1
G	1.2
Н	8.1±0.2
I	6.1±0.2
J	1.0±0.2
K	0.17±0.03
L	0.5
M	0.13
N	0.10
Р	3°+5°
Т	0.25
U	0.6±0.15

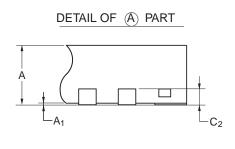
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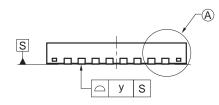
4.5 32-pin Package

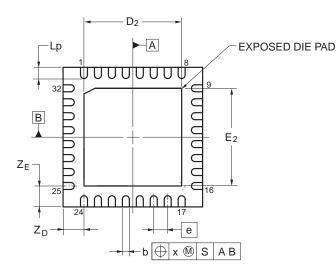
JEITA Package code	RENESAS code	Previous code	MASS (TYP.)[g]
P-HWQFN32-5x5-0.50	PWQN0032KB-A	P32K8-50-3B4-5	0.06







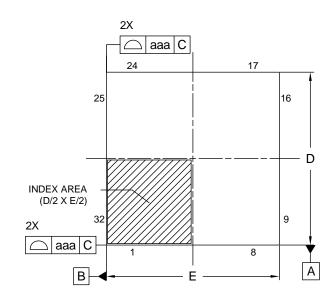


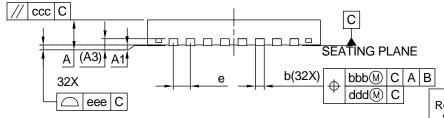


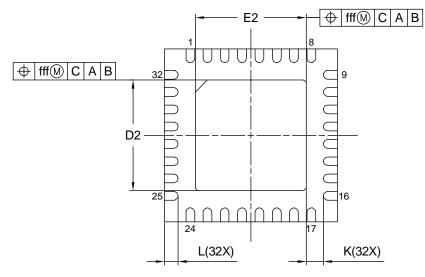
Referance	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	4.95	5.00	5.05
Е	4.95	5.00	5.05
А			0.80
A ₁	0.00		
b	0.18	0.25	0.30
е		0.50	
Lp	0.30	0.40	0.50
х			0.05
у	_		0.05
Z _D		0.75	
Z _E		0.75	
C ₂	0.15	0.20	0.25
D ₂		3.50	
E ₂	_	3.50	_

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN032-5x5-0.50	PWQN0032KE-A	0.06



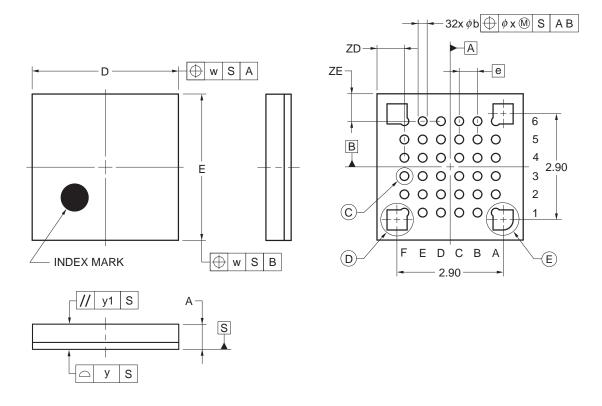


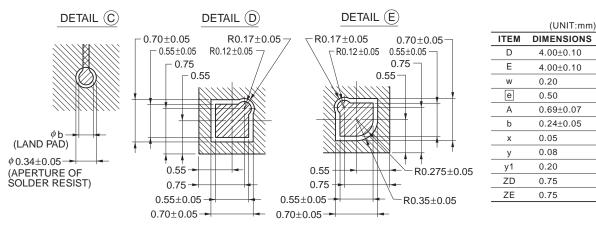


Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
А			0.80
A ₁	0.00	0.02	0.05
Аз	0.203 REF.		
b	0.18	0.25	0.30
D	5.00 BSC		
Е	5.00 BSC		
е	0.50 BSC		
L	0.35	0.40	0.45
K	0.20		
D ₂	3.15	3.20	3.25
E ₂	3.15	3.20	3.25
aaa	0.15		
bbb	0.10		
ccc	0.10		
ddd	0.05		
eee	0.08		
fff	0.10		

4.6 36-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA36-4x4-0.50	PWLG0036KA-A	P36FC-50-AA4-2	0.023





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(UNIT:mm)

4.00±0.10

4.00±0.10

0.24±0.05

0.20

0.50 0.69±0.07

0.05 0.08

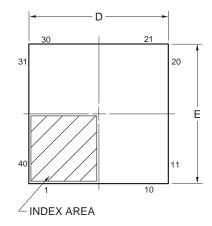
0.20

0.75

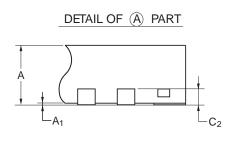
0.75

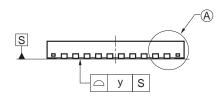
4.7 40-pin Package

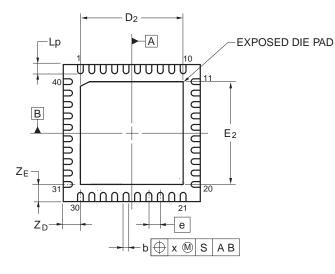
JEITA Package code	RENESAS code	Previous code	MASS (TYP.) [g]
P-HWQFN40-6x6-0.50	PWQN0040KC-A	P40K8-50-4B4-5	0.09









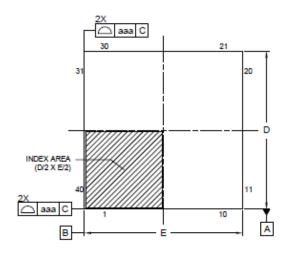


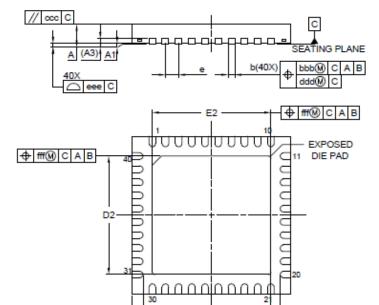
Referance	Dimens	Dimension in Millimeters		
Symbol	Min	Nom	Max	
D	5.95	6.00	6.05	
Е	5.95	6.00	6.05	
А			0.80	
A ₁	0.00			
b	0.18	0.25	0.30	
е		0.50		
Lp	0.30	0.40	0.50	
х			0.05	
у	_		0.05	
Z _D		0.75		
Z _E		0.75		
C ₂	0.15	0.20	0.25	
D ₂	_	4.50		
E ₂		4.50		

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<R>

JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN040-6x6-0.50	PWQN0040KD-A	0.08





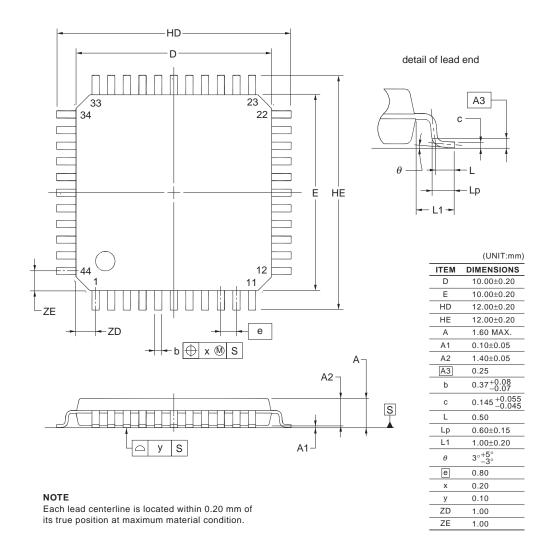
L(40X)

Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
Α	-	_	0.80
A ₁	0.00	0.02	0.05
As		0.203 REF	
b	0.18	0.25	0.30
D	6.00 BSC		
E	6.00 BSC		
e	0.50 BSC		
L	0.30	0.40	0.50
K	0.20	_	_
D ₂	4.45	4.50	4.55
E2	4.45	4.50	4.55
aaa		0.15	
bbb	0.10		
coc	0.10		
ddd	0.05		
eee	0.08		
fff	0.10		

K(40X)

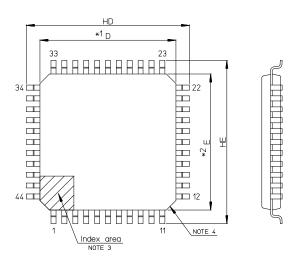
4.8 44-pin Package

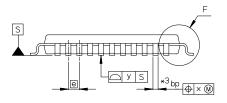
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP44-10x10-0.80	PLQP0044GC-A	P44GB-80-UES-2	0.36



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JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP44-10x10-0.80	PLQP0044GC-D		0.36g





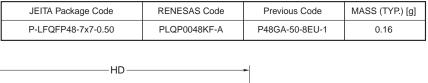
- OTE)

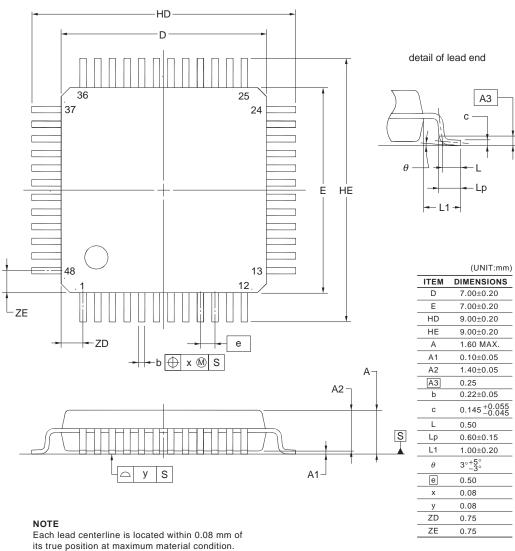
 1. DIMENSIONS '*1' AND '*2' DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION '*3' DOES NOT INCLUDE TRIM OFFSET.
 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

A A A A A A A A A A A A A A A A A A A		0.25	0
		Lp L1	_
	Detail F		

Reference Symbol	Dimens	ion in Mil	limeters
	Min	Nom	Max
D	9.8	10.0	10.2
E	9.8	10.0	10.2
A2		1.4	
HD	11.8	12.0	12.2
HE	11.8	12.0	12.2
Α	_		1.6
A1	0.05		0.15
bp	0.22	0.37	0.45
С	0.09		0.20
θ	0 °	3.5°	8 °
е		0.80	_
×			0.20
У			0.10
Lp	0.45	0.6	0.75
L1		1.0	

4.9 48-pin Package



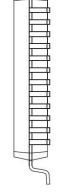


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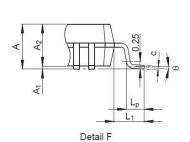
JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP48-7x7-0.50	PLQP0048KB-B	_	0.2

 H_D *1 D 37 💷 124 ш П П *2 E 뿐 ш П ш ш ш 13 48 □□ NOTE 4

Unit: mm



- NOTE)
 1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
- 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.
- 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

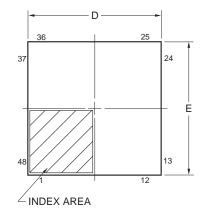


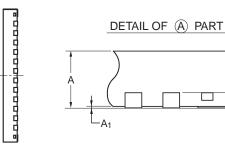
NOTE 3

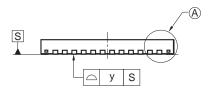
Reference Symbol	Dimensions in millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A ₂	_	1.4	5
HD	8.8	9.0	9.2
HE	8.8	9.0	9.2
Α			1.7
A ₁	0.05	-	0.15
bp	0.17	0.20	0.27
С	0.09	1	0.20
θ	0°	3.5°	8°
е	_	0.5	
X	_	-	0.08
У	_		0.08
Lp	0.45	0.6	0.75
L ₁	_	1.0	,—,

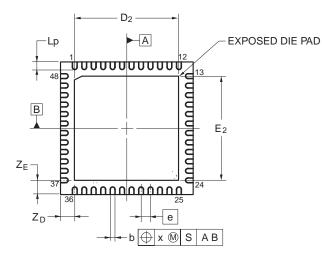
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JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6	0.13





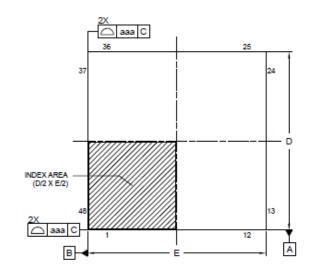


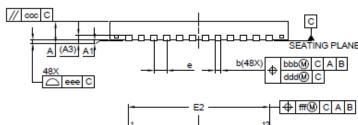


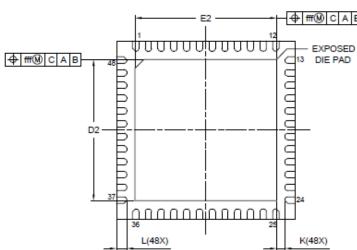
Referance	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	6.95	7.00	7.05
Е	6.95	7.00	7.05
А			0.80
A ₁	0.00		
b	0.18	0.25	0.30
е		0.50	
Lp	0.30	0.40	0.50
Х			0.05
у			0.05
Z _D		0.75	
Z _E		0.75	
c ₂	0.15	0.20	0.25
D ₂		5.50	_
E ₂		5.50	_

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JEITA Package code	RENESAS code	MASS(TYP.)[g]
P-HWQFN048-7x7-0.50	PWQN0048KE-A	0.13



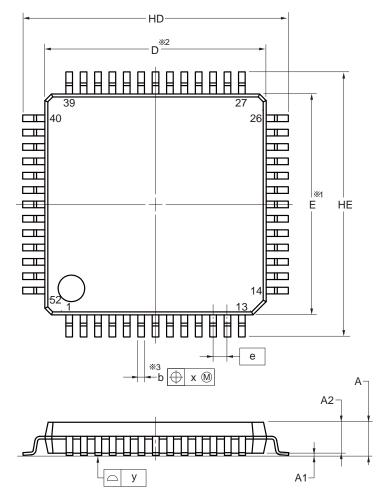




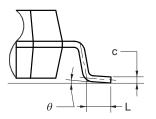
Reference	Dimension in Millimeters		
Symbol	Min.	Nom.	Max.
Α	-	-	0.80
A ₁	0.00	0.02	0.05
Aa	(0.203 REF	
b	0.20	0.25	0.30
D		7.00 BSC	
Е	7.00 BSC		
e	0.50 BSC		
L	0.30	0.40	0.50
K	0.20		
D2	5.50	5.55	5.60
E₂	5.50	5.55	5.60
aaa		0.15	
bbb		0.10	
ccc	0.10		
ddd	0.05		
eee	0.08		
fff	·	0.10	

4.10 52-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP52-10x10-0.65	PLQP0052JA-A	P52GB-65-GBS-1	0.3



detail of lead end



(UNIT:mm)

	, ,
ITEM	DIMENSIONS
D	10.00±0.10
Е	10.00±0.10
HD	12.00±0.20
HE	12.00±0.20
Α	1.70 MAX.
A1	0.10±0.05
A2	1.40
b	0.32 ± 0.05
С	0.145±0.055
L	0.50±0.15
θ	0° to 8°
е	0.65
х	0.13
v	0.10

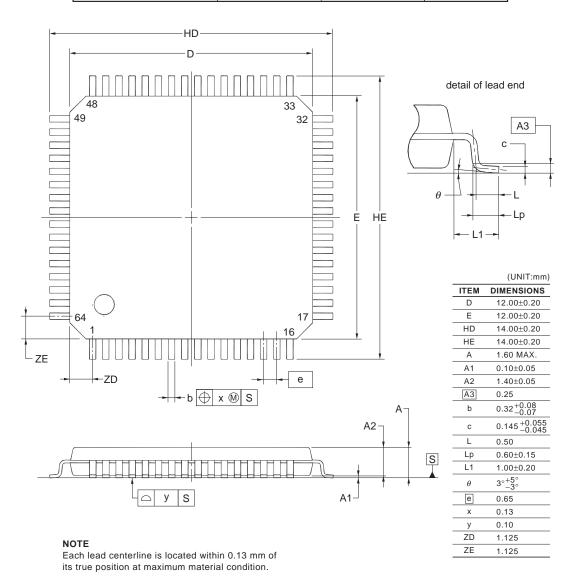
NOTE

- 1.Dimensions "%1" and "%2" do not include mold flash.
- 2.Dimension "%3" does not include trim offset.

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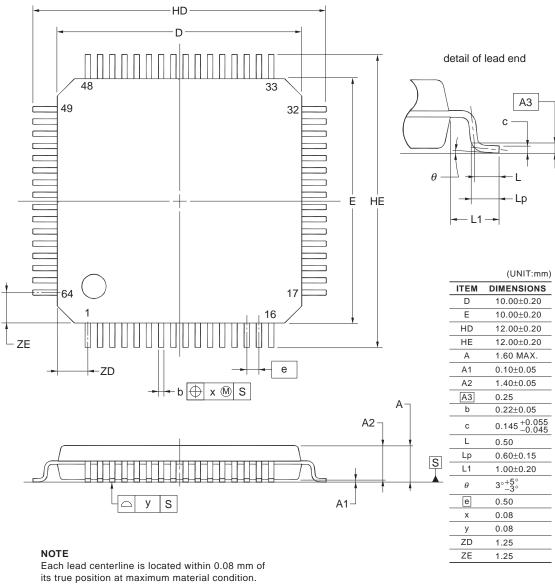
4.11 64-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP64-12x12-0.65	PLQP0064JA-A	P64GK-65-UET-2	0.51



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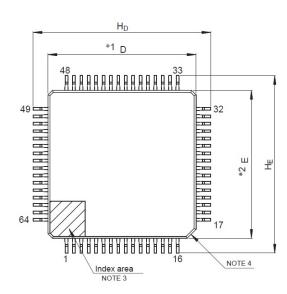
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35
НО		 -I	

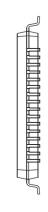


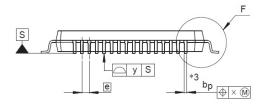
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JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP64-10x10-0.50	PLQP0064KB-C	_	0.3

Unit: mm



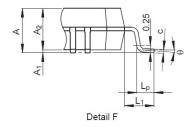




- NOTE)
 1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
- 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.

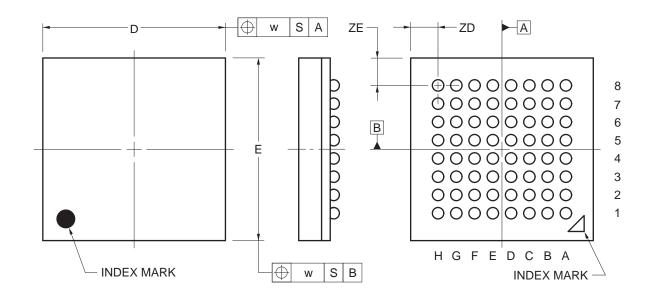
 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

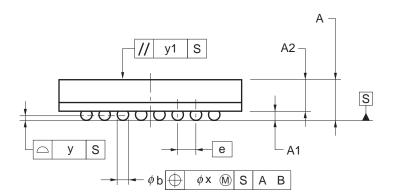
Reference	Dimensi	ons in mi	llimeters
Symbol	Min	Nom	Max
D	9.9	10.0	10.1
E	9.9	10.0	10.1
A ₂	9-0	1.4	_
H_D	11.8	12.0	12.2
HE	11.8	12.0	12.2
Α	_	_	1.7
A ₁	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09	1	0.20
θ	0°	3.5°	8°
е	1	0.5	
X	-	10-0	0.08
У	11	1	0.08
Lp	0.45	0.6	0.75
L ₁	10-04	1.0	-



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JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-VFBGA64-4x4-0.40	PVBG0064LA-A	P64F1-40-AA2-2	0.03



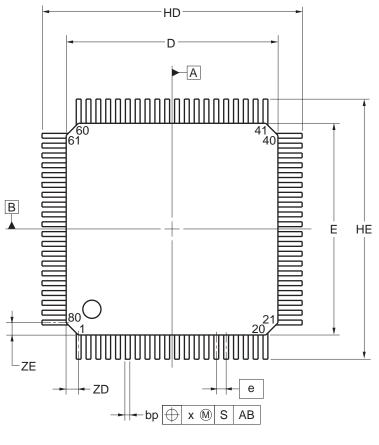


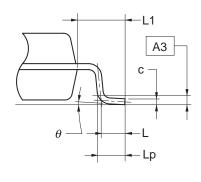
	(UNIT:mm)
ITEM	DIMENSIONS
D	4.00±0.10
Е	4.00±0.10
W	0.15
Α	0.89±0.10
A1	0.20±0.05
A2	0.69
е	0.40
b	0.25±0.05
х	0.05
у	0.08
у1	0.20
ZD	0.60
ZE	0.60

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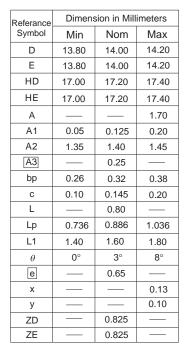
4.12 80-pin Package

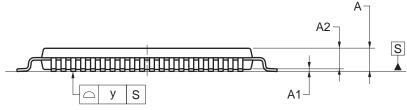
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69





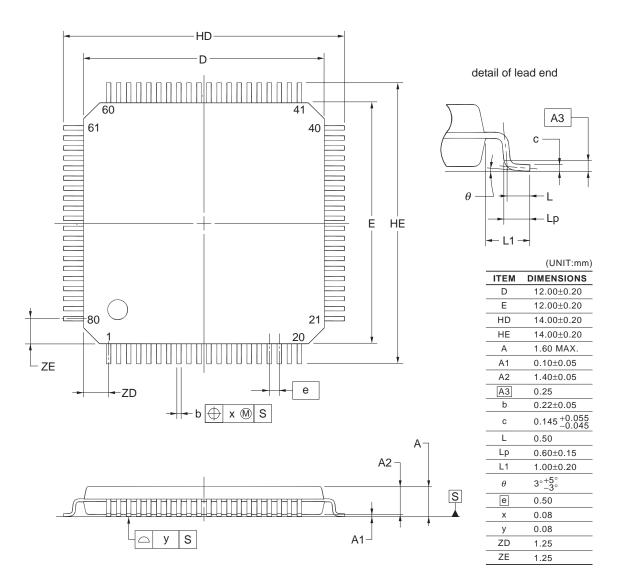
detail of lead end





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JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP80-12x12-0.50	PLQP0080KE-A	P80GK-50-8EU-2	0.53

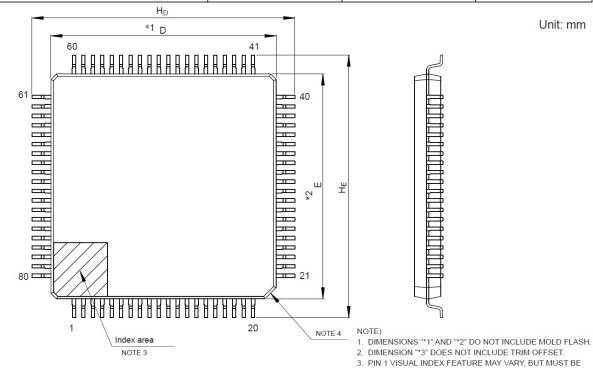


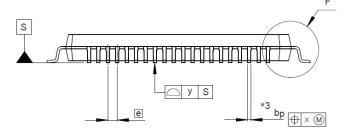
NOTE

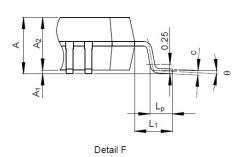
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

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JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP80-12x12-0.50	PLQP0080KB-B	=	0.5







Reference	Dimensi	ions in mi	llimeters
Symbol	Min	Nom	Max
D	11.9	12.0	12.1
Е	11.9	12.0	12.1
A ₂		1.4	00
H_D	13.8	14.0	14.2
HE	13.8	14.0	14.2
Α	_	_	1.7
A ₁	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09	_	0.20
θ	0°	3.5°	8°
е	_	0.5	0-0
X	_	_	0.08
У	_	_	0.08
Lp	0.45	0.6	0.75
L ₁	_	1.0	.—.

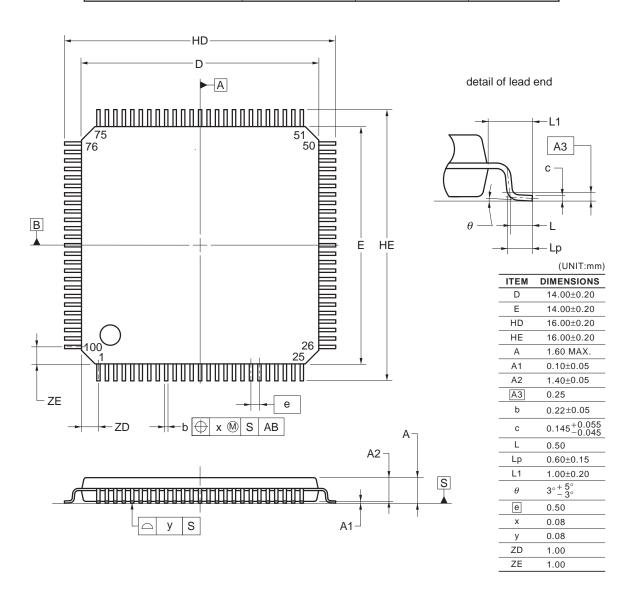
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LOCATED WITHIN THE HATCHED AREA.

4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

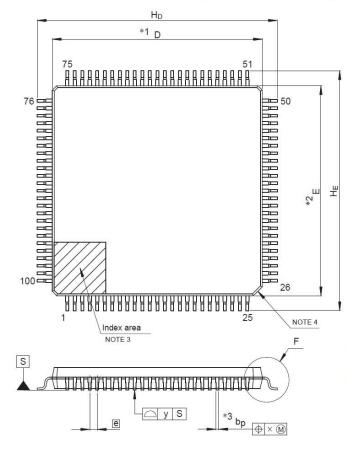
4.13 100-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP100-14x14-0.50	PLQP0100KE-A	P100GC-50-GBR-1	0.69



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JEITA Package Code	RENESAS Code	Previous Code	MASS (Typ) [g]
P-LFQFP100-14x14-0.50	PLQP0100KB-B	-	0.6



Detail F

Unit: mm

NOTE)

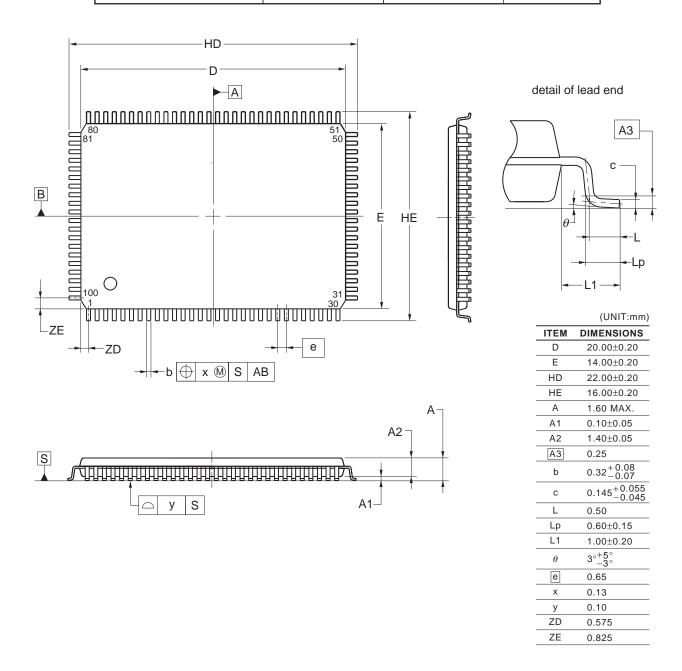
- 1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
 2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.
- 3. PIN 1 VISUAL INDEX FEATURE MAY VARY, BUT MUST BE LOCATED WITHIN THE HATCHED AREA.

 4. CHAMFERS AT CORNERS ARE OPTIONAL, SIZE MAY VARY.

Reference	Dimens	ions in mi	llimeters
Symbol	Min	Nom	Max
D	13.9	14.0	14.1
E	13.9	14.0	14.1
A ₂	_	1.4	S
H _D	15.8	16.0	16.2
HE	15.8	16.0	16.2
Α		_	1.7
A ₁	0.05	_	0.15
bp	0.15	0.20	0.27
С	0.09	_	0.20
θ	0°	3.5°	8°
е	_	0.5	-
Х	_	-	0.08
У	_	_	0.08
Lp	0.45	0.6	0.75
L ₁	-	1.0	11-11-11

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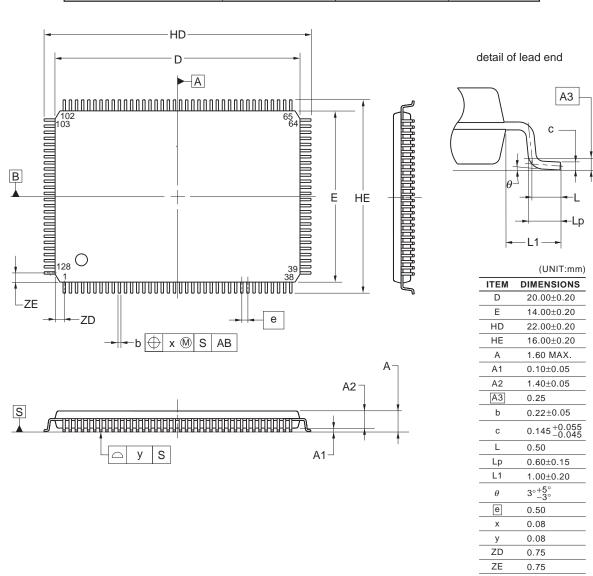
JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP100-14x20-0.65	PLQP0100JC-A	P100GF-65-GBN-1	0.92



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4.14 128-pin Package

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LFQFP128-14x20-0.50	PLQP0128KD-A	P128GF-50-GBP-1	0.92



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Revision History

RL78/G13 Datasheet

			Description		
Rev.	Date	Page	Summary		
1.00	Feb 29, 2012	-	First Edition issued		
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count corrected.		
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.		
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.		
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.		
		59, 63, 67	Descriptions of Note 8 in a table corrected.		
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.		
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.		
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.		
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.		
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.		
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.		
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.		
3.00	Aug 02, 2013	1	Modification of 1.1 Features		
		3	Modification of 1.2 List of Part Numbers		
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution		
		16 to 32	Modification of package type in 1.3.1 to 1.3.14		
		33	Modification of description in 1.4 Pin Identification		
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions		
		55	Modification of description in table of Absolute Maximum Ratings (T _A = 25°C)		
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics		
		57	Modification of table in 2.2.2 On-chip oscillator characteristics		
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics		
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics		
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products		
		68	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products		
		70	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products		
		72	Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products		
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products		
		75	Modification of (4) Peripheral Functions (Common to all products)		
		77	Modification of table in 2.4 AC Characteristics		
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation		
		80	Modification of figures of AC Timing Test Points and External System Clock Timing		

			Description
Rev.	Date	Page	Summary
3.00	Aug 02, 2013	81	Modification of figure of AC Timing Test Points
		81	Modification of description and note 3 in (1) During communication at same potential (UART mode)
		83	Modification of description in (2) During communication at same potential (CSI mode)
		84	Modification of description in (3) During communication at same potential (CSI mode)
		85	Modification of description in (4) During communication at same potential (CSI mode) (1/2)
		86	Modification of description in (4) During communication at same potential (CSI mode) (2/2)
		88	Modification of table in (5) During communication at same potential (simplified I ² C mode) (1/2)
		89	Modification of table and caution in (5) During communication at same potential (simplified I ² C mode) (2/2)
		91	Modification of table and notes 1 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		92, 93	Modification of table and notes 2 to 7 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		94	Modification of remarks 1 to 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		95	Modification of table in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (1/2)
		96	Modification of table and caution in (7) Communication at different potential (2.5 V, 3 V) (CSI mode) (2/2)
		97	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		98	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		99	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		100	Modification of remarks 3 and 4 in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		102	Modification of table in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/2)
		103	Modification of table and caution in (9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/2)
		106	Modification of table in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (1/2)
		107	Modification of table, note 1, and caution in (10) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)
		109	Addition of (1) I ² C standard mode
		111	Addition of (2) I ² C fast mode
		112	Addition of (3) I ² C fast mode plus
		112	Modification of IICA serial transfer timing
		113	Addition of table in 2.6.1 A/D converter characteristics
		113	Modification of description in 2.6.1 (1)
		114	Modification of notes 3 to 5 in 2.6.1 (1)
		115	Modification of description and notes 2, 4, and 5 in 2.6.1 (2)
		116	Modification of description and notes 3 and 4 in 2.6.1 (3)
		117	Modification of description and notes 3 and 4 in 2.6.1 (4)

			Description
Rev.	Date	Page	Summary
3.00	Aug 02, 2013	118	Modification of table in 2.6.2 Temperature sensor/internal reference voltage characteristics
		118	Modification of table and note in 2.6.3 POR circuit characteristics
		119	Modification of table in 2.6.4 LVD circuit characteristics
		120	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode
		120	Renamed to 2.6.5 Power supply voltage rising slope characteristics
		122	Modification of table, figure, and remark in 2.10 Timing Specs for Switching Flash Memory Programming Modes
		123	Modification of caution 1 and description
		124	Modification of table and remark 3 in Absolute Maximum Ratings (T _A = 25°C)
		126	Modification of table, note, caution, and remark in 3.2.1 X1, XT1 oscillator characteristics
		126	Modification of table in 3.2.2 On-chip oscillator characteristics
		127	Modification of note 3 in 3.3.1 Pin characteristics (1/5)
		128	Modification of note 3 in 3.3.1 Pin characteristics (2/5)
		133	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (1/2)
		135	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (2/2)
		137	Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (1/2)
		139	Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products (2/2)
		140	Modification of (3) Peripheral Functions (Common to all products)
		142	Modification of table in 3.4 AC Characteristics
		143	Addition of Minimum Instruction Execution Time during Main System Clock Operation
		143	Modification of figure of AC Timing Test Points
		143	Modification of figure of External System Clock Timing
		145	Modification of figure of AC Timing Test Points
		145	Modification of description, note 1, and caution in (1) During communication at same potential (UART mode)
		146	Modification of description in (2) During communication at same potential (CSI mode)
		147	Modification of description in (3) During communication at same potential (CSI mode)
		149	Modification of table, note 1, and caution in (4) During communication at same potential (simplified I ² C mode)
		151	Modification of table, note 1, and caution in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)
		152 to 154	Modification of table, notes 2 to 6, caution, and remarks 1 to 4 in (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (2/2)
		155	Modification of table in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (1/3)
		156	Modification of table and caution in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (2/3)
		157, 158	Modification of table, caution, and remarks 3 and 4 in (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (3/3)
		160, 161	Modification of table and caution in (7) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode)

			Description		
Rev.	Date	Page	Summary		
3.00	Aug 02, 2013	163	Modification of table in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I^2C mode) (1/2)		
		164, 165	Modification of table, note 1, and caution in (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (simplified I ² C mode) (2/2)		
		166	Modification of table in 3.5.2 Serial interface IICA		
		166	Modification of IICA serial transfer timing		
		167	Addition of table in 3.6.1 A/D converter characteristics		
		167, 168	Modification of table and notes 3 and 4 in 3.6.1 (1)		
		169	Modification of description in 3.6.1 (2)		
		170	Modification of description and note 3 in 3.6.1 (3)		
		171	Modification of description and notes 3 and 4 in 3.6.1 (4)		
		172	Modification of table and note in 3.6.3 POR circuit characteristics		
		173	Modification of table of LVD Detection Voltage of Interrupt & Reset Mode		
		173	Modification from Supply Voltage Rise Time to 3.6.5 Power supply voltage		
			rising slope characteristics		
		174	Modification of 3.9 Dedicated Flash Memory Programmer Communication (UART)		
		175	Modification of table, figure, and remark in 3.10 Timing Specs for Switching Flash Memory Programming Modes		
3.10	Nov 15, 2013	123	Caution 4 added.		
		125	Note for operating ambient temperature in 3.1 Absolute Maximum Ratings deleted.		
3.30	Mar 31, 2016	18	Modification of the position of the index mark in 25-pin plastic WFLGA (3 \times 3 mm, 0.50 mm pitch) of 1.3.3 25-pin products		
		49	Modification of power supply voltage in 1.6 Outline of Functions [20-pin, 24-pin, 25-pin, 30-pin, 32-pin, 36-pin products]		
		51	Modification of power supply voltage in 1.6 Outline of Functions [40-pin, 44-pin, 48-pin, 52-pin, 64-pin products]		
		53	Modification of power supply voltage in 1.6 Outline of Functions [80-pin, 100-pin, 128-pin products]		
		110 to 112, 167	ACK corrected to ACK		
3.40	May 31, 2018	172	Addition of note in 3.6.3 POR circuit characteristics		
3.41	Jan 31, 2020	3	Addition of packaging specifications in Figure 1-1 Part Number, Memory Size,		
			and Package of RL78/G13		
		4 to 28	Addition of ordering part numbers and RENESAS codes in Table 1-1 List of Ordering Part Numbers		
		189, 190,	Modification of the titles of the subchapters and deletion of product names in		
		192 to 194,	Chapter 4		
		196 to 198,			
		200,			
		202 to 205, 207 to 209,			
		211, 213,			
		214			
		191	Addition of figure in 4.2 24-pin Package		
		195	Addition of figure in 4.3 32-pin Package		
		199	Addition of figure in 4.8 44-pin Package		

		Description	
Rev.	Date	Page	Summary
3.41	Jan 31, 2020	201	Addition of figure in 4.9 48-pin Package
		206	Addition of figure in 4.11 64-pin Package
		210	Addition of figure in 4.12 80-pin Package
		212	Addition of figure in 4.13 100-pin Package
3.50	Jun 30, 2020	1	Modification of description in 1.1 Features
		3	Modification of Figure 1-1 Part Number, Memory Size, and Package of RL78/G13
		4 to 11	Modification of Table 1-1 List of Ordering Part Numbers
		12	Addition of packaging specifications in 1.3.1 20-pin products
		173	Addition of package drawing in 4.1 20-pin Package
		182	Addition of package drawing in 4.7 40-pin Package
		188	Addition of package drawing in 4.9 48-pin Package

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General Precautions in the Handling of Microprocessing Unit and Microcontroller Unit Products

The following usage notes are applicable to all Microprocessing unit and Microcontroller unit products from Renesas. For detailed usage notes on the products covered by this document, refer to the relevant sections of the document as well as any technical updates that have been issued for the products.

1. Precaution against Electrostatic Discharge (ESD)

A strong electrical field, when exposed to a CMOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop the generation of static electricity as much as possible, and quickly dissipate it when it occurs. Environmental control must be adequate. When it is dry, a humidifier should be used. This is recommended to avoid using insulators that can easily build up static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work benches and floors must be grounded. The operator must also be grounded using a wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions must be taken for printed circuit boards with mounted semiconductor devices.

2. Processing at power-on

The state of the product is undefined at the time when power is supplied. The states of internal circuits in the LSI are indeterminate and the states of register settings and pins are undefined at the time when power is supplied. In a finished product where the reset signal is applied to the external reset pin, the states of pins are not guaranteed from the time when power is supplied until the reset process is completed. In a similar way, the states of pins in a product that is reset by an on-chip power-on reset function are not guaranteed from the time when power is supplied until the power reaches the level at which resetting is specified.

3. Input of signal during power-off state

Do not input signals or an I/O pull-up power supply while the device is powered off. The current injection that results from input of such a signal or I/O pull-up power supply may cause malfunction and the abnormal current that passes in the device at this time may cause degradation of internal elements. Follow the guideline for input signal during power-off state as described in your product documentation.

4. Handling of unused pins

Handle unused pins in accordance with the directions given under handling of unused pins in the manual. The input pins of CMOS products are generally in the high-impedance state. In operation with an unused pin in the open-circuit state, extra electromagnetic noise is induced in the vicinity of the LSI, an associated shoot-through current flows internally, and malfunctions occur due to the false recognition of the pin state as an input signal become possible.

Clock signals

After applying a reset, only release the reset line after the operating clock signal becomes stable. When switching the clock signal during program execution, wait until the target clock signal is stabilized. When the clock signal is generated with an external resonator or from an external oscillator during a reset, ensure that the reset line is only released after full stabilization of the clock signal. Additionally, when switching to a clock signal produced with an external resonator or by an external oscillator while program execution is in progress, wait until the target clock signal is stable.

- 6. Voltage application waveform at input pin
 - Waveform distortion due to input noise or a reflected wave may cause malfunction. If the input of the CMOS device stays in the area between V_{IL} (Max.) and V_{IH} (Min.) due to noise, for example, the device may malfunction. Take care to prevent chattering noise from entering the device when the input level is fixed, and also in the transition period when the input level passes through the area between V_{IL} (Max.) and V_{IH} (Min.).
- 7. Prohibition of access to reserved addresses

Access to reserved addresses is prohibited. The reserved addresses are provided for possible future expansion of functions. Do not access these addresses as the correct operation of the LSI is not guaranteed.

8. Differences between products

Before changing from one product to another, for example to a product with a different part number, confirm that the change will not lead to problems. The characteristics of a microprocessing unit or microcontroller unit products in the same group but having a different part number might differ in terms of internal memory capacity, layout pattern, and other factors, which can affect the ranges of electrical characteristics, such as characteristic values, operating margins, immunity to noise, and amount of radiated noise. When changing to a product with a different part number, implement a system-evaluation test for the given product.

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Renesas Electronics Corporation TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan

Renesas Electronics America Inc. Milpitas Campus 1001 Murphy Ranch Road, Milpitas, CA 95035, U.S.A. Tel: +1-408-432-8888, Fax: +1-408-434-5351

Renesas Electronics America Inc. San Jose Campus 6024 Silver Creek Valley Road, San Jose, CA 95138, USA Tel: +1-408-284-8200, Fax: +1-408-284-2775

Renesas Electronics Canada Limited 9251 Yonge Street, Suite 8309 Richmond Hill, Ontario Canada L4C 9T3 Tel: +1-905-237-2004

Renesas Electronics Europe GmbH

Arcadiastrasse 10, 40472 Düsseldorf, German Tel: +49-211-6503-0, Fax: +49-211-6503-1327

Renesas Electronics (China) Co., Ltd.
Room 101-T01, Floor 1, Building 7, Yard No. 7, 8th Street, Shangdi, Haidian District, Beijing 100085, China Tel: +86-10-8235-1155, Fax: +86-10-8235-7679 Renesas Electronics (Shanghai) Co., Ltd.
Unit 301, Tower A, Central Towers, 555 Langao Road, Putuo District, Shanghai 200333, China Tel: +86-21-2226-0888, Fax: +86-21-2226-0999

Renesas Electronics Hong Kong Limited
Unit 1601-1611, 16/F., Tower 2, Grand Century Place, 193 Prince Edward Road West, Mongkok, Kowloon, Hong Kong Tel: +852-2265-6688, Fax: +852 2886-9022

Renesas Electronics Taiwan Co., Ltd. 13F, No. 363, Fu Shing North Road, Taipei 10543, Taiwan Tel: +886-2-8175-9600, Fax: +886 2-8175-9670

Renesas Electronics Singapore Pte. Ltd. 80 Bendemeer Road, #06-02 Singapore 33 Tel: +65-6213-0200, Fax: +65-6213-0300

Renesas Electronics Malaysia Sdn.Bhd.
Unit No 3A-1 Level 3A Tower 8 UOA Business Park, No 1 Jalan Pengaturcara U1/51A, Seksyen U1, 40150 Shah Alam, Selangor, Malaysia Tel: +60-3-5022-1288, Fax: +60-3-5022-1290

Renesas Electronics India Pvt. Ltd. No.777C, 100 Feet Road, HAL 2nd Stage, Indiranagar, Bangalore 560 038, India Tel: +91-80-67208700

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